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PSoC 6 MCU: CYB06447BZI-BLDx Datasheet

PSoC 64 "Secure Boot" MCU with Bluetooth LE

General Description

PSoC[®] 6 MCU is a high-performance, ultra-low-power and secured MCU platform, purpose-built for IoT applications. The PSoC 64 product line, based on the PSoC 6 MCU platform, features out-of-box security functionality, providing an isolated root-of-trust with true attestation and provisioning services. In addition, it delivers a pre-configured secured execution environment which supports system software of various IoT platforms; and enables TLS authentication, secured storage, and secured firmware management. PSoC 64 also includes a rich execution environment for application development, with RTOS support that communicates with the secured execution environment.

The PSoC 64 CYB06447BZI-BLDx product line provides wireless connectivity with Bluetooth LE 5.0 compliance.

Features

32-bit Dual CPU Subsystem

Note: In PSoC 64 the Cortex M0+ is reserved for system functions, and is not available for applications.

- 150-MHz Arm[®] Cortex[®]-M4F (CM4) CPU with single-cycle multiply, floating point, and memory protection unit (MPU)
- 100-MHz Cortex-M0+ (CM0+) CPU with single-cycle multiply and MPU
- User-selectable core logic operation at either 1.1 V or 0.9 V
- Active CPU current slope with 1.1-V core operation
- □ Cortex-M4: 40 µA/MHz
- □ Cortex-M0+: 20 µA/MHz
- Active CPU current slope with 0.9-V core operation
 - □ Cortex-M4: 22 µA/MHz
 - □ Cortex-M0+: 15 µA/MHz
- Two DMA controllers with 16 channels each

Memory Subsystem

- 832-KB application flash, 32-KB auxiliary flash (AUXflash), and 32-KB supervisory flash (SFlash); read-while-write (RWW) support. Two 8-KB flash caches, one for each CPU.
- 176-KB SRAM with power and data retention control
- One-time-programmable (OTP) 1-Kb eFuse array

Hardware-Based Root-of-Trust (RoT)

- RoT based on immutable boot-up code, flash content hash, and Cypress public key that ensures firmware integrity prior to provisioning
- Supports trusted RoT handover to maintain chain of trust and establish OEM trust anchor for secured boot
- Device generates a unique device ID and a device secret key during the provisioning process, which can be used for attestation and signing

Immutable "Secure Boot" Support

 Flexible chain of trust can use different signatures for different images ■ ECC-based image signature validation

Cypress Bootloader

- Open Source MCUBoot^[1] based bootloader optimized for the PSoC 64 family
- Pre-built bootloader binary capable of validating, launching and updating signed user application images
- Tightly integrated with provisioned debug and boot policies to inherit and implement security policies

Bluetooth Low Energy Subsystem

- 2.4-GHz RF transceiver with 50-Ω antenna drive
- Digital PHY
- Link Layer engine supporting master and slave modes
- Programmable TX power: up to 4 dBm
- RX sensitivity: -95 dBm
- RSSI: 4-dB resolution
- 5.7-mA Tx (0 dBm) and 6.7 mA RX (2 Mbps) current with 3.3-V supply and internal SIMO Buck converter
- Link Layer engine supports four connections simultaneously
- Supports 2 Mbps data rate

Low-Power 1.7-V to 3.6-V Operation

- Six power modes for fine-grained power management
- Deep Sleep mode current of 7 µA with 64-KB SRAM retention
- On-chip Single-In Multiple Out (SIMO) DC-DC buck converter, <1 µA quiescent current
- Backup domain with 64 bytes of memory and real-time clock

Flexible Clocking Options

- 8-MHz Internal Main Oscillator (IMO) with ±2% accuracy
- Ultra-low-power 32-kHz Internal Low-speed Oscillator (ILO)
- On-chip crystal oscillators (16 to 35 MHz, and 32 kHz)
- Phase-locked loop (PLL) for multiplying clock frequencies
- Frequency-locked loop (FLL) for multiplying IMO frequency
- Integer and fractional peripheral clock dividers

Note

1. For details, refer to https://mcuboot.com/.

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Quad SPI (QSPI)/Serial Memory Interface (SMIF)

- Execute-In-Place (XIP) from external quad SPI Flash
- On-the-fly encryption and decryption
- 4-KB cache for greater XIP performance with lower power
- Supports single, dual, quad, dual-quad, and octal interfaces with throughput up to 640 Mbps

Segment LCD Drive

■ Supports up to 83 segments and up to 8 commons

Serial Communication

- Nine run-time configurable serial communication blocks (SCBs)
 - □ Eight SCBs: configurable as SPI, I²C, or UART
 - □ One Deep Sleep SCB: configurable as SPI or I²C
- USB full-speed device interface

Audio Subsystem

■ Two pulse density modulation (PDM) channels and one I²S channel with time division multiplexed (TDM) mode

Timing and Pulse-Width Modulation

- Thirty-two timer/counter/pulse-width modulators (TCPWM)
- Center-aligned, edge, and pseudo-random modes
- Comparator-based triggering of Kill signals

Programmable Analog

- 12-bit 1-Msps SAR ADC with differential and single-ended modes and 16-channel sequencer with result averaging
- Two low-power comparators available in Deep Sleep and Hibernate modes
- Built-in temperature sensor connected to ADC
- One 12-bit voltage-mode digital-to-analog converter (DAC) with < 2-µs settling time
- Two opamps with low-power operation modes

Up to 84 Programmable GPIOs

- Two Smart I/O[™] ports (16 I/Os) enable Boolean operations on GPIO pins; available during system Deep Sleep
- Programmable drive modes, strengths, and slew rates
- Six overvoltage-tolerant (OVT) pins

Capacitive Sensing

- Cypress CapSense[®] provides best-in-class signal-to-noise ratio (SNR), liquid tolerance, and proximity sensing
- Enables dynamic usage of both self and mutual sensing
- Automatic hardware tuning (SmartSense[™])

Cryptography Accelerator

- Hardware acceleration for symmetric and asymmetric cryptographic methods and hash functions
- True random number generation (TRNG) function

Programmable Digital

- Twelve programmable logic blocks, each with 8 Macrocells and an 8-bit data path (called universal digital blocks or UDBs)
- Usable as drag-and-drop Boolean primitives (gates, registers), or as Verilog-programmable blocks
- Cypress-provided peripheral component library using UDBs to implement functions such as communication peripherals (for example, LIN, UART, SPI, I²C, S/PDIF and other protocols), Waveform Generators, Pseudo-Random Sequence (PRS) generation, and many other functions.

Profiler

Eight counters provide event or duration monitoring of on-chip resources

Packages

■ 124-BGA and 116-BGA

Device Identification and Revisions

- Product line ID (12-bit): 0x100
- Major/Minor Die Revision ID: 2/4
- Firmware Revisions: Rom Boot: 4.1, Flash Boot: 4.0.2.1842 (see Boot Code section)

This product line has a JTAG ID which is available through the SWJ interface. It is a 32-bit ID, where:

- The most significant digit is the device revision, based on the Major Die Revision
- The next four digits correspond to the part number, for example "E4B0" as a hexadecimal number
- The three least significant digits are the manufacturer ID, in this case "069" as a hexadecimal number

The Silicon ID system call can be used by firmware to get Silicon ID and ROM Boot data. For more information, see the technical reference manual (TRM).

The Flash Boot version can be read directly from a designated address 0x1600 2004. For more information, see the technical reference manual (TRM).



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Development Ecosystem

PSoC 6 MCU Resources

Cypress provides a wealth of data at www.cypress.com to help you select the right PSoC device and quickly and effectively integrate it into your design. The following is an abbreviated, hyperlinked list of resources for PSoC 6 MCU:

- Overview: PSoC Portfolio, PSoC Roadmap
- Product Selectors: PSoC 6 MCU
- Application Notes cover a broad range of topics, from basic to advanced level, and include the following:
 - □ AN221774: Getting Started with PSoC 6 MCU
 - AN210781: Getting Started with PSoC 6 MCU with Bluetooth Low Energy Connectivity
 - □ AN218241: PSoC 6 MCU Hardware Design Guide
 - □ AN213924: PSoC 6 MCU Device Firmware Update Guide
 - □ AN219528: PSoC 6 MCU Power Reduction Techniques
 - □ AN85951: PSoC 4, PSoC 6 MCU CapSense Design Guide
- Code Examples demonstrate product features and usage, and are also available on Cypress GitHub repositories.
- Technical Reference Manuals (TRMs) provide detailed descriptions of PSoC 6 MCU architecture and registers.

- PSoC 6 MCU Programming Specification provides the information necessary to program PSoC 6 MCU nonvolatile memory.
- Development Tools
 - ModusToolbox[®] software enables cross platform code development with a robust suite of tools and software libraries.
 - Secure Boot" SDK includes all required libraries, tools, and sample code to provision and develop applications for PSoC 64 MCUs.
 - □ CY8CPROTO-064B0S1-BLE PSoC 64 "Secure Boot" Prototyping Kit: a low-cost hardware platform that enables design and debug of the PSoC 64 CYB06447BZI-BLDx product line
 - PSoC 6 CAD libraries provide footprint and schematic support for common tools. BSDL files and IBIS models are also available.
- Training Videos are available on a wide range of topics including the PSoC 6 MCU 101 series.
- Cypress Developer Community enables connection with fellow PSoC developers around the world, 24 hours a day, 7 days a week, and hosts a dedicated PSoC 6 MCU Community.



ModusToolbox Software

ModusToolbox Software is Cypress' comprehensive collection of multi-platform tools and software libraries that enable an immersive development experience for creating converged MCU and wireless systems. It is:

- Comprehensive it has the resources you need
- Flexible you can use the resources in your own workflow
- Atomic you can get just the resources you want

Cypress provides a large collection of code repositories on GitHub. This includes:

- Board Support Packages (BSPs) aligned with Cypress kits
- Low-level resources, including a hardware abstraction layer (HAL) and peripheral driver library (PDL)
- Middleware enabling industry-leading features such as CapSense[®], Bluetooth Low Energy, and mesh networks
- An extensive set of thoroughly tested code example applications

Note: The HAL provides a high-level, simplified interface to configure and use the hardware blocks on Cypress MCUs. It is a generic interface that can be used across multiple product families. For example, it wraps the PSoC 6 PDL with a simplified API, but the PDL exposes all low-level peripheral functionality. You can leverage the HAL's simpler and more generic interface for most of an application, even if one portion requires finer-grained control.

ModusToolbox Software is IDE-neutral and easily adaptable to your workflow and preferred development environment. It includes a project creator, peripheral and library configurators, a library manager, as well as the optional Eclipse IDE for ModusToolbox, as Figure 1 shows. For information on using Cypress tools, refer to the documentation delivered with ModusToolbox software, and AN228571: Getting Started with PSoC 6 MCU on ModusToolbox.

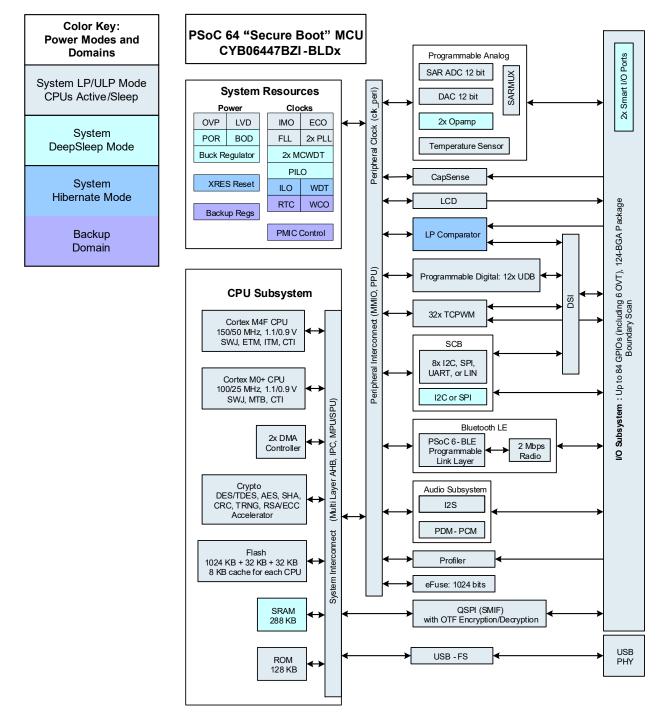
Figure 1. ModusToolbox Software Tools





Blocks and Functionality

Figure 2 shows the major subsystems and a simplified view of their interconnections. The color coding shows the lowest power mode where a block is still functional. For example, the SRAM is functional down to Deep Sleep mode.









This product line has up to 1 MB of flash; however, 192 KB is reserved for system usage, leaving 832 KB for applications. It also has up to 288 KB of SRAM; however, 112 KB is reserved for system usage, leaving 176 KB for applications.

The PSoC 64 devices offer an immutable, RoT-based boot-up process, which allows only signed applications to be booted up. In addition, secured user assets such as keys and debug policies can be provisioned on the device in an HSM environment and made immutable PSoC 64 also allows for root-of-trust based cryptography services which can be accessed using System calls.

There are three debug access ports, one each for CM4 and CM0+, and a system port. All debug and test interfaces can be permanently disabled during final production provisioning to avoid any malicious reprogramming or reading of flash and register contents.

PSoC 6 MCU devices include extensive support for programming, testing, debugging, and tracing both hardware and firmware. All device interfaces can be permanently disabled for applications concerned about a reprogrammed device or starting and interrupting flash programming sequences. All programming, debug, and test interfaces can be disabled.

Complete debug-on-chip functionality enables full device debugging in the final system using the standard production device. It does not require special interfaces, debugging pods, simulators, or emulators. Only the standard programming connections are required to fully support debug.

The Eclipse IDE for ModusToolbox provides fully integrated programming and debug support for these devices. The SWJ (SWD and JTAG) interface is fully compatible with industry-standard third party probes. With the ability to disable debug features, with very robust flash protection, and by allowing customer-proprietary functionality to be implemented in on-chip programmable blocks, PSoC 6 provides multiple levels of device security.



Functional Description

The following sections provide an overview of the features, capabilities and operation of each functional block identified in the block diagram in Figure 2. For more detailed information, refer to the following documentation:

■ Board Support Package (BSP) Documentation

BSPs are available on GitHub. They are aligned with Cypress kits and provide files for basic device functionality such as hardware configuration files, startup code, and linker files. The BSP also includes other libraries that are required to support a kit. Each BSP has its own documentation, but typically includes an API reference such as the example here. This search link finds all currently available BSPs on the Cypress GitHub site.

■ Hardware Abstraction Layer API Reference Manual

The Cypress Hardware Abstraction Layer (HAL) provides a high-level interface to configure and use hardware blocks on Cypress MCUs. It is a generic interface that can be used across multiple product families. You can leverage the HAL's simpler and more generic interface for most of an application, even if one portion requires finer-grained control. The HAL API Reference provides complete details. Example applications that use the HAL download it automatically from the GitHub repository.

Peripheral Driver Library (PDL) Application Programming Interface (API) Reference Manual

The Peripheral Driver Library (PDL) integrates device header files and peripheral drivers into a single package and supports all PSoC 6 MCU product lines. The drivers abstract the hardware functions into a set of easy-to-use APIs. These are fully documented in the PDL API Reference. Example applications that use the PSoC 6 PDL download it automatically from the GitHub repository.

■ Architecture Technical Reference Manual (TRM)

The architecture TRM provides a detailed description of each resource in the device. This is the next reference to use if it is necessary to understand the operation of the hardware below the software provided by PDL. It describes the architecture and functionality of each resource and explains the operation of each resource in all modes. It provides specific guidance regarding the use of associated registers.

■ Register Technical Reference Manual

The register TRM provides a complete list of all registers in the device. It includes the breakdown of all register fields, their possible settings, read/write accessibility, and default states. All registers that have a reasonable use in typical applications have functions to access them from within PDL. Note that ModusToolbox and PDL may provide software default conditions for some registers that are different from and override the hardware defaults.

CPU and Memory Subsystem

PSoC 6 has multiple bus masters, as Figure 2 shows. They are: CPUs, DMA controllers, QSPI, USB, and a Crypto block. Generally, all memory and peripherals can be accessed and shared by all bus masters through multi-layer Arm AMBA high-performance bus (AHB) arbitration. Accesses between CPUs can be synchronized using an inter-processor communication (IPC) block.

CPUs

There are two Arm Cortex CPUs:

The Cortex-M4 (CM4) has single-cycle multiply, a floating-point unit (FPU), and a memory protection unit (MPU). It can run at up to 150 MHz. This is the main CPU, designed for a short interrupt response time, high code density, and high throughput.

CM4 implements a version of the Thumb instruction set based on Thumb-2 technology (defined in the *Armv7-M Architecture Reference Manual*).

The Cortex-M0+ (CM0+) has single-cycle multiply, and an MPU. It can run at up to 100 MHz; however, for CM4 speeds above 100 MHz, CM0+ and bus peripherals are limited to half the speed of CM4. Thus, for CM4 running at 150 MHz, CM0+ and peripherals are limited to 75 MHz in system low power (LP) mode. In system ultra-low power (ULP) mode, CPU speeds are limited to 50 MHz and 25 MHz respectively.

In PSoC 64, the initial CM0+ frequency is set according to a provisioned security policy (see PSoC 64 Security). The frequency ranges from 8 MHz to 50 MHz. For more information, see the Architecture and Registers TRM.

CM0+ is the secondary CPU; it is used to implement system calls and device-level safety and protection features. CM0+ provides a secured, uninterruptible boot function. This helps ensure that post boot, system integrity is checked and memory and peripheral access privileges are enforced.

CM0+ implements the Armv6-M Thumb instruction set (defined in the *Armv6-M Architecture Reference Manual*).

The CPUs have the following power draw, at V_{DDD} = 3.3 V and using the internal buck regulator:

Table 1. Active Current Slope at V_{DDD} = 3.3 V Using the Internal Buck Regulator

		System Power Mode	
		ULP	LP
CPU	Cortex-M0+	15 μA/MHz	20 μA/MHz
CPU	Cortex-M4	22 μA/MHz	40 μA/MHz

The CPUs can be selectively placed in their Sleep and Deep Sleep power modes as defined by Arm.

Both CPUs have nested vectored interrupt controllers (NVIC) for rapid and deterministic interrupt response, and wakeup interrupt controllers (WIC) for CPU wakeup from Deep Sleep power mode.



The CPUs have extensive debug support. PSoC 6 has a debug access port (DAP) that acts as the interface for device programming and debug. An external programmer or debugger (the "host") communicates with the DAP through the device serial wire debug (SWD) or Joint Test Action Group (JTAG) interface pins. Through the DAP (and subject to restrictions), the host can access the device memory and peripherals as well as the registers in both CPUs.

Each CPU offers debug and trace features as follows:

- CM4 supports six hardware breakpoints and four watchpoints, 4-bit embedded trace macrocell (ETM), serial wire viewer (SWV), and printf()-style debugging through the single wire output (SWO) pin.
- CM0+ supports four hardware breakpoints and two watchpoints, and a micro trace buffer (MTB) with 4-KB dedicated RAM.

PSoC 6 also has an Embedded Cross Trigger for synchronized debugging and tracing of both CPUs.

Interrupts

This product line has 147 system and peripheral interrupt sources and supports interrupts and system exceptions on both CPUs. CM4 has 147 interrupt request lines (IRQ), with the interrupt source 'n' directly connected to IRQn. CM0+ has 32 interrupts IRQ[31:0] with configurable mapping of one system interrupt source to any of the IRQ[31:0].

Each interrupt supports configurable priority levels (eight levels for CM4 and four levels for CM0+). One system interrupt can be mapped to each of the CPUs' non-maskable interrupts (NMI). Up to 41 interrupt sources are capable of waking the device from Deep Sleep power mode using the WIC. Refer to the technical reference manual for details.

InterProcessor Communication (IPC)

In addition to the Arm SEV and WFE instructions, a hardware InterProcessor Communication (IPC) block is included. It includes 16 IPC channels and 16 IPC interrupt structures. The IPC channels can be used to implement data communication between the processors. Each IPC channel also implements a locking scheme which can be used to manage shared resources. The IPC interrupts let one processor interrupt the other, signaling an event. This is used to trigger events such as notify and release of the corresponding IPC channels. Some IPC channels and other resources are reserved, as Table 2 shows:

Table 2. Distribution of IPC Channels and Other Resources

Resources Available	Resources Consumed
IPC channels, 16 available	13 reserved
IPC interrupts, 16 available	13 reserved
Other interrupts	1 reserved
CM0+ NMI	Reserved
Other resources: clock dividers, DMA channels, etc.	4 CM0+ interrupt mux

DMA Controllers

There are two DMA controllers with 16 channels each, which support CPU-independent accesses to memory and peripherals. The descriptors for DMA channels can be in SRAM or flash. Therefore, the number of descriptors are limited only by the size of the memory. Each descriptor can transfer data in two nested loops with configurable address increments to the source and destination. The size of data transfer per descriptor varies based on the type of DMA channel. Refer to the technical reference manual for detail.

Cryptography Accelerator (Crypto)

This subsystem consists of hardware implementation and acceleration of cryptographic functions and random number generators.

The Crypto subsystem supports the following:

- Encryption/Decryption Functions
 - Data Encryption Standard (DES)
 - □ Triple DES (3DES)
 - □ Advanced Encryption Standard (AES) (128-, 192-, 256-bit)
 - □ Elliptic Curve Cryptography (ECC)
 - RSA cryptography functions
- Hashing functions
 - Secure Hash Algorithm (SHA)
 - □ SHA-1
 - □ SHA-224/-256/-384/-512
- Message authentication functions (MAC)
 - □ Hashed message authentication code (HMAC)
 - Cipher-based message authentication code (CMAC)
- 32-bit cyclic redundancy code (CRC) generator
- Random number generators
 - □ Pseudo random number generator (PRNG)
 - True random number generator (TRNG)

Protection Units

This product line has multiple types of protection units to control erroneous or unauthorized access to memory and peripheral registers. CM4 and CM0+ have Arm MPUs for protection at the bus master level. Other bus masters use additional MPUs. Shared memory protection units (SMPUs) help implement memory protection for memory resources that are shared among multiple bus masters. Peripheral protection units (PPU) are similar to SMPUs but are designed for protecting the peripheral register space.

Protection units support memory and peripheral access attributes including address range, read/write, code/data, privilege level, secured/non-secured, and protection context. Some protection unit resources are reserved for system usage; see the technical reference manual (TRM) for details.

Up to eight protection contexts (boot is in protection context 0) allow access privileges for memory and system resources to be set by the boot process per protection context by bus master and code privilege level.



In PSoC 64, multiple protection contexts are used to isolate the different security levels within the device. The CM0+ makes use of several of them during the boot sequence, bootloading, system calls, etc. Protection context 6 is used for the user application code that runs on the CM4 CPU. The SMPUs are set up by default and cannot be modified by the user. See section 8 in the Architecture TRM for the protection context assignment.

Memory

PSoC 6 contains flash, SRAM, ROM, and eFuse memory blocks.

Flash

There is up to 1 MB of flash; however 192 KB is reserved for system usage, leaving 832 KB for applications, organized in 256-KB sectors. There are also two 32-KB flash sectors:

- Auxiliary flash (AUXflash), typically used for EEPROM emulation
- Supervisory flash (SFlash). Data stored in SFlash includes device trim values, Flash Boot code, and encryption keys. After the device transitions into the "Secure" lifecycle stage, SFlash can no longer be changed.

The flash has 128-bit-wide accesses to reduce power. Write operations can be performed at the row level. A row is 512 bytes. Read operations are supported in both Low Power and Ultra-Low Power modes, however write operations may not be performed in Ultra-Low Power mode.

The flash controller has two caches, one for each CPU. Each cache is 8 KB, with 4-way set associativity.

SRAM

Up to 288 KB of SRAM is provided, however, 112 KB is reserved for system usage, leaving 176 KB for applications. Power control and retention granularity is implemented in 32-KB blocks allowing the user to control the amount of memory retained in Deep Sleep. Memory is not retained in Hibernate mode.

ROM

The 128-KB ROM, also referred to as the supervisory ROM (SROM), provides code (ROM Boot) for several system functions. The ROM contains device initialization, flash write, security, eFuse programming, and other system-level routines. ROM code is executed only by the CM0+ CPU, in protection context 0. A system function can be initiated by either CPU, or through the DAP. This causes an NMI in CM0+, which causes CM0+ to execute the system function.

eFuse

A one-time-programmable (OTP) eFuse array consists of 1024 bits, all of which are reserved for system use. The bits are used for storing hash values, unique IDs, or other PSoC 64 parameters.

Each fuse is individually programmed; once programmed (or "blown"), its state cannot be changed. Blowing a fuse transitions it from the default state of 0 to 1. To program an eFuse, V_{DDIO0} must be at 2.5 V ±5%, at 14 mA.

Because blowing an eFuse is an irreversible process, programming is recommended only in mass production under controlled factory conditions. For more information, see PSoC 6 MCU Programming Specifications.

Boot Code

Two blocks of code, ROM Boot and Flash Boot, are pre-programmed into the device and work together to provide device startup and configuration, basic security features, life-cycle stage management and other system functions.

ROM Boot

On a device reset, the boot code in ROM is the first code to execute. This code performs the following:

- Integrity checks of flash boot code
- Device trim setting (calibration)
- Setting the device protection units
- Setting device access restrictions for life-cycle states

ROM cannot be changed and acts as the Root of Trust in a secured system.

Flash Boot

Flash boot is a firmware module stored in SFlash and application flash. It ensures that only a validated application may run on the device. It also ensures that the firmware image has not been modified, such as by a malicious third party.

Flash boot:

- □ Is validated by ROM Boot
- □ Runs after ROM Boot and before the user application
- Enables system calls
- Enables provisioning and device policy features
- Implements RoT-based services for cryptography
- □ Provides secured storage for keys and certificates
- Validates and launches first image based on policies provisioned in the device
- Uses mbed TLS v2.24

If the user application cannot be validated, then flash boot ensures that the device is transitioned into a safe state. Refer to PSoC 64 Security section for more details.



Memory Map

Both CPUs have a fixed address map, with shared access to memory and peripherals. The 32-bit (4 GB) address space is divided into the regions shown in Table 3. Note that code can be executed from the Code and External RAM.

Table 3. Address Map for CM4 and CM0+

Address Range	Name	Use
0x0000 0000 – 0x1FFF FFFF	Code	Program code region. Data can also be placed here. It includes the exception vector table, which starts at address 0.
0x2000 0000 – 0x3FFF FFFF	SRAM	Data region. This region is not supported in PSoC 6.
0x4000 0000 – 0x5FFF FFFF	Peripheral	All peripheral registers. Code cannot be executed from this region. CM4 bit-band in this region is not supported in PSoC 6.
0x6000 0000 – 0x9FFF FFFF	External RAM	SMIF or Quad SPI, (see the QSPI Interface Serial Memory Interface (SMIF) section). Code can be executed from this region.
0xA000 0000 – 0xDFFF FFFF	External Device	Not used.
0xE000 0000 – 0xE00F FFFF	Private Peripheral Bus	Provides access to peripheral registers within the CPU core.
0xE010 0A000 – 0xFFFF FFFF	Device	Device-specific system registers.

The device memory map shown in Table 4 applies to both CPUs. That is, the CPUs share access to all PSoC 6 MCU memory and peripheral registers.

Address Range	Memory Type	Size
0x0000 0000 – 0x0001 FFFF	ROM	128 KB
0x0800 0000 – 0x0802 BFFF 0x0802 C000 - 0x0804 7FFF	Application SRAM System SRAM	Up to 176 KB 112 KB
0x1000 0000 - 0x100C FFFF 0x100D 0000 - 0x100F FFFF	Application flash Secured code flash Used for secured boot, secured bootloader, and system calls	832 KB 192 KB
0x1400 0000 - 0x1400 7FFF	Auxiliary flash, can be used for EEPROM em- ulation	32 KB
0x1600 0000 - 0x1600 7FFF	Supervisory flash, for secured access	32 KB

Note that the SRAM is located in the Arm Code region for both CPUs (see Table 3). There is no physical memory located in the CPUs' Arm SRAM regions.

System Resources

Power System

The power system provides assurance that voltage levels are as required for each respective mode and will either delay mode entry (on power-on reset (POR), for example) until voltage levels are as required for proper function or generate resets (brown-out detect (BOD)) when the power supply drops below specified levels. The design guarantees safe chip operation between power supply voltage dropping below specified levels (for example, below 1.7 V) and the reset occurring. There are no voltage sequencing requirements.

The V_{DDD} supply (1.7 to 3.6 V) powers an on-chip buck regulator or a low-dropout regulator (LDO), selectable by the user. In addition, both the buck and the LDO offer a selectable (0.9 or 1.1 V) core operating voltage (V_{CCD}). The selection lets users choose between two system power modes:

- System Low Power (LP) operates V_{CCD} at 1.1 V and offers high performance, with no restrictions on device configuration.
- System Ultra Low Power (ULP) operates V_{CCD} at 0.9 V for exceptional low power, but imposes limitations on clock speeds.

In addition, a backup domain adds an "always on" functionality using a separate power domain supplied by a backup supply (V_{BACKUP}) such as a battery or supercapacitor. It includes a real-time clock (RTC) with alarm feature, supported by a 32.768-kHz watch crystal oscillator (WCO), and power-management IC (PMIC) control. Refer to Power Supply Considerations for more details.

Power Modes

PSoC 6 MCU can operate in four system and three CPU power modes. These modes are intended to minimize the average power consumption in an application. For more details on power modes and other power-saving configuration options, see the application note, AN219528: PSoC 6 MCU Low-Power Modes and Power Reduction Techniques and the Architecture TRM, Power Modes chapter.

Power modes supported by PSoC 6 MCUs, in the order of decreasing power consumption, are:

- System Low Power (LP) All peripherals and CPU power modes are available at maximum speed
- System Ultra Low Power (ULP) All peripherals and CPU power modes are available, but with limited speed
- CPU Active CPU is executing code in system LP or ULP mode
- CPU Sleep CPU code execution is halted in system LP or ULP mode
- CPU Deep Sleep CPU code execution is halted and system Deep Sleep is requested in system LP or ULP mode
- System Deep Sleep Only low-frequency peripherals are available after both CPUs enter CPU Deep Sleep mode
- System Hibernate Device and I/O states are frozen and the device resets on wakeup



CPU Active, Sleep, and Deep Sleep are standard Arm-defined power modes supported by the Arm CPU instruction set architecture (ISA). System LP, ULP, Deep Sleep and Hibernate modes are additional low-power modes supported by PSoC 6 MCU.

Clock System

Figure 3 shows that the clock system consists of the following:

- Internal main oscillator (IMO)
- Internal low-speed oscillator (ILO)
- Precision ILO (PILO)
- Watch crystal oscillator (WCO)
- External MHz crystal oscillators (ECOs) for the system and the Bluetooth LE subsystem
- External clock input
- Phase-locked loop (PLL)
- Frequency-locked loop (FLL)

Clocks may be buffered and brought out to a pin on a smart I/O port.

The default clocking when the application starts is CLK_HF[0] being driven by the IMO and the FLL. CLK_HF[0], clk_fast, clk_peri, and clk_slow are all either 50 MHz (LP mode) or 25 MHz (ULP mode). All other clocks, including all peripheral clocks, are off.

Internal Main Oscillator (IMO)

The IMO is the primary source of internal clocking. It is trimmed during testing to achieve the specified accuracy. The IMO default frequency is 8 MHz and tolerance is $\pm 2\%$.

Internal Low-speed Oscillator (ILO)

The ILO is a very low power oscillator, nominally 32 kHz, which operates in all power modes. The ILO can be calibrated against a higher accuracy clock for better accuracy.

Precision ILO (PILO)

PILO is a 32.768-kHz clock that can provide a more accurate clock than ILO when periodically calibrated using a high-accuracy clock such as the ECO.

Yellow multiplexer are glitch safe Path Mux (FLL/PLL) Root mux clk_fast Divide CM4 Predivide CLK_HF[0] (1/2/4/8) Peripheral FLL IMO >> dsi_in0 clk_peri Peripheral Clock Dividers clocks Divide TCPWM EXTCLK 🛛 SCB Predivide CLK_HF[1] clk slow PLL Audio CM0+ Divider (1/2/4/8) dsi in1 ECO CapSense AHB CLK PATH2 ALTHF Predivider CLK_HF[2] OSPI/SMIE UDB (1/2/4/8) DMA dsi in2 CLK PATH3 dsi out <1:0> LCD eFuse CLK_HF[3] Predivider USB Analog (1/2/4/8) CLK PATH4 dsi in3 MMIO Subsyster tD Smart I/O PPU Predivide CLK_HF[4] D clk_ext System LP/ULP Domain (1/2/4/8) dsi_in4 System Deep Sleep Crypto Hibernate Domain ILO* CLK_LF WCO* *Works in Hibernate

Figure 3. Clocking Diagram

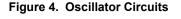
PILO

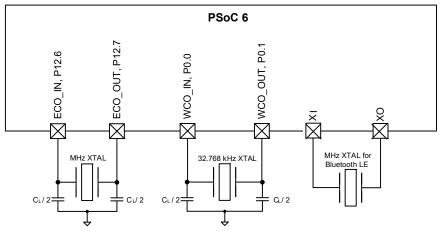


External Crystal Oscillators

TRM Figure 4 shows all of the external crystal oscillator circuits for this product line. The component values shown are typical; check the ECO Specifications for the crystal values, and the crystal datasheet for the load capacitor values. The ECO and

WCO require balanced external load capacitors. The Bluetooth LE oscillator does not require external load capacitors. For more information, see the TRM and AN218241, PSoC 6 MCU Hardware Design Considerations.





If the ECO is used, note that its performance is affected by GPIO switching noise. GPIO ports should be used as Table 5 shows. See also Table 6 for additional restrictions for general analog subsystem use.

Table 5. ECO Osage Guidennes			
Ports	Max Frequency	Drive Strength for $V_{DDD} \le 2.7 V$	Drive Strength for $V_{DDD} > 2.7 V$
Port 11	60 MHz for SMIF (QSPI)	DRIVE_SEL 2	DRIVE_SEL 3
Ports 12 and 13	Slow slew rate setting	No restrictions	No restrictions

Table 5 ECO Usage Guidelines

Watchdog Timers (WDT, MCWDT)

PSoC 6 MCU has one WDT and two multi-counter WDTs (MCWDTs). The WDT has a 16-bit free-running counter. Each MCWDT has two 16-bit counters and one 32-bit counter, with multiple operating modes. All of the 16-bit counters can generate a watchdog device reset. All of the counters can generate an interrupt on a match event.

The WDT is clocked by the ILO. It can do interrupt/wakeup generation in system LP/ULP, Deep Sleep, and Hibernate power modes. The MCWDTs are clocked by LFCLK (ILO or WCO). It can do periodic interrupt/wakeup generation in system LP/ULP and Deep Sleep power modes.

Clock Dividers

Integer and fractional clock dividers are provided for peripheral use and timing purposes. There are:

- Eight 8-bit clock dividers
- Sixteen 16-bit integer clock dividers
- Four 16.5-bit fractional clock dividers
- One 24.5-bit fractional clock divider

Trigger Routing

PSoC 6 MCU contains a trigger multiplexer block. This is a collection of digital multiplexers and switches that are used for routing trigger signals between peripheral blocks and between GPIOs and peripheral blocks.

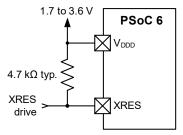
There are two types of trigger routing. Trigger multiplexers have reconfigurability in the source and destination. There are also hardwired switches called "one-to-one triggers", which connect a specific source to a destination. The user can enable or disable the route.

Reset

PSoC 6 MCU can be reset from a variety of sources:

- Power-on reset (POR) to hold the device in reset while the power supply ramps up to the level required for the device to function properly. POR activates automatically at power-up.
- Brown-out detect (BOD) reset to monitor the digital voltage supply V_{DDD} and generate a reset if V_{DDD} falls below the minimum required logic operating voltage.
- External reset dedicated pin (XRES) to reset the device using an external source. The XRES pin is active low. It can be connected either to a pull-up resistor to V_{DDD}, or to an active drive circuit, as Figure 5 shows. If a pull-up resistor is used, select its value to minimize current draw when the pin is pulled low; 4.7 k Ω to 100 k Ω is typical.

Figure 5. XRES Connection Diagram





- Watchdog timer (WDT or MCWDT) to reset the device if firmware fails to service it within a specified timeout period.
- Software-initiated reset to reset the device on demand using firmware.
- Logic-protection fault can trigger an interrupt or reset the device if unauthorized operating conditions occur; for example, reaching a debug breakpoint while executing privileged code.
- Hibernate wakeup reset to bring the device out of the system Hibernate low-power mode.

Reset events are asynchronous and guarantee reversion to a known state. Some of the reset sources are recorded in a register, which is retained through reset and allows software to determine the cause of the reset.

Bluetooth LE Radio and Subsystem

This product line incorporates a Bluetooth LE subsystem that contains the Physical Layer (PHY) and Link Layer (LL) engines with an embedded security engine. Cypress also provides extensive driver library and middleware support for Bluetooth LE; see ModusToolbox Software.

The physical layer consists of the digital PHY and the RF transceiver that transmits and receives Gaussian frequency shift keying (GFSK) packets at 2 Mbps over a 2.4-GHz ISM band, which is compliant with Bluetooth LE Specification 5.0.

The baseband controller is a composite hardware and firmware implementation that supports both master and slave modes. Key protocol elements, such as HCI and link control, are implemented in firmware. Time-critical functional blocks, such as encryption, CRC, data whitening, and access code correlation, are implemented in hardware (in the LL engine).

The RF transceiver contains an integrated balun, which provides a single-ended RF port pin to drive a 50- Ω antenna via a matching/filtering network. In the receive direction, this block converts the RF signal from the antenna to a digital bit stream after performing GFSK demodulation. In the transmit direction, this block performs GFSK modulation and then converts a digital baseband signal to a radio frequency before transmitting it through the antenna.

Key features, implemented in hardware and firmware, are as follows:

- Master and slave single-mode protocol stack with logical link control and adaptation protocol (L2CAP), attribute (ATT), and security manager (SM) protocols
- API access to generic attribute profile (GATT), generic access profile (GAP), and L2CAP
- L2CAP connection-oriented channel (Bluetooth 4.1 feature)
- GAP features
 - D Broadcaster, Observer, Peripheral, and Central roles
 - □ Security Mode 1: Level 1, 2, 3, and 4; Security Mode 2: Level 1 and 2
 - User-defined advertising data
- Multiple bond support
- GATT features
 - □ GATT Client and Server
 - □ Supports GATT sub-procedures
 - □ 32-bit universally unique identifier (UUID) (Bluetooth 4.1 feature)
- Security Manager (SM)
 - Dearing methods: Just works, Passkey Entry, and Out of Band
- □ LE Secure Connection Pairing model
- Authenticated man-in-the-middle (MITM) protection and data signing
- Link Layer (LL)
 - Master and Slave roles
 - □ 128-bit AES engine
- □ Low-duty cycle advertising
- LE Ping
- LL privacy 1.2 (Bluetooth 4.2 feature)
- □ Data length extension (Bluetooth 4.2 feature)
- Supports all SIG-adopted Bluetooth LE profiles

Power consumption for Advertisement (1.28s, 31-byte packets, 0 dBm TX output power) and Connection (300 ms, 0-byte packets, 0 dBm TX output power) are 42 μW and 70 μW respectively



Programmable Analog Subsystem

12-bit SAR ADC

The 12-bit, 1-Msps SAR ADC can operate at a maximum clock rate of 18 MHz and requires a minimum of 18 clocks at that frequency to do a 12-bit conversion. One of three internal references may be used for the ADC reference voltage: V_{DDA} , $V_{DDA/2}$, and an analog reference (AREF). AREF is nominally 1.2 V, trimmed to ±1%; see Table 23. An external reference may also be used, by driving the V_{REF} pin. When using $V_{DDA/2}$ or AREF as a reference, an external bypass capacitor may be connected to the V_{REF} pin to improve performance in noisy conditions. These reference options allow ratio-metric readings or absolute readings at the accuracy of the reference used. The input range of the ADC is the full supply voltage between V_{SS} and V_{DDA}/V_{DDIOA} . The SAR ADC may be configured with a mix of single-ended and differential signals in the same configuration.

The SAR ADC's sample-and-hold (S/H) aperture is programmable to allow sufficient time for signals with a high impedance to settle sufficiently, if required. System performance will be 65 dB for true 12-bit precision provided appropriate references are used and system noise levels permit it.

The SAR is connected to a fixed set of pins through an input multiplexer. The multiplexer cycles through the selected channels autonomously (sequencer scan) and does so with zero switching overhead (that is, the aggregate sampling bandwidth is equal to 1 Msps whether it is for a single channel or distributed over several channels). The result of each channel is buffered, so that an interrupt may be triggered only when a full scan of all channels is complete. Also, a pair of range registers can be set to detect and cause an interrupt if an input exceeds a minimum and/or maximum value. This allows fast detection of out-of-range values without having to wait for a sequencer scan to be completed and the CPU to read the values and check for out-of-range values in software. The SAR can also be connected, under firmware control, to most other GPIO pins via the Analog Multiplexer Bus (AMUXBUS). The SAR is not available in Deep Sleep and Hibernate modes as it requires a high -speed clock (up to 18 MHz). The SAR operating range is 1.71 to 3.6 V.

ADC accuracy is affected by GPIO switching noise. To improve accuracy, implement the GPIO port restrictions listed in Table 6. In addition, there should be no switching outputs on ports 9 and 10.

Temperature Sensor

An on-chip temperature sensor is part of the SAR and may be scanned by the SAR ADC. It consists of a diode, which is biased by a current source that can be disabled to save power. The temperature sensor may be connected directly to the SAR ADC as one of the measurement channels. The ADC digitizes the temperature sensor's output and a Cypress-supplied software function may be used to convert the reading to temperature which includes calibration and linearization.

12-bit Digital-Analog Converter

There is a 12-bit voltage mode DAC on the chip, which can settle in less than 2 μ s. The DAC may be driven by the DMA controllers to generate user-defined waveforms. The DAC output from the chip can either be the resistive ladder output (highly linear near ground) or a buffered output using an opamp in the CTBm block.

Continuous Time Block mini (CTBm) with Two Opamps

This block consists of two opamps, which have their inputs and outputs connected to pins and other analog blocks, as Figure 6 shows. They have three power modes (high, medium, and low) and a comparator mode. The opamps can be used to buffer SAR inputs and DAC outputs. The non-inverting inputs of these opamps can be connected to either of two pins, thus allowing independent sensors to be used at different times. The pin selection can be made via firmware.

The opamps also support operation in system Deep Sleep mode, with lower performance and reduced power consumption.

Low-Power Comparators

Two low-power comparators are provided, which can operate in all power modes. This allows other analog system resources to be disabled while retaining the ability to monitor external voltage levels during system Deep Sleep and Hibernate modes. The comparator outputs are normally synchronized to avoid metastability unless operating in an asynchronous power mode (Hibernate) where the system wake-up circuit is activated by a comparator-switch event.



Figure 6 shows an overview of the analog subsystem. This diagram is a high-level abstraction. See the Architecture TRM for detailed connectivity information.

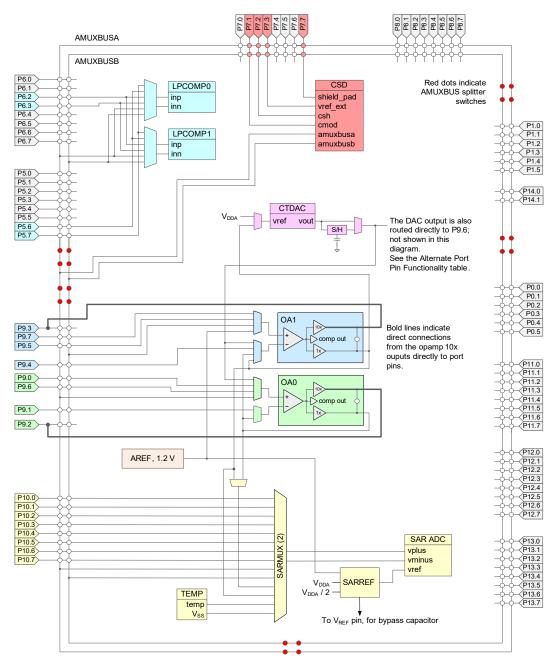


Figure 6. Analog Subsystem



Programmable Digital

Smart I/O

Smart I/O is a programmable logic fabric that enables Boolean operations on signals traveling from device internal resources to the GPIO pins or on signals traveling into the device from external sources. A Smart I/O block sits between the GPIO pins and the high-speed I/O matrix (HSIOM) and is dedicated to a single port.

There are two Smart I/O blocks: one on Port 8 and one on Port 9. When Smart I/O is not enabled, all signals on Port 8 and Port 9 bypass the Smart I/O hardware.

Smart I/O supports:

- System Deep Sleep operation
- Boolean operations without CPU intervention
- Asynchronous or synchronous (clocked) operation

Each Smart I/O block contains a data unit (DU) and eight lookup tables (LUTs).

The DU:

- Performs unique functions based on a selectable opcode.
- Can source input signals from internal resources, the GPIO port, or a value in the DU register.

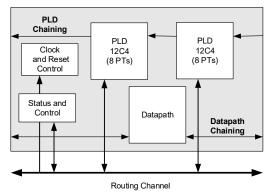
Each LUT:

- Has three selectable input sources. The input signals may be sourced from another LUT, an internal resource, an external signal from a GPIO pin, or from the DU.
- Acts as a programmable Boolean logic table.
- Can be synchronous or asynchronous.

Universal Digital Blocks (UDBs)

This product line has 12 UDBs. Each UDB is a collection of uncommitted logic (PLD) and nano-CPU (datapath) optimized to create common embedded peripherals and custom functionality, as Figure 7 shows. UDB datapaths are 8 bits wide, and can be chained to form 16, 24, and 32-bit functions. Included with the UDBs is the digital system interconnect (DSI), which routes signals among UDBs, fixed function peripherals, I/O pins and other system blocks to implement full featured device connectivity. The DSI enables routing between any digital function and any pin. Port adapter blocks extend the UDBs to provide an interface to the GPIOs through the HSIOM.

Figure 7. UDB Block Diagram



Fixed-Function Digital

Timer/Counter/Pulse-width Modulator (TCPWM) Block

- The TCPWM supports the following operational modes:
 - Timer-counter with compare
 - □ Timer-counter with capture
 - Quadrature decoding
 - Pulse width modulation (PWM)
 - Pseudo-random PWM
 - PWM with dead time
- Up, down, and up/down counting modes.
- Clock prescaling (division by 1, 2, 4, ... 64, 128)
- Double buffering of compare/capture and period values
- Underflow, overflow, and capture/compare output signals
- Supports interrupt on:
 - Terminal count Depends on the mode; typically occurs on overflow or underflow
 - Capture/compare The count is captured to the capture register or the counter value equals the value in the compare register
- Complementary output for PWMs
- Selectable start, reload, stop, count, and capture event signals for each TCPWM; with rising edge, falling edge, both edges, and level trigger options. The TCPWM has a Kill input to force outputs to a predetermined state.

In this device there are:

- Eight 32-bit TCPWMs
- Twenty-four 16-bit TCPWMs

Serial Communication Blocks (SCB)

This product line has nine SCBs:

- Eight can implement either I²C, UART, or SPI.
- One SCB (SCB #8) can operate in system Deep Sleep mode with an external clock; this SCB can be either SPI slave or I²C slave.

I²C Mode: The SCB can implement a full multi-master and slave interface (it is capable of multimaster arbitration). This block can operate at speeds of up to 1 Mbps (Fast Mode Plus). It also supports EZI2C, which creates a mailbox address range and effectively reduces I²C communication to reading from and writing to an array in the memory.The SCB supports a 256-byte FIFO for receive and transmit.

The I²C peripheral is compatible with I²C standard-mode, Fast Mode, and Fast Mode Plus devices as defined in the NXP I²C-bus specification and user manual (UM10204). The I²C bus I/O is implemented with GPIO in open-drain modes.

UART Mode: This is a full-feature UART operating at up to 8 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows the addressing of peripherals connected over common Rx and Tx lines. Common UART functions such as parity error, break detect, and frame error are supported. A 256-byte FIFO allows much greater CPU service latencies to be tolerated.



SPI Mode: The SPI mode supports full Motorola SPI, TI Secure Simple Pairing (SSP) (essentially adds a start pulse that is used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block supports an EZSPI mode in which the data interchange is reduced to reading and writing an array in memory. The SPI interface operates with a 25-MHz clock.

USB Full-Speed Device Interface

PSoC 6 incorporates a full-speed USB device interface. The device can have up to eight endpoints. A 512-byte SRAM buffer is provided and DMA is supported.

Note: If the USB pins are not used, connect V_{DDUSB} to ground and leave the P14.0/USBDP and P14.1/USBDM pins unconnected.

QSPI Interface Serial Memory Interface (SMIF)

A serial memory interface is provided, running at up to 80 MHz. It supports single, dual, quad, dual-quad and octal SPI configurations, and supports up to four external memory devices. It supports two modes of operation:

- Memory-mapped I/O (MMIO), a command mode interface that provides data access via the SMIF registers and FIFOs
- Execute in Place (XIP), in which AHB reads and writes are directly translated to SPI read and write transfers.

In XIP mode, the external memory is mapped into the PSoC 6 MCU internal address space, enabling code execution directly from the external memory. To improve performance, a 4-KB cache is included. XIP mode also supports AES-128 on-the-fly encryption and decryption, enabling secured storage and access of code and data in the external memory.

LCD

This block drives LCD commons and segments; routing is available to most of the GPIOs. One to eight of the GPIOs must be used for commons, the rest can be used for segments.

The LCD block has two modes of operation: high speed (8 MHz) and low speed (32 kHz). Both modes operate in system LP and ULP modes. Low-speed mode operates with reduced contrast in system Deep Sleep mode - review the number of common and segment lines, viewing angle requirements, and prototype performance before using this mode.

GPIO

This product line has up to 84 GPIOs, which implement:

- Eight drive strength modes:
- Analog input mode (input and output buffers disabled)
 Input only
- Weak pull-up with strong pull-down
- □ Strong pull-up with weak pull-down
- □ Open drain with strong pull-down
- Open drain with strong pull-up
- □ Strong pull-up with strong pull-down
- □ Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL)
- Hold mode for latching previous state (used for retaining the I/O state in system Hibernate mode)
- Selectable slew rates for dV/dt-related noise control to improve EMI

The pins are organized in logical entities called ports, which are up to 8 pins in width. Data output and pin state registers store, respectively, the values to be driven on the pins and the input states of the pins.

Every pin can generate an interrupt if enabled; each port has an interrupt request (IRQ) associated with it.

The port 1 pins are capable of overvoltage-tolerant (OVT) operation, where the input voltage may be higher than V_{DDD} . OVT pins are commonly used with I²C, to allow powering the chip OFF while maintaining a physical connection to an operating I²C bus without affecting its functionality.

GPIO pins can be ganged to source or sink higher values of current. GPIO pins, including OVT pins, may not be pulled up higher than the absolute maximum; see Electrical Specifications.

During power-on and reset, the pins are forced to the analog input drive mode, with input and output buffers disabled, so as not to crowbar any inputs and/or cause excess turn-on current.

A multiplexing network known as the high-speed I/O matrix (HSIOM) is used to multiplex between various peripheral and analog signals that may connect to an I/O pin.

Analog performance is affected by GPIO switching noise. In order to get the best analog performance, the following frequency and drive mode constraints must be applied. The DRIVE_SEL values (refer to Table 6) represent drive strengths (see the Architecture and Register TRMs for further detail).

See also Table 5 for additional restrictions for ECO use.

Table 6.	DRIVE	SEL	Values

Ports	Max Frequency	Drive Strength for $V_{DDD} \le 2.7 V$	Drive Strength for V_{DDD} > 2.7 V
Port 0	8 MHz	DRIVE_SEL 2	DRIVE_SEL 3
Port 1	1 MHz; slow slew rate, 2 outputs max		
Ports 5 to 10	16 MHz; 25 MHz for SPI		
Ports 11 to 13	80 MHz for SMIF (QSPI).	DRIVE_SEL 1	DRIVE_SEL 2
Ports 9 and 10	8 MHz; slow slew rate setting for TQFP Packages for ADC performance	No restrictions	No restrictions



Special-Function Peripherals

Audio Subsystem

This subsystem consists of the following hardware blocks:

- One Inter-IC Sound (I²S) interface
- Two pulse-density modulation (PDM) to pulse-code modulation (PCM) decoder channels

The I^2S interface implements two independent hardware FIFO buffers – TX and RX, which can operate in master or slave mode. The following features are supported:

- Multiple data formats I²S, left-justified, Time Division Multiplexed (TDM) mode A, and TDM mode B
- Programmable channel/word lengths 8/16/18/20/24/32 bits
- Internal/external clock operation. Up to 192 ksps
- Interrupt mask events trigger, not empty, full, overflow, underflow, watchdog
- Configurable FIFO trigger level with DMA support

The I^2S interface is commonly used to connect with audio codecs, simple DACs, and digital microphones.

The PDM-to-PCM decoder implements a single hardware Rx FIFO that decodes a stereo or mono 1-bit PDM input stream to PCM data output. The following features are supported:

- Programmable data output word length 16/18/20/24 bits
- Programmable gain amplifier (PGA) for volume control from -12 dB to +10.5 dB in 1.5 dB steps
- Configurable PDM clock generation. Range from 384 kHz to 3.072 MHz
- Droop correction and configurable decimation rate for sampling; up to 48 ksps
- Programmable high-pass filter gain
- Interrupt mask events not empty, overflow, trigger, underflow
- Configurable FIFO trigger level with DMA support

The PDM-to-PCM decoder is commonly used to connect to digital PDM microphones. Up to two microphones can be connected to the same PDM Data line.

CapSense Subsystem

CapSense is supported in PSoC 6 MCU through a CapSense sigma-delta (CSD) hardware block. It is designed for high-sensitivity self-capacitance and mutual-capacitance measurements, and is specifically built for user interface solutions.

In addition to CapSense, the CSD hardware block supports three general-purpose functions. These are available when CapSense is not being used. Alternatively, two or more functions can be time-multiplexed in an application under firmware control. The four functions supported by the CSD hardware block are:

- CapSense
- 10-bit ADC
- Programmable current sources (IDAC)
- Comparator

CapSense

Capacitive touch sensors are designed for user interfaces that rely on human body capacitance to detect the presence of a finger on or near a sensor. Cypress CapSense solutions bring elegant, reliable, and simple capacitive touch sensing functions to applications including IoT, industrial, automotive, and home appliances.

The Cypress-proprietary CapSense technology offers the following features:

- Best-in-class signal-to-noise ratio (SNR) and robust sensing under harsh and noisy conditions
- Self-capacitance (CSD) and mutual-capacitance (CSX) sensing methods
- Support for various widgets, including buttons, matrix buttons, sliders, touchpads, and proximity sensors
- High-performance sensing across a variety of materials
- Best-in-class liquid tolerance
- SmartSense auto-tuning technology that helps avoid complex manual tuning processes
- Superior immunity against external noise
- Spread-spectrum clocks for low radiated emissions
- Gesture and built-in self-test libraries
- Ultra-low power consumption
- An integrated graphical CapSense tuner for real-time tuning, testing, and debugging

CapSense sensitivity and accuracy are affected by GPIO switching noise. To improve sensitivity and accuracy, implement the GPIO port restrictions listed in Table 6, and do the following:

- Restrict CapSense pins to ports 6 and 7
- There should be no other GPIO output activity on ports 6 and 7
- There should be no more than two GPIO outputs on ports 5 and 8
- Restrict GPIO output switching in ports 5 and 8 to 1 MHz, with slow slew rate setting

ADC

The CapSense subsystem slope ADC offers the following features:

- Selectable 8- or 10-bit resolution
- \blacksquare Selectable input range: GND to V_{REF} and GND to V_{DDA} on any GPIO input
- Measurement of V_{DDA} against an internal reference without the use of GPIO or external components

IDAC

The CSD block has two programmable current sources, which offer the following features:

- 7-bit resolution
- Sink and source current modes
- A current source programmable from 37.5 nA to 609 µA
- Two IDACs that can be used in parallel to form one 8-bit IDAC



Comparator

The CapSense subsystem comparator operates in the system Low Power and Ultra-Low Power modes. The inverting input is connected to an internal programmable reference voltage and the non-inverting input can be connected to any GPIO via the AMUXBUS.

CapSense Hardware Subsystem

Figure 8 shows the high-level hardware overview of the CapSense subsystem, which includes a delta sigma converter, internal clock dividers, a shield driver, and two programmable current sources.

The inputs are managed through analog multiplexed buses (AMUXBUS A/B). The input and output of all functions offered by the CSD block can be provided on any GPIO or on a group of GPIOs under software control, with the exception of the comparator output and external capacitors that use dedicated GPIOs.

Self-capacitance is supported by the CSD block using AMUXBUS A, an external modulator capacitor, and a GPIO for each sensor. There is a shield electrode (optional) for self-capacitance sensing. This is supported using AMUXBUS B and an optional external shield tank capacitor (to increase the drive capability of the shield driver) should this be required. Mutual-capacitance is supported by the CSD block using AMUXBUS A, two external integrated capacitors, and a GPIO for transmit and receive electrodes.

The ADC does not require an external component. Any GPIO that can be connected to AMUXBUS A can be an input to the ADC under software control. The ADC can accept V_{DDA} as an input without needing GPIOs (for applications such as battery voltage measurement).

The two programmable current sources (IDACs) in general-purpose mode can be connected to AMUXBUS A or B. They can therefore connect to any GPIO pin. The comparator resides in the delta-sigma converter. The comparator inverting input can be connected to the reference. Both comparator inputs can be connected to any GPIO using AMUXBUS B; see Figure 8. The reference has a direct connection to a dedicated GPIO; see Table 9.

The CSD block can operate in active and sleep CPU power modes, and seamlessly transition between system LP and ULP modes. It can be powered down in system Deep Sleep and Hibernate modes. Upon wakeup from Hibernate mode, the CSD block requires re-initialization. However, operation can be resumed without re-initialization upon exit from Deep Sleep mode, under firmware control.

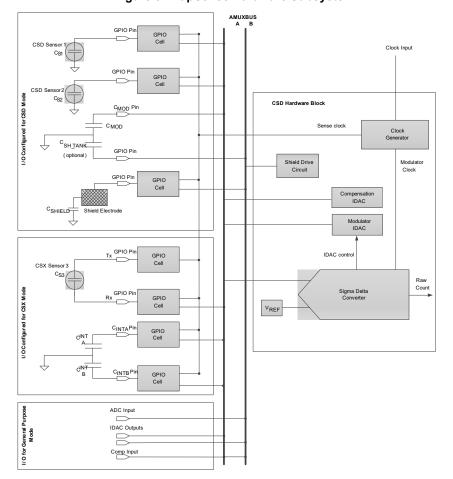


Figure 8. CapSense Hardware Subsystem



Figure 9 shows the high-level software overview. Cypress provides middleware libraries for CapSense, ADC, and IDAC on GitHub to enable quick integration. The Board Support Package for any kit with CapSense capabilities automatically includes the CapSense library in any application that uses the BSP.

User applications interact only with middleware to implement functions of the CSD block. The middleware interacts with underlying drivers to access hardware as necessary. The CSD driver facilitates time-multiplexing of the CSD hardware if more than one piece of CSD-related middleware is present in a project. It prevents access conflicts in this case.

ModusToolbox Software provides a CapSense configurator to enable fast library configuration. It also provides a tuner for performance evaluation and real-time tuning of the system. The tuner requires an EZI2C communication interface in the application to enable real-time tuning capability. The tuner can update configuration parameters directly in the device as well as in the configurator. CapSense and ADC middleware use the CSD interrupt to implement non-blocking sensing and A-to-D conversion. Therefore, interrupt service routines are a defined part of the middleware, which must be initialized by the application. Middleware and drivers can operate on either CPU. Cypress recommends using the middleware only in one CPU. If both CPUs must access the CSD driver, memory access should be managed in the application.

Refer to AN85951: PSoC 4 and PSoC 6 MCU CapSense Design Guide for more details on CSX sensing, CSD sensing, shield electrode usage and its benefits, and capacitive system design guidelines.

Refer to the API reference guides for CapSense, ADC, and IDAC available on GitHub.

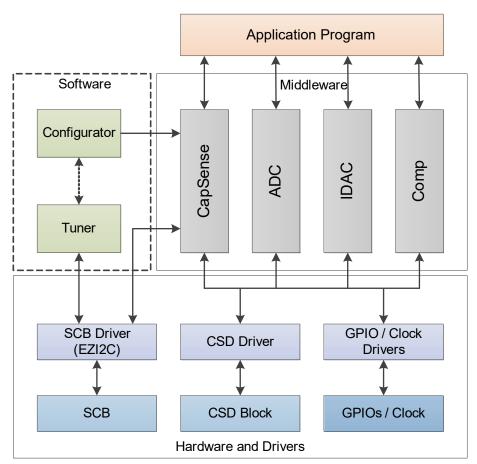


Figure 9. CapSense Software/Firmware Subsystem



PSoC 64 Security

All PSoC 64 "Secure Boot" MCU product lines feature enhanced security functionality. They provide an isolated root of trust (RoT) with true attestation and provisioning services. Cypress also provides a "Secure Boot" SDK User Guide, which includes all required libraries, tools, and sample code to provision PSoC 64 devices. The SDK also provides provisioning scripts with sample keys and policies, a pre-built bootloader image, and tools for signing firmware images. For more information, see the "Secure Boot" SDK User Guide.

The "Secure Boot" SDK also includes entrance exam scripts. An entrance exam can optionally be run on PSoC 64 devices before provisioning to help ensure that no device tampering has occurred.

The first step in using a PSoC 64 device is to inject the following information into the device - a process called provisioning:

- A set of cryptographic public keys, which are used to:
 Transfer the RoT from Cypress to the user/OEM, as Figure 10 shows
 - Validate applications
- A set of security policies that define how the device should behave
- Certificates (optional) used to bind device identity or provide a chain of trust to a higher certifying authority
- The Cypress bootloader

Provisioning is done before an application is programmed into the device.

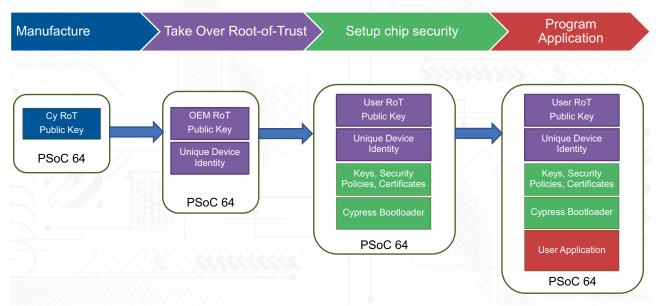


Figure 10. PSoC 64 Usage Processes

Provisioning is done using a hardware security module (HSM). An HSM is a physical computing device, placed in a secured facility, that safeguards and manages digital keys for strong authentication, and provides cryptographic processing.

After the device is provisioned, it can be programmed with signed applications. The signature and authenticity of the application is verified before control is transferred to it.



Figure 11 shows a simplified flash memory map of PSoC 64 assets and immutable sections. As noted in Memory, a portion of device SRAM is also reserved for system usage.

Figure 11. PSoC 64 "Secure" MCU Asset Memory Map

	0x1000:0000	
User Application Space		
	0x101D:0000	Typically immutable, can be
Cypress Bootloader	0,1010,0000	 updated if allowed by security policy during provisioning
"Secure Flash Boot"	0x101E:0000	Immutable after Cypress Manufacturing
OEM Asset storage	0x101F:BF00	Typically immutable, can be
User Flash	0x101F:FFFF	 partially updated if allowed by security policy during provisioning
"Secure Flash Boot" + Cypress Public Key	0x1600:7FFF	
Supervisory Flash	0x1600:0000	
Boot ROM	0x0001:FFFF	Immutable after Cypress Manufacturing
ROM	0x0000:0000	



Cypress Bootloader

The Cypress Bootloader is a port of the open source MCUBoot library. For more details about this library, refer to MCUBoot Bootloader design. The current version of The Cypress Bootloader for this device does not support the swap-based images feature as documented in the MCUBoot design document.

The Cypress Bootloader is included in the "Secure Boot" SDK as a pre-built hex image. This image acts as the first image launched by the PSoC 64 boot code. It parses the provisioned Boot&Upgrade policy to launch an application image. The Cypress Bootloader supports external memory over the PSoC 64 Serial Memory Interface (SMIF). The bootloader currently supports only external memory vendors who support the Serial Flash Discovery Protocol (SFDP).

The Cypress Bootloader enforces protection contexts for the bootloader code, so code running in another protection context may be prohibited from overwriting/tampering with the bootloader code. Figure 12 shows the launch sequence of the Cypress Bootloader:

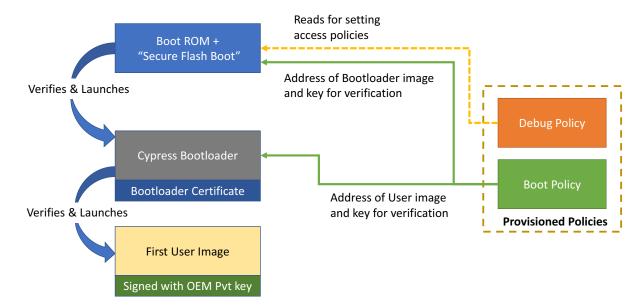
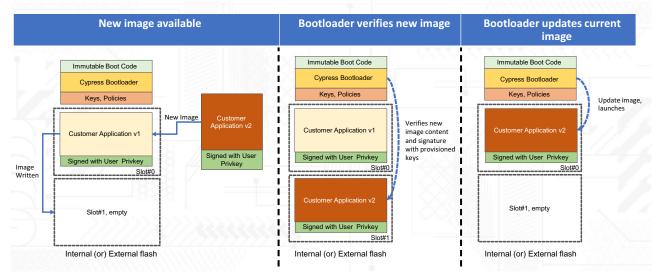


Figure 12. Bootloader Launch Sequence

Figure 13 shows a typical application update scenario using the Cypress Bootloader.

Figure 13. Bootloader Application Update Sequence





Pinouts

Note: TheCYB06447BZI-BLDx Datasheet web page contains a spreadsheet with a consolidated list of pinouts and pin alternate functions with HSIOM mapping.

GPIO ports are powered by V_{DDx} pins as follows:

- P0: V_{BACKUP}
- P1: V_{DDD}. Port 1 pins are overvoltage tolerant (OVT).
- P5, P6, P7, P8: V_{DDIO1}
- P9, P10: V_{DDIOA}, V_{DDA} (V_{DDIOA}, when present, and V_{DDA} must be connected together on the PCB)
- P11, P12, P13: V_{DDIO0}
- P14: V_{DDUSB}

Din	Packages		
Pin	124-BGA	116-BGA	
V _{DDD}	A13	B1	
V _{CCD}	B13	A2	
V _{DDA}	M13	A9	
V _{DDIOA}	N13	-	
V _{DDIO0}	D11	B3	
V _{DDIO1}	M4	G10	
VBACKUP	A10	C1	
V _{DDUSB}	A2	-	
V _{SS}	C11, D4, D10, K4, K10, M12	B2, B9, D1, H2, H9	
V _{SSR}	A1, B1, B2, C3, D1, E3, G2	J1, K2, K3, K4, K5, L1, L3, L4, L5, M3, M8	
V _{DD_NS}	A5	H3	
V _{IND1}	B5	F1	
V _{IND2}	B4	G1	
V _{BUCK1}	C4	G2	
V _{RF}	A4	H1	
V _{DCDC}	F3	M7	
V _{DDR1}	C2	L2	
V _{DDR2}	E2	M1	
V _{DDR3}	D2	M2	
DV _{DD}	F2	M6	
V _{DDR_HVL}	G3	L7	
XRES	A8	E2	
V _{REF}	N12	B10	
ANT	C1	К1	
XI	F1	M4	
XO	E1	M5	
P0.0	C9	C2	
P0.1	B9	D3	
P0.2	A9	E4	
P0.3	C8	E3	
P0.4	B8	F3	
P0.5	C7	D2	

Table 7. Packages and Pin Information



Table 7. Packages and Pin Information (continued)

D .		Packages
Pin –	124-BGA	116-BGA
P1.0	B7	G3
P1.1	A7	F2
P1.2	C6	J5
P1.3	B6	J4
P1.4	A6	J3
P1.5	C5	J2
P5.0	G1	L6
P5.1	H3	K6
P5.2	H2	J6
P5.3	H1	К7
P5.4	J3	J7
P5.5	J2	L8
P5.6	J1	M9
P5.7	K1	-
P6.0	K2	К8
P6.1	К3	J8
P6.2	L3	L9
P6.3	L2	К9
P6.4	L1	J9
P6.5	M2	M10
P6.6	M1	L10
P6.7	N2	K10
P7.0	N3	J10
P7.1	M3	H10
P7.2	N4	Н8
P7.3	N1	H7
P7.4	L4	H6
P7.5	N5	G9
P7.6	M5	G8
P7.7	L5	G7
P8.0	N6	F10
P8.1	M6	F9
P8.2	L6	F8
P8.3	N7	F7
P8.4	M7	G6
P8.5	L7	E9
P8.6	N8	E8
P8.7	M8	E7
P9.0	L9	D10
P9.1	M9	D9
P9.2	N9	D8
P9.3	L8	D7
P9.4	N10	C10
P9.5	M10	C9
P9.6	L10	C8



Table 7. Packages and Pin Information (continued)

Pin		Packages
	124-BGA	116-BGA
P9.7	N11	C7
P10.0	M11	B8
P10.1	L13	A8
P10.2	L12	F6
P10.3	L11	E6
P10.4	K13	D6
P10.5	K12	B7
P10.6	K11	A7
P10.7	J13	-
P11.0	J12	F5
P11.1	J11	E5
P11.2	H13	D5
P11.3	H12	C6
P11.4	H11	B6
P11.5	G13	A6
P11.6	G12	B5
P11.7	G11	A5
P12.0	F13	A4
P12.1	F12	B4
P12.2	F11	C4
P12.3	E13	A3
P12.4	E12	C5
P12.5	E11	D4
P12.6	D13	G5
P12.7	D12	H5
P13.0	A12	H4
P13.1	C13	G4
P13.2	C12	-
P13.3	B12	-
P13.4	B11	-
P13.5	A11	-
P13.6	C10	F4
P13.7	B10	C3
P14.0 / USBDP	B3	-
P14.1 / USBDM	A3	-
NC	D3	-

Note: If the USB pins are not used, connect V_{DDUSB} to ground and leave the P14.0/USBDP and P14.1/USBDM pins unconnected.





Each Port Pin has multiple alternate functions. These are defined in Table 8.

Table 8. Multiple Alternate Functions^[1]

Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P0.0	tcpwm[0].li ne[0]:0	tcpwm[1].lin e[0]:0		srss.ext_ clk:0				scb[0].spi_ select1:0			peri.tr_io_in put[0]:0						
P0.1	tcpwm[0].li ne_compl[0]:0	tcpwm[1].lin e_compl[0]: 0						scb[0].spi_ select2:0			peri.tr_io_in put[1]:0					cpuss.swj_ trstn	
P0.2	tcpwm[0].li ne[1]:0	tcpwm[1].lin e[1]:0				scb[0].uart _rx:0	scb[0].i2c _scl:0	scb[0].spi_ mosi:0									
P0.3	tcpwm[0].li ne_compl[1]:0	tcpwm[1].lin e_compl[1]: 0				scb[0].uart _tx:0	scb[0].i2c _sda:0	scb[0].spi_ miso:0									
P0.4	tcpwm[0].li ne[2]:0	tcpwm[1].lin e[2]:0				scb[0].uart _rts:0		scb[0].spi_ clk:0				peri.tr_io_ output[0]:2					
P0.5	tcpwm[0].li ne_compl[2]:0	tcpwm[1].lin e_compl[2]: 0		srss.ext_ clk:1		scb[0].uart _cts:0		scb[0].spi_ select0:0				peri.tr_io_ output[1]:2					
P1.0	tcpwm[0].li ne[3]:0	tcpwm[1].lin e[3]:0				scb[7].uart _rx:0	scb[7].i2c _scl:0	scb[7].spi_ mosi:0			peri.tr_io_in put[2]:0						
P1.1	tcpwm[0].li ne_compl[3]:0	tcpwm[1].lin e_compl[3]: 0				scb[7].uart _tx:0	scb[7].i2c _sda:0	scb[7].spi_ miso:0			peri.tr_io_in put[3]:0						
P1.2	tcpwm[0].li ne[4]:4	tcpwm[1].lin e[12]:1				scb[7].uart _rts:0		scb[7].spi_ clk:0									
P1.3	tcpwm[0].li ne_compl[4]:4	tcpwm[1].lin e_compl[12]:1				scb[7].uart _cts:0		scb[7].spi_ select0:0									
P1.4	tcpwm[0].li ne[5]:4	tcpwm[1].lin e[13]:1						scb[7].spi_ select1:0									
P1.5	tcpwm[0].li ne_compl[5]:4	tcpwm[1].lin e_compl[14]:1						scb[7].spi_ select2:0									
P5.0	tcpwm[0].li ne[4]:0	tcpwm[1].lin e[4]:0				scb[5].uart _rx:0	scb[5].i2c _scl:0	scb[5].spi_ mosi:0		audioss.clk _i2s_if	peri.tr_io_in put[10]:0						
P5.1	tcpwm[0].li ne_compl[4]:0	tcpwm[1].lin e_compl[4]: 0				scb[5].uart _tx:0	scb[5].i2c _sda:0	scb[5].spi_ miso:0		audioss.tx _sck	peri.tr_io_in put[11]:0						
P5.2	tcpwm[0].li ne[5]:0	tcpwm[1].lin e[5]:0				scb[5].uart _rts:0		scb[5].spi_ clk:0		audioss.tx _ws							

Note

The notation for a signal is of the form IPName[x].signal_name[u]:y.
 IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates copies of the signal name.
 For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P5.3	tcpwm[0].li ne_compl[5]:0	tcpwm[1].lin e_compl[5]: 0				scb[5].uart _cts:0		scb[5].spi_ select0:0		audioss.tx _sdo							
P5.4	tcpwm[0].li ne[6]:0	tcpwm[1].lin e[6]:0						scb[5].spi_ select1:0		audioss.rx _sck							
P5.5	tcpwm[0].li ne_compl[6]:0	tcpwm[1].lin e_compl[6]: 0						scb[5].spi_ select2:0		audioss.rx _ws							
P5.6	tcpwm[0].li ne[7]:0	tcpwm[1].lin e[7]:0						scb[5].spi_ select3:0		audioss.rx _sdi							
P5.7	tcpwm[0].li ne_compl[7]:0	tcpwm[1].lin e_compl[7]: 0						scb[3].spi_ select3:0									
P6.0	tcpwm[0].li ne[0]:1	tcpwm[1].lin e[8]:0	scb[8].i2 c_scl:0			scb[3].uart _rx:0	scb[3].i2c _scl:0	scb[3].spi_ mosi:0				cpuss.fault _out[0]					scb[8].spi _mosi:0
P6.1	tcpwm[0].li ne_compl[0]:1	tcpwm[1].lin e_compl[8]: 0	scb[8].i2 c_sda:0			scb[3].uart _tx:0	scb[3].i2c _sda:0	scb[3].spi_ miso:0				cpuss.fault _out[1]					scb[8].spi _miso:0
P6.2	tcpwm[0].li ne[1]:1	tcpwm[1].lin e[9]:0				scb[3].uart _rts:0		scb[3].spi_ clk:0									scb[8].spi _clk:0
P6.3	tcpwm[0].li ne_compl[1]:1	tcpwm[1].lin e_compl[9]: 0				scb[3].uart _cts:0		scb[3].spi_ select0:0									scb[8].spi _select0:0
P6.4	tcpwm[0].li ne[2]:1	tcpwm[1].lin e[10]:0	scb[8].i2 c_scl:1			scb[6].uart _rx:2	scb[6].i2c _scl:2	scb[6].spi_ mosi:2			peri.tr_io_in put[12]:0	peri.tr_io_ output[0]:1				cpuss.swj_ swo_tdo	scb[8].spi _mosi:1
P6.5	tcpwm[0].li ne_compl[2]:1	tcpwm[1].lin e_compl[10]:0	scb[8].i2 c_sda:1			scb[6].uart _tx:2	scb[6].i2c _sda:2	scb[6].spi_ miso:2			peri.tr_io_in put[13]:0	peri.tr_io_ output[1]:1				cpuss.swj_ swdoe_tdi	scb[8].spi _miso:1
P6.6	tcpwm[0].li ne[3]:1	tcpwm[1].lin e[11]:0				scb[6].uart _rts:2		scb[6].spi_ clk:2								cpuss.swj_ swdio_tms	scb[8].spi _clk:1
P6.7	tcpwm[0].li ne_compl[3]:1	tcpwm[1].lin e_compl[11] :0				scb[6].uart _cts:2		scb[6].spi_ select0:2								cpuss.swj_ swclk_tclk	scb[8].spi _select0:1
P7.0	tcpwm[0].li ne[4]:1	tcpwm[1].lin e[12]:0				scb[4].uart _rx:1	scb[4].i2c _scl:1	scb[4].spi_ mosi:1			peri.tr_io_in put[14]:0		cpuss.trac e_clock				
P7.1	tcpwm[0].li ne_compl[4]:1	tcpwm[1].lin e_compl[12]:0				scb[4].uart _tx:1	scb[4].i2c _sda:1	scb[4].spi_ miso:1			peri.tr_io_in put[15]:0						
P7.2	tcpwm[0].li ne[5]:1	tcpwm[1].lin e[13]:0				scb[4].uart _rts:1		scb[4].spi_ clk:1									

Note

1. The notation for a signal is of the form IPName[x].signal_name[u].y. IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates copies of the signal name.

For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P7.3	tcpwm[0].li ne_compl[5]:1	tcpwm[1].lin e_compl[13]:0				scb[4].uart _cts:1		scb[4].spi_ select0:1									
P7.4	tcpwm[0].li ne[6]:1	tcpwm[1].lin e[14]:0						scb[4].spi_ select1:1					bless.ext_l- na_rx_ct- l_out	cpuss.trace_ data[3]:2			
P7.5	tcpwm[0].li ne_compl[6]:1	tcpwm[1].lin e_compl[14]:0						scb[4].spi_ select2:1					bless.ext_p a_tx_ct- I_out	cpuss.trace_ data[2]:2			
P7.6	tcpwm[0].li ne[7]:1	tcpwm[1].lin e[15]:0						scb[4].spi_ select3:1					bless.ext_p a_lna chip_en_o ut	cpuss.trace_ data[1]:2			
P7.7	tcpwm[0].li ne_compl[7]:1	tcpwm[1].lin e_compl[15]:0						scb[3].spi_ select1:0	cpuss.clk_ fm_pump					cpuss.trace_ data[0]:2			
P8.0	tcpwm[0].li ne[0]:2	tcpwm[1].lin e[16]:0				scb[4].uart _rx:0	scb[4].i2c _scl:0	scb[4].spi_ mosi:0			peri.tr_io_in put[16]:0						
P8.1	tcpwm[0].li ne_compl[0]:2	tcpwm[1].lin e_compl[16]:0				scb[4].uart _tx:0	scb[4].i2c _sda:0	scb[4].spi_ miso:0			peri.tr_io_in put[17]:0						
P8.2	tcpwm[0].li ne[1]:2	tcpwm[1].lin e[17]:0				scb[4].uart _rts:0		scb[4].spi_ clk:0									
P8.3	tcpwm[0].li ne_compl[1]:2	tcpwm[1].lin e_compl[17]:0				scb[4].uart _cts:0		scb[4].spi_ select0:0									
P8.4	tcpwm[0].li ne[2]:2	tcpwm[1].lin e[18]:0						scb[4].spi_ select1:0									
P8.5	tcpwm[0].li ne_compl[2]:2	tcpwm[1].lin e_compl[18]:0						scb[4].spi_ select2:0									
P8.6		tcpwm[1].lin e[19]:0						scb[4].spi_ select3:0									
P8.7	tcpwm[0].li ne_compl[3]:2	tcpwm[1].lin e_compl[19]:0						scb[3].spi_ select2:0									
P9.0	tcpwm[0].li ne[4]:2	tcpwm[1].lin e[20]:0				scb[2].uart _rx:0	scb[2].i2c _scl:0	scb[2].spi_ mosi:0			peri.tr_io_in put[18]:0			cpuss.trace_ data[3]:0			
P9.1	tcpwm[0].li ne_compl[4]:2	tcpwm[1].lin e_compl[20]:0				scb[2].uart _tx:0	scb[2].i2c _sda:0	scb[2].spi_ miso:0			peri.tr_io_in put[19]:0			cpuss.trace_ data[2]:0			

Note

The notation for a signal is of the form IPName[x].signal_name[u].y.
 IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates

copies of the signal name. For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P9.2	tcpwm[0].li ne[5]:2	tcpwm[1].lin e[21]:0				scb[2].uart _rts:0		scb[2].spi_ clk:0		pass.dsi_c tb_cmp0:1				cpuss.trace_ data[1]:0			
P9.3	tcpwm[0].li ne_compl[5]:2	tcpwm[1].lin e_compl[21]:0				scb[2].uart _cts:0		scb[2].spi_ select0:0		pass.dsi_c tb_cmp1:1				cpuss.trace_ data[0]:0			
P9.4	tcpwm[0].li ne[7]:5	tcpwm[1].lin e[0]:2						scb[2].spi_ select1:0									
P9.5	tcpwm[0].li ne_compl[7]:5	tcpwm[1].lin e_compl[0]: 2						scb[2].spi_ select2:0									
P9.6	tcpwm[0].li ne[0]:6	tcpwm[1].lin e[1]:2						scb[2].spi_ select3:0									
P9.7	tcpwm[0].li ne_compl[0]:6	tcpwm[1].lin e_compl[1]: 2															
P10.0	tcpwm[0].li ne[6]:2	tcpwm[1].lin e[22]:0				scb[1].uart _rx:1	scb[1].i2c _scl:1	scb[1].spi_ mosi:1			peri.tr_io_in put[20]:0			cpuss.trace_ data[3]:1			
P10.1	tcpwm[0].li ne_compl[6]:2	tcpwm[1].lin e_compl[22]:0				scb[1].uart _tx:1	scb[1].i2c _sda:1	scb[1].spi_ miso:1			peri.tr_io_in put[21]:0			cpuss.trace_ data[2]:1			
P10.2	tcpwm[0].li ne[7]:2	tcpwm[1].lin e[23]:0				scb[1].uart _rts:1		scb[1].spi_ clk:1						cpuss.trace_ data[1]:1			
P10.3	tcpwm[0].li ne_compl[7]:2	tcpwm[1].lin e_compl[23]:0				scb[1].uart _cts:1		scb[1].spi_ select0:1						cpuss.trace_ data[0]:1			
P10.4	tcpwm[0].li ne[0]:3	tcpwm[1].lin e[0]:1						scb[1].spi_ select1:1	audioss.p dm_clk								
P10.5	tcpwm[0].li ne_compl[0]:3	tcpwm[1].lin e_compl[0]: 1						scb[1].spi_ select2:1	audioss.p dm_data								
P10.6		tcpwm[1].lin e[2]:2						scb[1].spi_ select3:1									
P10.7	tcpwm[0].li	tcpwm[1].lin e_compl[2]: 2															
P11.0	tcpwm[0].li ne[1]:3	tcpwm[1].lin e[1]:1			smif.spi_ select2	scb[5].uart _rx:1	scb[5].i2c _scl:1	scb[5].spi_ mosi:1			peri.tr_io_in put[22]:0						
P11.1	tcpwm[0].li ne_compl[1]:3	tcpwm[1].lin e_compl[1]: 1			smif.spi_ select1	scb[5].uart _tx:1	scb[5].i2c _sda:1	scb[5].spi_ miso:1			peri.tr_io_in put[23]:0						

Note

The notation for a signal is of the form IPName[x].signal_name[u].y.
 IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates

copies of the signal name. For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P11.2	tcpwm[0].li ne[2]:3	tcpwm[1].lin e[2]:1			smif.spi_ select0	scb[5].uart _rts:1		scb[5].spi_ clk:1									
P11.3	tcpwm[0].li ne_compl[2]:3	tcpwm[1].lin e_compl[2]: 1			smif.spi_ data3	scb[5].uart _cts:1		scb[5].spi_ select0:1				peri.tr_io_ output[0]:0					
P11.4	tcpwm[0].li ne[3]:3	tcpwm[1].lin e[3]:1			smif.spi_ data2			scb[5].spi_ select1:1				peri.tr_io_ output[1]:0					
P11.5	tcpwm[0].li ne_compl[3]:3	tcpwm[1].lin e_compl[3]: 1			smif.spi_ data1			scb[5].spi_ select2:1									
P11.6					smif.spi_ data0			scb[5].spi_ select3:1									
P11.7					smif.spi_ clk												
P12.0	tcpwm[0].li ne[4]:3	tcpwm[1].lin e[4]:1			smif.spi_ data4	scb[6].uart _rx:0	scb[6].i2c _scl:0	scb[6].spi_ mosi:0			peri.tr_io_in put[24]:0						
P12.1	tcpwm[0].li ne_compl[4]:3	tcpwm[1].lin e_compl[4]: 1			smif.spi_ data5	scb[6].uart _tx:0	scb[6].i2c _sda:0	scb[6].spi_ miso:0			peri.tr_io_in put[25]:0						
P12.2	tcpwm[0].li ne[5]:3	tcpwm[1].lin e[5]:1			smif.spi_ data6	scb[6].uart _rts:0		scb[6].spi_ clk:0									
P12.3	tcpwm[0].li ne_compl[5]:3	tcpwm[1].lin e_compl[5]: 1			smif.spi_ data7	scb[6].uart _cts:0		scb[6].spi_ select0:0									
P12.4	tcpwm[0].li ne[6]:3	tcpwm[1].lin e[6]:1			smif.spi_ select3			scb[6].spi_ select1:0	audioss.p dm_clk								
P12.5	tcpwm[0].li ne_compl[6]:3	tcpwm[1].lin e_compl[6]: 1						scb[6].spi_ select2:0	audioss.p dm_data								
P12.6	tcpwm[0].li ne[7]:3	tcpwm[1].lin e[7]:1						scb[6].spi_ select3:0									
P12.7	tcpwm[0].li ne_compl[7]:3	tcpwm[1].lin e_compl[7]: 1															
P13.0	tcpwm[0].li ne[0]:4	tcpwm[1].lin e[8]:1				scb[6].uart _rx:1	scb[6].i2c _scl:1	scb[6].spi_ mosi:1			peri.tr_io_in put[26]:0						
P13.1	tcpwm[0].li ne_compl[0]:4	tcpwm[1].lin e_compl[8]: 1				scb[6].uart _tx:1	scb[6].i2c _sda:1	scb[6].spi_ miso:1			peri.tr_io_in put[27]:0						

Note

1. The notation for a signal is of the form IPName[x].signal_name[u].y. IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates

copies of the signal name. For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Port/ Pin	ACT #0	ACT #1	DS #2	ACT #4	ACT #5	ACT #6	ACT #7	ACT #8	ACT #9	ACT #10	ACT #12	ACT #13	ACT #14	ACT #15	DS #4	DS #5	DS #6
P13.2	tcpwm[0].li ne[1]:4	tcpwm[1].lin e[9]:1				scb[6].uart _rts:1		scb[6].spi_ clk:1									
P13.3	tcpwm[0].li ne_compl[1]:4	tcpwm[1].lin e_compl[9]: 1				scb[6].uart _cts:1		scb[6].spi_ select0:1									
P13.4	tcpwm[0].li ne[2]:4	tcpwm[1].lin e[10]:1						scb[6].spi_ select1:1									
P13.5	tcpwm[0].li ne_compl[2]:4	tcpwm[1].lin e_compl[10]:1						scb[6].spi_ select2:1									
P13.6	tcpwm[0].li ne[3]:4	tcpwm[1].lin e[11]:1						scb[6].spi_ select3:1									
P13.7	tcpwm[0].li ne_compl[3]:4	tcpwm[1].lin e_compl[11] :1															

Note

The notation for a signal is of the form IPName[x].signal_name[u]:y.
 IPName = Name of the block (such as tcpwm), x = Unique instance of the IP, Signal_name = Name of the signal, u = Signal number where there are more than one signals for a particular signal name, y = Designates copies of the signal name.
 For example, the name tcpwm[0].line_compl[3]:4 indicates that this is instance 0 of a tcpwm block, the signal is line_compl # 3 (complement of the line output) and this is the fourth occurrence (copy) of the signal. Signal copies are provided to allow flexibility in routing and to maximise utilisation of on-chip resources.



Analog, Smart I/O, and DSI alternate Port Pin functionality is provided in Table 9.

Table 9. Port Pin Analog, Smart I/O, and DSI Functions

Port/Pin	Name	Analog	Digital HV	DSI	SMARTIO	USB
P0.0	P0.0	wco_in		dsi[0].port_if[0]		
P0.1	P0.1	wco_out		dsi[0].port_if[1]		
P0.2	P0.2			dsi[0].port_if[2]		
P0.3	P0.3			dsi[0].port_if[3]		
P0.4	P0.4		pmic_wakeup_in hibernate_wakeup[1]	dsi[0].port_if[4]		
P0.5	P0.5		pmic_wakeup_out	dsi[0].port_if[5]		
P1.0	P1.0			dsi[1].port_if[0]		
P1.1	P1.1			dsi[1].port_if[1]		
P1.2	P1.2			dsi[1].port_if[2]		
P1.3	P1.3			dsi[1].port_if[3]		
P1.4	P1.4		hibernate_wakeup[0]	dsi[1].port_if[4]		
P1.5	P1.5			dsi[1].port_if[5]		
P14.0	USBDP					usb.usb_dp_pad
P14.1	USBDM					usb.usb_dm_pad
P5.0	P5.0			dsi[3].port_if[0]		
P5.1	P5.1			dsi[3].port_if[1]		
P5.2	P5.2			dsi[3].port_if[2]		
P5.3	P5.3			dsi[3].port_if[3]		
P5.4	P5.4			dsi[3].port_if[4]		
P5.5	P5.5			dsi[3].port_if[5]		
P5.6	P5.6	lpcomp.inp_comp0		dsi[3].port_if[6]		
P5.7	P5.7	lpcomp.inn_comp0		dsi[3].port_if[7]		
P6.0	P6.0			dsi[4].port_if[0]		
P6.1	P6.1			dsi[4].port_if[1]		
P6.2	P6.2	lpcomp.inp_comp1		dsi[4].port_if[2]		
P6.3	P6.3	lpcomp.inn_comp1		dsi[4].port_if[3]		
P6.4	P6.4			dsi[4].port_if[4]		
P6.5	P6.5			dsi[4].port_if[5]		
P6.6	P6.6		swd_data	dsi[4].port_if[6]		
P6.7	P6.7		swd_clk	dsi[4].port_if[7]		
P7.0	P7.0			dsi[5].port_if[0]		
P7.1	P7.1	csd.cmodpadd csd.cmodpads		dsi[5].port_if[1]		
P7.2	P7.2	csd.csh_tankpadd csd.csh_tankpads		dsi[5].port_if[2]		
P7.3	P7.3	csd.vref_ext		dsi[5].port_if[3]		
P7.4	P7.4			dsi[5].port_if[4]		
P7.5	P7.5			dsi[5].port_if[5]		
P7.6	P7.6			dsi[5].port_if[6]		
P7.7	P7.7	csd.cshieldpads		dsi[5].port_if[7]		



Port/Pin	Name	Analog	Digital HV	DSI	SMARTIO	USB
P8.0	P8.0			dsi[11].port_if[0]	smartio[8].io[0]	
P8.1	P8.1			dsi[11].port_if[1]	smartio[8].io[1]	
P8.2	P8.2			dsi[11].port_if[2]	smartio[8].io[2]	
P8.3	P8.3			dsi[11].port_if[3]	smartio[8].io[3]	
P8.4	P8.4			dsi[11].port_if[4]	smartio[8].io[4]	
P8.5	P8.5			dsi[11].port_if[5]	smartio[8].io[5]	
P8.6	P8.6			dsi[11].port_if[6]	smartio[8].io[6]	
P8.7	P8.7			dsi[11].port_if[7]	smartio[8].io[7]	
P9.0	P9.0	ctb_oa0+		dsi[10].port_if[0]	smartio[9].io[0]	
P9.1	P9.1	ctb_oa0-		dsi[10].port_if[1]	smartio[9].io[1]	
P9.2	P9.2	ctb_oa0_out		dsi[10].port_if[2]	smartio[9].io[2]	
P9.3	P9.3	ctb_oa1_out		dsi[10].port_if[3]	smartio[9].io[3]	
P9.4	P9.4	ctb_oa1-		dsi[10].port_if[4]	smartio[9].io[4]	
P9.5	P9.5	ctb_oa1+		dsi[10].port_if[5]	smartio[9].io[5]	
P9.6	P9.6	ctb_oa0+		dsi[10].port_if[6]	smartio[9].io[6]	
P9.7	P9.7	ctb_oa1+ or ext_vref		dsi[10].port_if[7]	smartio[9].io[7]	
P10.0	P10.0	sarmux[0]		dsi[9].port_if[0]		
P10.1	P10.1	sarmux[1]		dsi[9].port_if[1]		
P10.2	P10.2	sarmux[2]		dsi[9].port_if[2]		
P10.3	P10.3	sarmux[3]		dsi[9].port_if[3]		
P10.4	P10.4	sarmux[4]		dsi[9].port_if[4]		
P10.5	P10.5	sarmux[5]		dsi[9].port_if[5]		
P10.6	P10.6	sarmux[6]		dsi[9].port_if[6]		
P10.7	P10.7	sarmux[7]		dsi[9].port_if[7]		
P11.0	P11.0			dsi[8].port_if[0]		
P11.1	P11.1			dsi[8].port_if[1]		
P11.2	P11.2			dsi[8].port_if[2]		
P11.3	P11.3			dsi[8].port_if[3]		
P11.4	P11.4			dsi[8].port_if[4]		
P11.5	P11.5			dsi[8].port_if[5]		
P11.6	P11.6			dsi[8].port_if[6]		
P11.7	P11.7			dsi[8].port_if[7]		
P12.0	P12.0			dsi[7].port_if[0]		
P12.1	P12.1			dsi[7].port_if[1]		
P12.2	P12.2			dsi[7].port_if[2]		
P12.3	P12.3			dsi[7].port_if[3]		
P12.4	P12.4			dsi[7].port_if[4]		
P12.5	P12.5			dsi[7].port_if[5]		
P12.6	P12.6	eco_in		dsi[7].port_if[6]		
P12.7	P12.7	eco_out		dsi[7].port_if[7]		
P13.0	P13.0			dsi[6].port_if[0]		

Table 9. Port Pin Analog, Smart I/O, and DSI Functions (continued)



Port/Pin	Name	Analog	Digital HV	DSI	SMARTIO	USB
P13.1	P13.1			dsi[6].port_if[1]		
P13.2	P13.2			dsi[6].port_if[2]		
P13.3	P13.3			dsi[6].port_if[3]		
P13.4	P13.4			dsi[6].port_if[4]		
P13.5	P13.5			dsi[6].port_if[5]		
P13.6	P13.6			dsi[6].port_if[6]		
P13.7	P13.7			dsi[6].port_if[7]		

Table 9. Port Pin Analog, Smart I/O, and DSI Functions (continued)



Power Supply Considerations

The following power system diagrams show typical connections for power pins for all supported packages.

In these diagrams, the package pin is shown with the pin name, for example " V_{DDA} , M13". For V_{DDx} pins, the I/O port that is powered by that pin is also shown, for example " V_{DDD} , A13; I/O port P1".



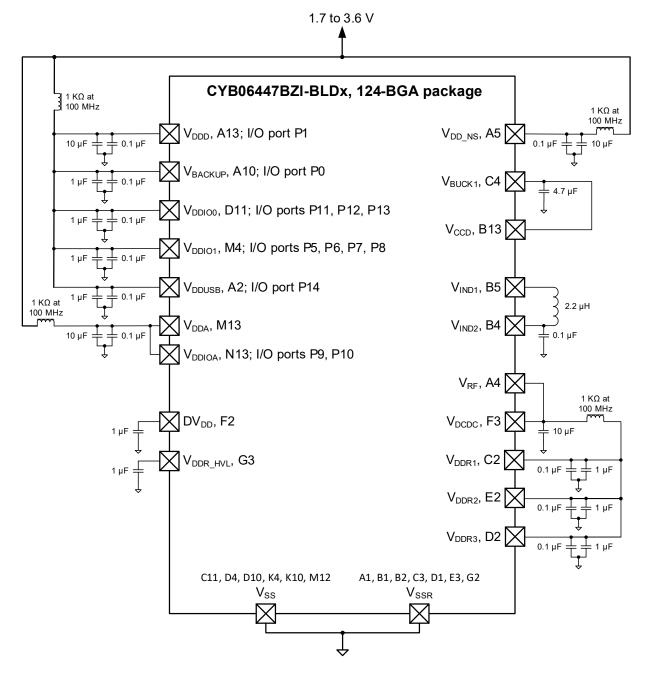
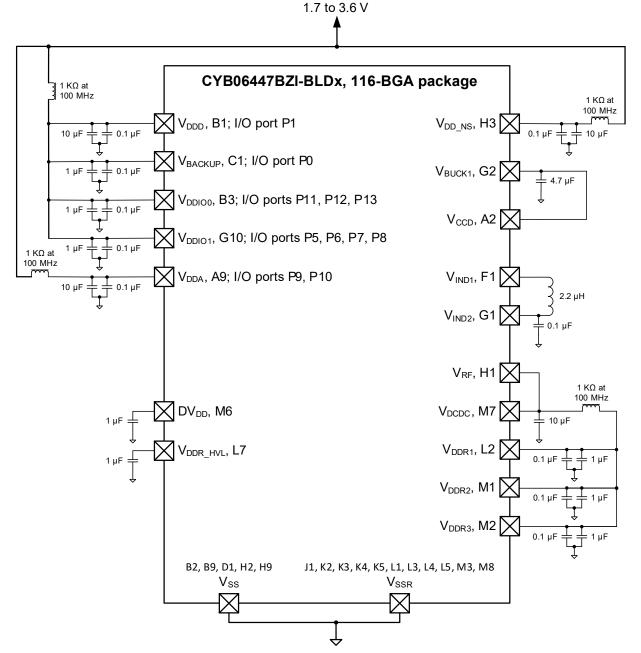




Figure 15. 116-BGA Power Connection Diagram

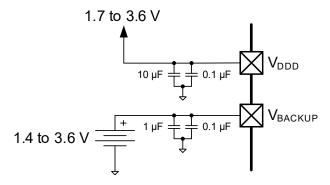


There are as many as eight V_{DDx} supply pins, depending on the package, and multiple V_{SS} ground pins. The power pins are:

- V_{DDD}: the main digital supply. It powers the low dropout (LDO) regulator and I/O port 1.
- V_{CCD}: the main LDO output. It requires a 4.7-µF capacitor for regulation. The LDO can be turned off when V_{CCD} is driven from the switching regulator (see V_{BUCK1} below). For more information, see the power system block diagram in the device technical reference manual (TRM).
- V_{DDA}: the supply for the analog peripherals. Voltage must be applied to this pin for correct device initialization and boot up.
- V_{DDIOA}: the supply for I/O ports 9 and 10. If it is present in the device package, it must be connected to V_{DDA}.
- V_{DDIO0}: the supply for I/O ports 11, 12, and 13.
- V_{DDIO1}: the supply for I/O ports 5, 6, 7, and 8.

■ V_{BACKUP}: the supply for the backup domain, which includes the 32-kHz WCO and the RTC. It can be a separate supply as low as 1.4 V, for battery or supercapacitor backup, as Figure 16 shows. Otherwise it is connected to V_{DDD}. It powers I/O port 0.

Figure 16. Separate Battery Connection to V_{BACKUP}



■ V_{DDUSB}: the supply for the USB peripheral and the USBDP and USBDM pins. It must be 2.85 V to 3.6 V for USB operation. If USB is not used, it can be 1.7 V to 3.6 V, and the USB pins can be used as limited-capability GPIOs on I/O port 14.

Table 10 shows a summary of the I/O port supplies:

Table 10. I/O Port Supplies

Port	Supply	Alternate Supply				
0	VBACKUP	V _{DDD}				
1	V _{DDD}	-				
5, 6, 7, 8	V _{DDIO1}	-				
9, 10	V _{DDIOA}	V _{DDA}				
11, 12, 13	V _{DDIO0}	-				
14	V _{DDUSB}	-				

Note: If the USB pins are not used, connect V_{DDUSB} to ground and leave the P14.0/USBDP and P14.1/USBDM pins unconnected.

Voltage must be applied to the V_{DDD} pin, and the V_{DDA} pin as noted above, for correct device initialization and operation. If an I/O port is not being used, applying voltage to the corresponding V_{DDx} pin is optional.

■ V_{SS} and V_{SSR}: ground pins for the above supplies. All ground pins should be connected together to a common ground.

In addition to the LDO regulator, a single input multiple output (SIMO) switching regulator is included. It provides two regulated outputs using a single inductor. The regulator pins are:

- V_{DD NS}: the regulator supply.
- \blacksquare V_{IND1} and V_{IND2}: the inductor and capacitor connections.
- \blacksquare V_{BUCK1}: the first regulator output. It is typically used to drive V_{CCD}, see above

■ V_{RF}: the second regulator output. It is typically used to drive the Bluetooth LE radio power pins: V_{DCDC} and V_{DDRx}.

A set of power pins for the Bluetooth LE radio are included. They are:

- V_{DCDC}: the radio digital supply.
- V_{DDR1}, V_{DDR2}, and V_{DDR3}: the radio analog supplies.
- D_{VDD}: the radio digital LDO output. It requires a 1-µF capacitor for regulation.
- V_{DDR_HVL}: the radio analog LDO output. It requires a 1-µF capacitor for regulation.

The various V_{DD} power pins are not connected together on chip. They can be connected off chip, in one or more separate nets. If separate power nets are used, they can be isolated from noise from the other nets using optional ferrite beads, as indicated in the diagrams.

No external load should be placed on V_{CCD} , V_{RF} , or any of the switching regulator power pins; whether or not the switching regulator is used.

There are no power pin sequencing requirements; power supplies may be brought up in any order. The power management system holds the device in reset until all power pins are at the voltage levels required for proper operation.

Note: If a battery is installed on the PCB first, V_{DDD} must be cycled for at least 50 µs. This prevents premature drain of the battery during product manufacture and storage.

Bypass capacitors must be connected to a common ground from the V_{DDx} and other pins, as indicated in the diagrams. Typical practice for systems in this frequency range is to use a 10-µF or 1-µF capacitor in parallel with a smaller capacitor (0.1 µF, for example). Note that these are simply rules of thumb and that, for critical applications, the PCB layout, lead inductance, and the bypass capacitor parasitic should be simulated for optimal bypassing.

All capacitors and inductors should be ±20% or better. The capacitor connected to V_{IND2} should be 100 nF. The recommended inductor value is 2.2 μ H ±20% (for example, TDK MLP2012H2R2MT0S1).

It is good practice to check the datasheets for your bypass capacitors, specifically the working voltage and the DC bias specifications. With some capacitors, the actual capacitance can decrease considerably when the applied voltage is a significant percentage of the rated working voltage.

For more information on pad layout, refer to PSoC 6 CAD libraries.



Electrical Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C and for 1.71 V to 3.6 V except where noted.

Note: These are preliminary and subject to change.

Absolute Maximum Ratings

Table 11. Absolute Maximum Ratings^[2]

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID1	V _{DD_ABS}	Analog or digital supply relative to V_{SS} ($V_{SSD} = V_{SSA}$)	-0.5	_	4	V	
SID2	V _{CCD_ABS}	Direct digital core voltage input relative to V _{SSD}	-0.5	-	1.2	V	
SID3	V _{GPIO_ABS}	GPIO voltage; V _{DDD} or V _{DDA}	-0.5	-	V _{DD} + 0.5	V	
SID4	I _{GPIO_ABS}	Current per GPIO	-25	_	25	mA	
SID5	I _{GPIO_injection}	GPIO injection current per pin	-0.5	-	0.5	mA	
SID3A	ESD_HBM	Electrostatic discharge Human Body Model	2200	-	-	V	
SID3B	ESD_HBM_ANT	Electrostatic discharge Human Body Model; Antenna Pin	500	_	-	V	RF pin
SID4A	ESD_CDM	Electrostatic discharge Charged Device Model	500	_	-	V	
SID4B	ESD_CDM_ANT	Electrostatic discharge Charged Device Model; Antenna Pin	200	-	-	V	RF pin
SID4C	ESD_CDM_X	Electrostatic discharge Charged Device Model; XI, XO pins	200	-	-	V	XI, XO Pins
SID5A	LU	Pin current for latchup-free operation	-100	-	100	mA	

Device-Level Specifications

Table 14 provides detailed specifications of CPU current. Table 12 summarizes these specifications, for rapid review of CPU currents under common conditions. Note that the max frequency for CM4 is 150 MHz, and for CM0+ is 100 MHz. IMO and FLL are used to generate the CPU clocks; FLL is not used when the CPU clock frequency is 8 MHz.

Table 12. CPU Current Specifications Summary

Condition	Range	Typ Range	Max Range
LP Mode, V _{DDD} = 3.3 V, V _{CCD} = 1.1 V,	with buck regulator		
CM4 active, CM0+ sleep		0.9–6.9 mA	1.5–8.6 mA
CM0+ active, CM4 sleep	Across CPUs clock ranges: 8–150/100 MHz; Dhrystone	0.8–3.8 mA	1.3–4.5 mA
CM4 sleep, CM0+ sleep	with flash cache enabled	0.7–1.5 mA	1.3–2.2 mA
CM0+ sleep, CM4 off		0.7–1.3 mA	1.3–2 mA
Minimum regulator current mode	Across CM4/CM0+ CPU active/sleep modes	0.6–0.7 mA	1.1–1.1 mA
ULP Mode, V _{DDD} = 3.3 V, V _{CCD} = 0.9 V	, with buck regulator		
CM4 active, CM0+ sleep		0.65–1.6 mA	0.8–2.2mA
CM0+ active, CM4 sleep	Across CPUs clock ranges: 8 – 50/25 MHz; Dhrystone	0.51–0.91 mA	0.72–1.25 mA
CM4 sleep, CM0+ sleep	with flash cache enabled	0.42–0.76 mA	0.65–1.1 mA
CM0+ sleep, CM4 off		0.41–0.62 mA	0.6–0.9 mA
Minimum regulator current mode	Across CM4/CM0+ CPU active/sleep modes	0.39–0.54 mA	0.6–0.76 mA
Deep Sleep	Across SRAM retention	7–9 µA	-
Hibernate	Across V _{DDD}	300–800 nA	-

Note

2. Usage above the absolute maximum conditions listed in Table 11 may cause permanent damage to the device. Exposure to absolute maximum conditions for extended periods of time may affect device reliability. The maximum storage temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below absolute maximum conditions but above normal operating conditions, the device may not operate to specification.



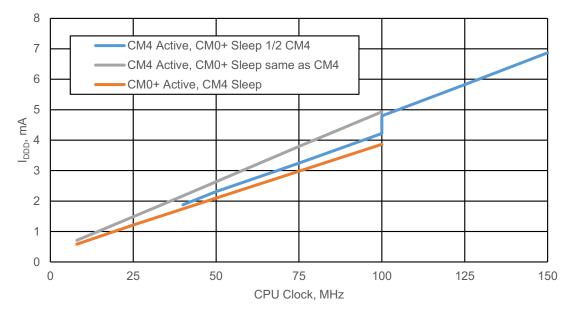


Figure 17. Typical Device Currents vs. CPU Frequency; System Low Power (LP) Mode^[3]

Power Supplies

Table 13. Power Supply DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SID6	V _{DDD}	Internal regulator and Port 1 GPIO supply	1.7	_	3.6	V	-
SID7	V _{DDA}	Analog power supply voltage. Shorted to V _{DDIOA} on PCB.	1.7	-	3.6	V	Internally unregulated supply
SID7A	V _{DDIO1}	GPIO supply for ports 5 to 8 when present	1.7	_	3.6	V	Must be \geq V _{DDA} if the CapSense (CSD) block is used in the application
SID7B	V _{DDIO0}	GPIO supply for ports 11 to 13 when present	1.7	-	3.6	V	-
SID7D	V _{DDIOA}	GPIO supply for ports 9 and 10 when present. Must be connected to V_{DDA} on PCB.	1.7	-	3.6	V	_
SID7F	V _{DDUSB}	Supply for port 14 (USB or GPIO) when present	1.7	-	3.6	V	Min. supply is 2.85 V for USB
SID6B	V _{BACKUP}	Backup power and GPIO Port 0 supply when present	1.7	-	3.6	V	Min. is 1.4 V when V_{DDD} is removed.
SID8	V _{CCD1}	Output voltage (for core logic bypass)	-	1.1	-	V	System LP mode
SID9	V _{CCD2}	Output voltage (for core logic bypass)	_	0.9	-	V	ULP mode. Valid for –20 to 85 °C.
SID10	C _{EFC}	External regulator voltage (V _{CCD}) bypass	3.8	4.7	5.6	μF	X5R ceramic or better; Value for 0.8 to 1.2 V.
SID11	C _{EXC}	Power supply decoupling capacitor	_	10	_	μF	X5R ceramic or better

Note 3. CM4 Active, CM0+ Sleep 1/2 CM4 trace values are higher because above 100 MHz, the PLL must be used instead of the FLL.



CPU Current and Transition Times

Table 14. CPU Current and Transition Times

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
LP RANGE	POWER SP	ECIFICATIONS (for V _{CCD} = 1.1 V v	vith Bu	ck and	LDO)	•	•
Cortex M4.	Active Mod	e					
Execute wi	ith Cache Di	sabled (Flash)					
SIDF1	I _{DD1}	Execute from Flash; CM4 Active 50 MHz, CM0+ Sloop 25 MHz	-	2.3	3.2	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
	וטטי	CM0+ Sleep 25 MHz. With IMO & FLL. While(1).	_	3.1	3.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			1	5.7	6.5	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
81052		Execute from Flash; CM4 Active 8 MHz, CM0+ Sleep 8 MHz. With IMO. While(1).	_	0.9	1.5	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDF2	DD2		_	1.2	1.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			_	2.8	3.5	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
Execute wi	ith Cache Er	nabled					•
	I _{DD3}	Execute from Cache; CM4 Active	_	6.9	8.6	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDC1		150 MHz, CM0+ Sleep 75 MHz. IMO & PLL. Dhrystone.	_	10.9	13.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		INO & FEL. DITYSIONE.	_	13.7	15.5	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
		Execute from Cache;	-	4.8	5.8	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDC2	I _{DD4}	CM4 Active 100 MHz, CM0+ Sleep 100 MHz. IMO & FLL. Dhrystone.	_	7.4	8.4	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		Too Minz. Into a r EE. Dhirystone.	I	11.3	12	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
		Execute from Cache; CM4 Active	1	2.4	3.4	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDC3	I _{DD5}	50 MHz, CM0+ Sleep 25 MHz. IMO & FLL. Dhrystone		3.7	4.1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		a FLL. Dhi ystone	_	6.3	7.2	mA	V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
		Execute from Cache; CM4 Active	-	0.9	1.5	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDC4	I _{DD6}	8 MHz, CM0+ Sleep 8 MHz. IMO. Dhrystone.	I	1.3	1.8	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		Dirystone.	-	3	3.8	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
Cortex M0-	+. Active Mo	de					
Execute wi	ith Cache Di	sabled (Flash)					
		Execute from Flash;	-	2.4	3.3	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDF3	I _{DD7}	CM4 Off, CM0+ Active 50 MHz. With IMO & FLL. While (1).	_	3.2	3.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			I	5.6	6.3	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
		Execute from Flash;	_	0.8	1.5	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDF4	I _{DD8}	CM4 Off, CM0+ Active 8 MHz. With IMO. While (1).	-	1.1	1.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			-	2.60	3.4	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C



Table 14. CPU Current and Transition Times (continued)

SIDC5 IDD9 CM4 Off, CM0+ Relative 100 MHz, With IMO & FLL. Dhrystone. - 5.9 6.5 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDC6 IDD10 Execute from Cache; CM4 Off, CM0+ Active 8 MHz. - 0.8 1.3 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDC6 IDD10 Execute from Cache; CM4 Off, CM0+ Active 8 MHz. - 0.8 1.3 mA V _{DDD} = 3.3 V. Buck ON, Max at 60 * SIDS1 IDD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS1 IDD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 mA V _{DDD} = 3.3 V. Buck ON, Max at 60 * SIDS2 IDD12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.2 1.9 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. - 1.3 2 mA V _{DD}	Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SIDC5 IDD9 CM4 Off, CM0+ Relative 100 MHz, With IMO & FLL. Dhrystone. - 5.9 6.5 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDC6 IDD10 Execute from Cache; CM4 Off, CM0+ Active 8 MHz. - 0.8 1.3 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDC6 IDD10 Execute from Cache; CM4 Off, CM0+ Active 8 MHz. - 0.8 1.3 mA V _{DDD} = 3.3 V. Buck ON, Max at 60 * SIDS1 IDD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS1 IDD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 mA V _{DDD} = 3.3 V. Buck ON, Max at 60 * SIDS2 IDD12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.2 1.9 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA V _{DDD} = 1.8 V. Buck ON, Max at 60 * SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. - 1.3 2 mA V _{DD}	Execute wi	th Cache Er	nabled					•
With IMO & FLL. Dhrystone. - 5.9 6.5 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDC6 IbD10 CM4 Off. CM0 + Active 8 MHz. With IMO. Dhrystone. - 9 9.7 mA Volce 1.8 v. Buck ON, Max at 80 ° SIDC6 IbD10 CM4 Off. CM0 + Active 8 MHz. With IMO. Dhrystone. - 0.8 1.3 mA Volce 1.8 v. Buck ON, Max at 60 ° Cortex M4. Sleep Mode - 1.20 1.7 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDS1 IbD11 CM4 Sleep 100 MHz: CM0 + Sleep 25 MHz. With IMO & FLL. - 1.5 2.2 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDS1 IbD12 CM4 Sleep 50 MHz: CM0 + Sleep 25 MHz. With IMO & FLL. - 1.2 1.9 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDS3 IbD12 CM4 Sleep 8 MHz. CM0 + Sleep 8 - 1.7 2.2 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDS3 IbD13 MtHz. CM4 Sleep 8 MHz. CM0 + Sleep 8 - 1.7 2.2 mA Volce 1.8 v. Buck ON, Max at 60 ° SIDS4 IbD14 CM4 Off. CM0 +	SIDCE			_	3.8	4.5	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDC6 Ibb 10 Execute from Cache; CM4 Off, CM0+ Active 8 MHz, With IMO. Dhrystone. - 0.8 1.3 mA VDDD = 3.3 V, Buck ON, Max at 60 * Cortex M4. Sleep Mode - 1.20 1.7 mA VDDD = 1.8 V, Buck ON, Max at 60 * SIDS1 Ibb 11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & FLL. - 1.5 2.2 mA VDDD = 3.3 V, Buck ON, Max at 60 * SIDS1 Ibb 11 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & FLL. - 1.5 2.2 mA VDDD = 1.8 V, Buck ON, Max at 60 * SIDS2 Ibb 12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & FLL. - 1.2 1.9 mA VDDD = 1.8 V, Buck ON, Max at 60 * SIDS3 Ibb 12 CM4 Sleep 50 MHz; CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 * SIDS3 Ibb 13 CM4 Off, CM0+ Sleep 50 MHz; With IMO & FLL. - 1.3 2 mA VDDD = 1.8 V, Buck ON, Max at 60 * SIDS4 Ibb 14 CM4 Off, CM0+ Sleep 50 MHz; With IMO & FLL. - 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 * <td>SIDC5</td> <td>DD9</td> <td></td> <td>-</td> <td>5.9</td> <td>6.5</td> <td>mA</td> <td>V_{DDD} = 1.8 V, Buck ON, Max at 60 °C</td>	SIDC5	DD9		-	5.9	6.5	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDC6 Ibb10 Execute from Cache; SM4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With IMO. Drivystone. Image: Cm4 2011 CM04 Active 8 MHz. With				_	9	9.7	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
With IMO. Dhrystone. - 1.20 1.7 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° Cortex M4. Sleep Mode - 2.60 3.4 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 86 ° SIDS1 IDD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 2.7 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS1 IDD11 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.5 2.2 2.7 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS2 IDD12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz. With IMO & - 1.2 1.9 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS3 IDD12 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 50 MHz, With IMO - 1.3 2 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz, With IMO & FLL. - 1.3 2 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS5 IDD15<				_	0.8	1.3	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
Cortex M4. Sleep Mode CM4 Sleep 100 MHz: CM0+ Sleep 25 MHz. With IMO & FLL. - 1.5 2.2 mA V _{DDD} = 3.3 V, Buck ON, Max at 60 ° V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - SIDS1 I _{DD11} CM4 Sleep 50 MHz: CM0+ Sleep 50 MHz: CM0+ Sleep 25 MHz. With IMO & FLL. - 1.2 1.9 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - SIDS2 I _{DD12} CM4 Sleep 50 MHz: CM0+ Sleep 25 MHz. With IMO & FLL. - 1.2 1.9 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - SIDS3 I _{DD13} CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 1.0 - 1.0 - 1.0 - 1.0 - 1.3 2 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° - - 1.3 <td>SIDCo</td> <td>DD10</td> <td></td> <td>_</td> <td>1.20</td> <td>1.7</td> <td>mA</td> <td>V_{DDD} = 1.8 V, Buck ON, Max at 60 °C</td>	SIDCo	DD10		_	1.20	1.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDS1 IbD11 CM4 Sleep 100 MHz; CM0+ Sleep 25 MHz; With IMO & FLL. - 1.5 2.2 mA VpDD = 3.3 V, Buck ON, Max at 60 ° VpDD = 1.8 V, Buck ON, Max at 60 ° - SIDS2 IbD12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz, With IMO & FLL. - 4 4.6 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - SIDS2 IbD12 CM4 Sleep 50 MHz; CM0+ Sleep 25 MHz, With IMO & FLL. - 1.2 1.9 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - SIDS3 IbD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz, With IMO. - 0.7 1.3 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - SIDS3 IbD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz, With IMO. - 0.7 1.3 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - 2.4 3.3 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - - 1.3 2 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - - 1.3 2 mA VpDD = 1.8 V, Buck ON, Max at 60 ° - - - 1.3 3.4 A MA VpDD = 1.8 V, Buck ON, Max at 60 ° - - <td></td> <td></td> <td></td> <td>_</td> <td>2.60</td> <td>3.4</td> <td>mA</td> <td>V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C</td>				_	2.60	3.4	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDS1 Ibb11 CM4 Sleep 100 MHz; FLL. With IMO & FLL. - 2.2 2.7 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS2 Ibb12 CM4 Sleep 25 MHz; With IMO & FLL. - 4 4.6 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS2 Ibb12 CM4 Sleep 50 MHz; CM0+ Sleep 50 MHz; CM0+ Sleep 8 MHz, CM0+ Sleep 8 - 1.7 2.2 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS3 Ibb13 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS3 Ibb13 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS4 Ibb14 CM4 Off, CM0+ Sleep 50 MHz. With IMO. - 1.3 2 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS4 Ibb14 CM4 Off, CM0+ Sleep 50 MHz. With IMO. - 1.3 2 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS5 Ibb15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 1.3 2 mA V_DDD = 1.8 V, Buck ON, Max at 60 °.	Cortex M4.	Sleep Mode)					•
SIDS1 IDD11 CMO+ Sleep 25 MHz. With IMO & FL. - 2.2 2.7 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS2 IDD12 CM4 Sleep 25 MHz. With IMO & FL. - 4 4.6 mA VDDD = 1.8 to 3.3 V, DDO, Max at 86 ° SIDS2 IDD12 CM4 Sleep 25 MHz. With IMO & FL. - 1.2 1.9 mA VDDD = 1.8 to 3.3 V, Buck ON, Max at 60 ° SIDS3 IDD13 CM4 Sleep 25 MHz. With IMO & FL. - 1.7 2.2 mA VDDD = 1.8 to 3.3 V, Buck ON, Max at 60 ° SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 - 0.7 1.3 mA VDDD = 3.3 V, Buck ON, Max at 60 ° SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. - 1.3 2 mA VDDD = 3.3 V, Buck ON, Max at 60 ° SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. - 1.3 2 mA VDDD = 1.8 to 3.3 V, LDO, Max at 80 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO - 1.3 2 mA VDDD = 1.8 to 3.3 V, LDO, Max at 60 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO - 1.1 1.5 mA <td></td> <td></td> <td>CM4 Sleep 100 MHz[.]</td> <td>_</td> <td>1.5</td> <td>2.2</td> <td>mA</td> <td>V_{DDD} = 3.3 V, Buck ON, Max at 60 °C</td>			CM4 Sleep 100 MHz [.]	_	1.5	2.2	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
Image: start	SIDS1	I _{DD11}	CM0+ Sleep 25 MHz. With IMO &	_	2.2	2.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDS2 IDD12 CMA Sleep 30 MHZ. With IMO & FLL. IDD12 CMA Sleep 30 MHZ. With IMO & FLL. IDD13 IDD13 IDD13 CMA Sleep 8 MHZ, CM0+ Sleep 8 MHZ. With IMO. IDD13 CMA Sleep 8 MHZ, CM0+ Sleep 8 MHZ. IDD13 CMA Sleep 30 MHZ. CM0+ Sleep 50 MHZ. IDD13 CMA Off, CM0+ Sleep 50 MHZ. With IMO & FLL. IDD14 CM4 Off, CM0+ Sleep 50 MHZ. With IMO & FLL. IDD14 CM4 Off, CM0+ Sleep 50 MHZ. With IMO & FLL. IDD14 CM4 Off, CM0+ Sleep 50 MHZ. With IMO & FLL. IDD14 CM4 Off, CM0+ Sleep 50 MHZ. With IMO & FLL. IDD14 CM4 Off, CM0+ Sleep 8 MHZ. With IMO. IDD15 CM4 Off, CM0+ Sleep 8 MHZ. With IMO. IDD15 CM4 Off, CM0+ Sleep 8 MHZ. With IMO. IDD15 CM4 Off, CM0+ Sleep 8 MHZ. With IMO. IDD16 Execute from Flash; CM4 LPA 8 MHZ. CM0+ Sleep 8 MHZ. With IMO. While (1). IDD15 CM4 Off, CM0+ Sleep 8 MHZ. With IMO. IDD16 Execute from Cache; CM4 LPA 8 MHZ. CM0+ Sleep 8 MHZ. With IMO. IDD17 Execute from Cache; CM4 LPA 8 MHZ. CM0+ Sleep 8 MHZ. With IMO. IDD18 Execute from Cache; CM4 LPA 8 MHZ. CM0+ Sleep 8 MHZ. With IMO. IDD18 IDD18			FLL.	_	4	4.6	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDS2 IbD12 CM0+ Sleep 25 MHz. With IMO & FLL. - 1.7 2.2 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS3 IDD13 CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1 1.5 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.3 2 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO - 1.3 2 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO - 0.7 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO - 0.9 1.5 mA VDDD = 1.8 V, Buck ON, Max at 6		I _{DD12}	CM4 Sleep 50 MHz [.]	_	1.2	1.9	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS3 - 3.4 4.3 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 ° SIDS3 I _{DD13} CM4 Sleep 8 MHz, CM0+ Sleep 8 MHz, With IMO. - 0.7 1.3 mA V _{DDD} = 3.3 V, Buck ON, Max at 60 ° Cortex M0+. Sleep Mode - 1 1.5 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 ° Cortex M0+. Sleep Mode - 1.4 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS4 I _{DD14} CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.3 2 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 1.9 2.4 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 I _{DD16} Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). - 0.9 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 I _{DD16} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1)	SIDS2		CM0+ Sleep 25 MHz. With IMO &	_	1.7	2.2	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDS3 IDD13 CM4 Sleep 8 MH2, CM0+ Sleep 8 MH2, With IMO. - 1 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° Cortex M0+. Sleep Mode - 2.4 3.3 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 60 ° SIDS4 I _{DD14} CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.3 2 mA V _{DDD} = 3.3 V, Buck ON, Max at 60 ° SIDS4 I _{DD14} CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.9 2.4 mA V _{DDD} = 1.8 to 3.3 V, Buck ON, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 to 3.3 V, Buck ON, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 I _{DD16} Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). - 0.9 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA2 I _{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA <td< td=""><td></td><td></td><td>_</td><td>3.4</td><td>4.3</td><td>mA</td><td>V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C</td></td<>				_	3.4	4.3	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDS3 IbD13 MHZ. With IMO. — 1 1.5 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. Cortex M0+. Sleep Mode — 2.4 3.3 mA V_DDD = 1.8 to 3.3 V, LDO, Max at 85 °. SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. — 1.3 2 mA V_DDD = 3.3 V, Buck ON, Max at 60 °. SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. — 1.3 2 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. — 0.7 1.3 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. — 0.7 1.3 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). — 0.9 1.5 mA V_DDD = 3.3 V, Buck ON, Max at 60 °. SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. — 0.9 1.5 mA V_DDD = 1.8 V, Buck ON, Max at 60 °. SIDLPA3 IDD17 Execute from Cache; CM4 LPA 8 MHZ, CM0+ Sleep 8 MHz. Wit			CM4 Sleep 8 MHz, CM0+ Sleep 8	_	0.7	1.3	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
Cortex M0+. Sleep Mode - 2.4 3.3 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 ° SIDS4 I _{DD14} CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.3 2 mA V _{DDD} = 3.3 V, Buck ON, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 1.3 2 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 60 ° SIDS5 I _{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDS5 I _{DD16} CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 I _{DD16} Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). - 0.9 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA2 I _{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 ° SIDLPA3 I _{DD18} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA </td <td>SIDS3</td> <td>I_{DD13}</td> <td>MHz.</td> <td>-</td> <td>1</td> <td>1.5</td> <td>mA</td> <td>V_{DDD} = 1.8 V, Buck ON, Max at 60 °C</td>	SIDS3	I _{DD13}	MHz.	-	1	1.5	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDS4 IDD14 CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL. - 1.3 2 mA VDDD = 3.3 V, Buck ON, Max at 60 ° - 1.9 2.4 mA VDDD = 1.8 V, Buck ON, Max at 60 ° - 3.80 4.6 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA VDDD = 3.3 V, Buck ON, Max at 60 ° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz. With IMO. While (1). - 0.9 1.5 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDLPA2 IDD16 Execute from Cache; CM4 LPA 8 MHz. With IMO. While (1). - 0.9 1.5 mA VDDD = 1.8 V, Buck ON, Max at 60 ° SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz. With IMO. While (1). - 0.9 1.5 mA VDDD = 1.8 V, Buck ON, Max at 60 ° - 1.017 Execute from Cache; CM4 LPA 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA VDDD = 1.8 V, Buck ON, Max at 60 °				_	2.4	3.3	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDS4IDD14CM4 Off, CM0+ Sleep 50 MHz. With IMO & FLL1.92.4mAV_{DDD} = 1.8 V, Buck ON, Max at 60 °SIDS5IDD15CM4 Off, CM0+ Sleep 8 MHz. With IMO3.804.6mAV_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °SIDS5IDD15CM4 Off, CM0+ Sleep 8 MHz. With IMO0.71.3mAV_{DDD} = 3.3 V, Buck ON, Max at 60 °SIDS5IDD15CM4 Off, CM0+ Sleep 8 MHz. With IMO0.71.3mAV_{DDD} = 1.8 to 3.3 V, LDO, Max at 60 °SIDLPA1IDD16Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1)0.91.5mAV_{DDD} = 3.3 V, Buck ON, Max at 60 °SIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone0.91.5mAV_{DDD = 1.8 to 3.3 V, LDO, Max at 86 °SIDLPA3IDD18Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone0.91.5mAV_{DDD = 1.8 to 3.3 V, LDO, Max at 60 °SIDLPA3IDD18Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone0.91.5mAV_{DDD = 1.8 to 3.3 V, Buck ON, Max at 60 °SIDLPA3IDD18Execute from Flash; CM4 Off, CM0+ Active 8 MHz0.91.5mAV_{DDD = 1.8 to 3.3 V, Buck ON, Max at 60 °-1.11.6mAV_{DDD = 1.8 V, Buck ON, Max at 60 °1.31.8mAV_{DDD = 1.8 V, Buck ON, Max at 60 °	Cortex M0+	. Sleep Moo	le					
SIDS4 IDD14 With IMO & FLL. - 1.9 2.4 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °. SIDS5 IDD15 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 °. SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. - 0.7 1.3 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 °. Cortex M4. Minimum Regulator Current Mode - 0.7 1.3 mA $V_{DDD} = 1.8$ to 3.3 V, LDO, Max at 60 °. SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). - 0.9 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 °. SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °. SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. - 0.9 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °. - 1.3 1.8 mA V_{DDD} = 1.8 V, Buck ON, Max at 60 °. - - 2.9 3.7 mA V_{DDD} = 1.8 V, Buc				-	1.3	2	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. $ 0.7$ 1.3 mA V_{DDD} = 3.3 V, Buck ON, Max at 60° SIDS5 IDD15 CM4 Off, CM0+ Sleep 8 MHz. With IMO. $ 1.5$ mA V_{DDD} = 1.8 V, Buck ON, Max at 60° Cortex M4. Minimum Regulator Current Mode $ 2.4$ 3.3 mA V_{DDD} = 1.8 to 3.3 V, LDO, Max at 60° SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA V_{DDD} = 3.3 V, Buck ON, Max at 60° SIDLPA1 IDD16 Execute from Flash; CM4 LPA 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA V_{DDD} = 1.8 V, Buck ON, Max at 60° SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA V_{DDD} = 1.8 V, Buck ON, Max at 60° SIDLPA2 IDD17 Execute from Cache; CM4 LPA 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA V_{DDD} = 1.8 V, Buck ON, Max at 60° SIDLPA3 IDD17 Execute from Slash; CM4 LPA 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA V_{DDD} = 1.8	SIDS4	I _{DD14}	With IMO & FLL.	_	1.9	2.4	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDS5 I_{DD15} CM4 Off, CM0+ Sleep 8 MHz. With IMO. $ 1$ 1.5 mA $V_{DDD} = 1.8 \text{ V}$, Buck ON, Max at 60 °Cortex M4. Minimum Regulator Current ModeSIDLPA1 I_{DD16} $E_{xecute from Flash; CM4 LPA 8 MHz. With IMO. While (1). 0.91.5mAV_{DDD} = 3.3 \text{ V}, Buck ON, Max at 60 °SIDLPA1I_{DD16}E_{xecute from Flash; CM4 LPA 8 MHz. With IMO. While (1). 0.91.5mAV_{DDD} = 1.8 \text{ V}, Buck ON, Max at 60 °SIDLPA2I_{DD17}E_{xecute from Cache; CM4 LPA 8 MHz. With IMO. Dhrystone. 0.91.5mAV_{DDD} = 1.8 \text{ V}, Buck ON, Max at 60 °SIDLPA3I_{DD18}E_{xecute from Flash; CM4 LPA 8 MHz. With IMO. While (1). 0.91.5mAV_{DDD} = 1.8 \text{ V}, Buck ON, Max at 60 °SIDLPA3I_{DD18}E_{xecute from Cache; CM4 LPA 8 MHz. With IMO. While (1). 0.81.4mAV_{DDD} = 1.8 \text{ V}, Buck ON, Max at 60 °SIDLPA3I_{DD18}E_{xecute from Flash; CM4 LPA 8 MHz. With IMO. While (1). 0.81.4mAV_{DDD} = 1.8 \text{ V}, Buck ON, Max at 60 °$				_	3.80	4.6	mA	V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDS3IDD15IMO. $ 1$ 1.3 IMA $V_{DDD} = 1.8$ to 3.3 V, Buck ON, Max at 60Cortex M4. Minimum Regulator Current ModeSIDLPA1 I_{DD16} Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$ SIDLPA1 I_{DD16} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $-$ SIDLPA2 I_{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$ SIDLPA2 I_{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $-$ SIDLPA3 I_{DD18} Execute from Flash; CM4 Off, CM0+ Active 8 MHz. $ 0.8$ 1.4 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$ SIDLPA3 I_{DD18} Execute from Flash; CM4 Off, CM0+ Active 8 MHz. $ 0.8$ 1.4 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$				_	0.7	1.3	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
Cortex M4. Minimum Regulator Current ModeSIDLPA1 I_{DD16} Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $ -$ SIDLPA1 I_{DD16} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). $ 0.9$ 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $-$ SIDLPA2 I_{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$ SIDLPA2 I_{DD17} Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $-$ SIDLPA3 I_{DD18} Execute from Flash; CM4 Off, CM0+ Active 8 MHz. $ 0.8$ 1.4 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $-$	SIDS5	I _{DD15}		_	1	1.5	mA	V_{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDLPA1 I_{DD16} $Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1). - 0.9 1.5 mA V_{DDD} = 3.3 V, ext{ Buck ON, Max at 60 } 0 - 1.2 1.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 3.3 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 3.3 V, ext{ Buck ON, Max at 60 } 0 - 2.8 3.5 mA V_{DDD} = 3.3 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 3.7 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 0.8 1.4 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 0.8 1.4 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 0.8 1.4 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 0.8 1.4 mA V_{DDD} = 1.8 V, ext{ Buck ON, Max at 60 } 0 - 2.9 0.8 1.4 mA V_{DDD} = 1.8 V, ext{ Buck ON, Ma$				_	2.4	3.3	mA	V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 $^\circ\text{C}$
SIDLPA1IDD16Execute from Flash; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. While (1)1.21.7mA $V_{DDD} = 1.8 \text{ V}$, Buck ON, Max at 60 °CSIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone0.91.5mA $V_{DDD} = 3.3 \text{ V}$, Buck ON, Max at 60 °CSIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone0.91.5mA $V_{DDD} = 3.3 \text{ V}$, Buck ON, Max at 60 °CCortex M0+. Minimum Regulator Current Mode-2.93.7mA $V_{DDD} = 1.8 \text{ to } 3.3 \text{ V}$, LDO, Max at 85 °CSIDLPA3IDD18Execute from Flash; CM4 Off, CM0+ Active 8 MHz0.81.4mA $V_{DDD} = 3.3 \text{ V}$, Buck ON, Max at 60 °C	Cortex M4.	Minimum R	egulator Current Mode					
SIDLPA1IDD16MHz, CM0+ Sleep 8 MHz. With IMO. While (1). $ 1.2$ 1.7 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °SIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 °SIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 0.9$ 1.5 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °Cortex M0+. Minimum Regulator Current Mode $ 0.8$ 1.4 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 °SIDLPA3IDD18Execute from Flash; With IMO. While (1). $ 0.8$ 1.4 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 °			Execute from Flash: CM4 LPA 8	_	0.9	1.5	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
$\frac{-2.8}{3.5} \text{ mA} V_{\text{DDD}} = 1.8 \text{ to } 3.3 \text{ V, LDO, Max at } 85^{\circ} \text{ Max}^{\circ} \text{ V}_{\text{DDD}} = 3.3 \text{ V, Buck ON, Max at } 60^{\circ} \text{ Max}^{\circ} Max$	SIDLPA1	I _{DD16}	MHz, CM0+ Sleep 8 MHz. With	_	1.2	1.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDLPA2IDD17Execute from Cache; CM4 LPA 8 MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone1.31.8mA V_{DDD} = 1.8 V, Buck ON, Max at 60 ° -Cortex M0+. Minimum Regulator Current Mode-2.93.7mA V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 ° -SIDLPA3IDD18Execute from Flash; CM4 Off, CM0+ Active 8 MHz. With IMO. While (1)0.81.4mA V_{DDD} = 3.3 V, Buck ON, Max at 60 ° -				_	2.8	3.5	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDLPA2IDD17MHz, CM0+ Sleep 8 MHz. With IMO. Dhrystone. $ 1.3$ 1.8 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $ 2.9$ 3.7 mA $V_{DDD} = 1.8$ to 3.3 V, LDO, Max at 85 °Cortex M0+. Minimum Regulator Current ModeExecute from Flash; CM4 Off, CM0+ Active 8 MHz. $ 0.8$ 1.4 mA $V_{DDD} = 3.3$ V, Buck ON, Max at 60 ° $ -$ SIDLPA3IDD18Execute from Flash; With IMO. While (1). $ 1.1$ 1.6 mA $V_{DDD} = 1.8$ V, Buck ON, Max at 60 ° $-$			Execute from Cache: CM4 LPA 8	_	0.9	1.5	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
Cortex M0+. Minimum Regulator Current Mode $ 2.9$ 3.7 mA V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °SIDLPA3IDD18Execute from Flash; CM4 Off, CM0+ Active 8 MHz. With IMO. While (1). $ 0.8$ 1.4 mA V_{DDD} = 3.3 V, Buck ON, Max at 60 °	SIDLPA2	I _{DD17}	MHz, CM0+ Sleep 8 MHz. With	_	1.3	1.8	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDLPA3 I _{DD18} Execute from Flash; CM4 Off, CM0+ Active 8 MHz. With IMO. While (1). $-$ 0.8 1.4 mA V_{DDD} = 3.3 V, Buck ON, Max at 60 °C $-$ 1.1 1.6 mA V_{DDD} = 1.8 V, Buck ON, Max at 60 °C					2.9	3.7	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
SIDLPA3 I_{DD18} I_{D18}	Cortex M0+	. Minimum	Regulator Current Mode		•	•		
SIDLPA3 I _{DD18} CM4 Off, CM0+ Active 8 MHz. – 1.1 1.6 mA V _{DDD} = 1.8 V, Buck ON, Max at 60 °			Execute from Flash	_	0.8	1.4	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
- 2.7 3.6 mA V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °	SIDLPA3	I _{DD18}	CM4 Off, CM0+ Active 8 MHz.	_	1.1	1.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			(1).	-	2.7	3.6	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C



Table 14. CPU Current and Transition Times (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
		Execute from Cache; CM4 Off,	_	0.8	1.4	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDLPA4	I _{DD19}	CM0+ Active 8 MHz. With IMO.	_	1.2	1.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		Dhrystone.	_	2.7	3.6	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
Cortex M4.	Minimum R	egulator Current Mode					L
		CM4 Sleep 8 MHz, CM0+ Sleep 8	_	0.7	1.1	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDLPS1	I _{DD20}	MHz.	_	1	1.5	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		With IMO.	_	2.4	3.3	mA	V _{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
Cortex M0+	. Minimum	Regulator Current Mode					•
			_	0.6	1.1	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDLPS3	I _{DD22}	CM4 Off, CM0+ Sleep 8 MHz. With IMO.	_	0.9	1.5	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
			_	2.4	3.3	mA	V_{DDD} = 1.8 to 3.3 V, LDO, Max at 85 °C
		SPECIFICATIONS (for V _{CCD} = 0.9 V	using	the Buo	ck). ULP	mode i	s valid from –20 to +85 °C.
	Active Mod						
Execute wit	th Cache Di	sabled (Flash)				1	
SIDF5	I _{DD3}	Execute from Flash; CM4 Active 50 MHz, CM0+ Sleep 25 MHz.		1.7	2.2	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
		With IMO & FLL. While(1).	_	2.1	2.4	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDF6	I _{DD4}	Execute from Flash; CM4 Active 8 MHz, CM0+ Sleep 8 MHz. With	-	0.56	0.8	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
-	004	IMO. While (1)	_	0.75	1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Execute wit	th Cache Er	nabled				•	
SIDC8	I _{DD10}	Execute from Cache; CM4 Active 50 MHz, CM0+ Sleep 25 MHz. With IMO & FLL. Dhrystone.	_	1.6	2.2	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
			_	2.4	2.7	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDC9	I _{DD11}	Execute from Cache; CM4 Active 8 MHz, CM0+ Sleep 8 MHz.	-	0.65	0.8	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
	bbn	With IMO. Dhrystone.	_	0.8	1.1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
	. Active Mo						
Execute wit	th Cache Di	sabled (Flash)		1		1	
SIDF7	I _{DD16}	Execute from Flash; CM4 Off, CM0+ Active 25 MHz. With IMO &	_	1	1.4	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
	DD10	FLL. Write(1).	_	1.34	1.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDF8	I _{DD17}	Execute from Flash; CM4 Off, CM0+ Active 8 MHz. With IMO.	_	0.54	0.75	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
	While(1).			0.73	1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Execute wit	th Cache Er	nabled		1	1	1	1
SIDC10	I _{DD18}	Execute from Cache; CM4 Off, CM0+ Active 25 MHz. With IMO &	-	0.91	1.25	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
		FLL. Dhrystone.	_	1.34	1.6	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDC11 I	I _{DD19}	Execute from Cache; CM4 Off, CM0+ Active 8 MHz. With IMO.	_	0.51	0.72	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
	DD19	Dhrystone.	_	0.73	0.95	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C



Table 14. CPU Current and Transition Times (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
Cortex M4.	Sleep Mode)					
01007		CM4 Sleep 50 MHz, CM0+ Sleep	_	0.76	1.1	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS7	I _{DD21}	25 MHz. With IMO & FLL.	_	1.1	1.4	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
		CM4 Sleep 8 MHz, CM0+ Sleep 8	_	0.42	0.65	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS8	I _{DD22}	MHz. With IMO.	_	0.59	0.8	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Cortex M0+	. Sleep Moo	le		I	I	I	
		CM4 Off, CM0+ Sleep 25 MHz.	_	0.62	0.9	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS9	I _{DD23}	With IMO & FLL.	_	0.88	1.1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
0.00/0		CM4 Off, CM0+ Sleep 8 MHz.	_	0.41	0.6	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDS10	I _{DD24}	With IMO.	_	0.58	0.8	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Cortex M4.	Minimum R	egulator Current Mode					
SIDLPA5		Execute from Flash. CM4 Active 8 MHz, CM0+ Sleep 8 MHz. With	_	0.52	0.75	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDLFAJ	I _{DD25}	IMO. While(1).	_	0.76	1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDLPA6		Execute from Cache. CM4 Active 8 MHz, CM0+ Sleep 8 MHz. With	_	0.54	0.76	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
	I _{DD26}	IMO. Dhrystone.		0.78	1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Cortex M0+	•. Minimum	Regulator Current Mode					
SIDLPA7	I _{DD27}	Execute from Flash. CM4 Off, CM0+ Active 8 MHz. With IMO.	_	0.51	0.75	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
		While (1).	_	0.75	1	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
SIDLPA8	I _{DD28}	Execute from Cache. CM4 Off, CM0+ Active 8 MHz. With IMO.	_	0.48	0.7	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
	'DD28	Dhrystone.	_	0.7	0.95	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Cortex M4.	Minimum R	egulator Current Mode					
SIDLPS5		CM4 Sleep 8 MHz, CM0 Sleep 8 MHz.	_	0.4	0.6	mA	V _{DDD} = 3.3 V, Buck ON, Max at 60 °C
	I _{DD29}	With IMO.	_	0.57	0.8	mA	V _{DDD} = 1.8 V, Buck ON, Max at 60 °C
Cortex M0+	. Minimum	Regulator Current Mode				•	•
SIDLPS7	1	CM4 Off, CM0+ Sleep 8 MHz. With	-	0.39	0.6	mA	V_{DDD} = 3.3 V, Buck ON, Max at 60 °C
SIDLFSI	I _{DD31}	IMO.	_	0.56	0.8	mA	V_{DDD} = 1.8 V, Buck ON, Max at 60 °C
Deep Sleep	o Mode						
SIDDS2	I _{DD33B}	With internal buck enabled and 160K SRAM retention	-	11	-	μA	
Hibernate I	Node						
SIDHIB1	I _{DD34}	V _{DDD} = 1.8 V	_	300	-	nA	No clocks running
SIDHIB2	I _{DD34A}	V _{DDD} = 3.3 V	_	800	_	nA	No clocks running
Power Mod	le Transitior	n Times					
SID12	T _{LPACT_AC}	Minimum regulator current to LP transition time	-	-	35	μs	Including PLL lock time
SID13	T _{DS_LPACT}	Deep Sleep to LP transition time	_	-	25	μs	Guaranteed by design
SID14	T _{HIB_ACT}	Hibernate to LP transition time	_	500	_	μs	Including PLL lock time



XRES

Table 15. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID17	T _{XRES_IDD}	IDD when XRES asserted	-	300	-	nA	V _{DDD} = 1.8 V
SID17A	T _{XRES_IDD_1}	IDD when XRES asserted	-	800	-	nA	V _{DDD} = 3.3 V
SID77	V _{IH}	Input voltage high threshold	0.7 × V _{DD}	_	-	V	CMOS Input
SID78	V _{IL}	Input voltage low threshold	-	_	0.3 × V _{DD}	V	CMOS Input
SID80	C _{IN}	Input capacitance	-	3	Ι	pF	-
SID81	V _{HYSXRES}	Input voltage hysteresis	-	100	Ι	mV	_
SID82	IDIODE	Current through protection diode to V_{DD}/V_{SS}	_	_	100	μA	-

Table 16. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID15	T _{XRES_ACT}	Time from XRES release to Cortex-M0+ executing application code	_	750	-		Not minimum regulator current mode; Cortex-M0+ executing at 50 MHz
SID16	T _{XRES_PW}	XRES Pulse width	5	-	-	μs	-

GPIO

Table 17. GPIO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SID57	V _{IH}	Input voltage high threshold	$0.7 \times V_{DD}$	-	-	V	CMOS Input
SID57A	I _{IHS}	Input current when Pad > V _{DDIO} for OVT inputs	-	-	10	μA	Per I ² C Spec
SID58	V _{IL}	Input voltage low threshold	-	-	0.3 × V _{DD}	V	CMOS Input
SID241	V _{IH}	LVTTL input, V _{DD} < 2.7 V	$0.7 \times V_{DD}$	_	-	V	-
SID242	V _{IL}	LVTTL input, V _{DD} < 2.7 V	-	_	0.3 × V _{DD}	V	-
SID243	V _{IH}	LVTTL input, $V_{DD} \ge 2.7 V$	2.0	-	-	V	-
SID244	V _{IL}	LVTTL input, $V_{DD} \ge 2.7 V$	_	-	0.8	V	-
SID59	V _{OH}	Output voltage high level	V _{DD} – 0.5	-	-	V	I _{OH} = 8 mA
SID62A	V _{OL}	Output voltage low level	_	-	0.4	V	I _{OL} = 8 mA
SID63	R _{PULLUP}	Pull-up resistor	3.5	5.6	8.5	kΩ	-
SID64	R _{PULLDOWN}	Pull-down resistor	3.5	5.6	8.5	kΩ	-
SID65	IIL	Input leakage current (absolute value)	-	-	2	nA	25 °C, V _{DD} = 3.0 V
SID65A	I _{IL_CTBM}	Input leakage on CTBm input pins	_	-	4	nA	-
SID66	C _{IN}	Input Capacitance	_	-	5	pF	-
SID67	V _{HYSTTL}	Input hysteresis LVTTL V _{DD} > 2.7 V	100	0	-	mV	-
SID68	V _{HYSCMOS}	Input hysteresis CMOS	$0.05 \times V_{DD}$	_	-	mV	-



Table 17. GPIO DC Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID69	IDIODE	Current through protection diode to V_{DD}/V_{SS}	-	-	100	μ A	-
SID69A	I _{TOT_GPIO}	Maximum total source or sink Chip Current	_	-	200	mA	-

Table 18. GPIO AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SID70	T _{RISEF}	Rise time in Fast Strong Mode. 10% to 90% of V _{DD}	-	_	2.5	ns	Cload = 15 pF, 8 mA drive strength
SID71	T _{FALLF}	Fall time in Fast Strong Mode. 10% to 90% of V _{DD}	-	_	2.5	ns	Cload = 15 pF, 8 mA drive strength
SID72	T _{RISES_1}	Rise time in Slow Strong Mode. 10% to 90% of V _{DD}	52	_	142	ns	Cload = 15 pF, 8 mA drive strength, $V_{DD} \le 2.7 V$
SID72A	T _{RISES_2}	Rise time in Slow Strong Mode. 10% to 90% of V _{DD}	48	-	102	ns	Cload = 15 pF, 8 mA drive strength, 2.7 V < $V_{DD} \le 3.6$ V
SID73	T _{FALLS_1}	Fall time in Slow Strong Mode. 10% to 90% of V _{DD}	44	-	211	ns	Cload = 15 pF, 8 mA drive strength, $V_{DD} \le 2.7 V$
SID73A	T _{FALLS_2}	Fall time in Slow Strong Mode. 10% to 90% of V _{DD}	42	_	93	ns	Cload = 15 pF, 8 mA drive strength, 2.7 V < V _{DD} \leq 3.6 V
SID73G	T _{FALL_I2C}	Fall time (30% to 70% of $V_{DD})$ in Slow Strong mode	20 × V _{DDIO} / 5.5	_	250	ns	Cload = 10 pF to 400 pF, 8-mA drive strength
SID74	F _{GPIOUT1}	GPIO Fout. Fast Strong mode.	-	_	100	MHz	90/10%, 15-pF load, 60/40 duty cycle
SID75	F _{GPIOUT2}	GPIO Fout; Slow Strong mode.	-	_	16.7	MHz	90/10%, 15-pF load, 60/40 duty cycle
SID76	F _{GPIOUT3}	GPIO Fout; Fast Strong mode.	-	-	7	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID245	F _{GPIOUT4}	GPIO Fout; Slow Strong mode.	-	_	3.5	MHz	90/10%, 25-pF load, 60/40 duty cycle
SID246	F _{GPIOIN}	GPIO input operating frequency;1.71 V \leq V _{DD} \leq 3.6 V	-	_	100	MHz	90/10% V _{IO}



Analog Peripherals

Opamp

Table 19. Opamp Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
	I _{DD}	Opamp block current. No load.	_	_	-		-
SID269	I _{DD_HI}	Power = Hi	_	1300	1500	μA	-
SID270	I _{DD_MED}	Power = Med	_	450	600	μA	-
SID271	I _{DD_LOW}	Power = Lo	_	250	350	μA	-
	GBW	Load = 50 pF, 0.1 mA. V _{DDA} \geq 2.7 V	_	-	-		-
SID272	G _{BW_HI}	Power = Hi	6	-	_	MHz	-
SID273	G _{BW_MED}	Power = Med	3	-	-	MHz	-
SID274	G _{BW_LO}	Power = Lo	1	-	-	MHz	-
	I _{OUT_MAX}	$V_{DDA} \ge 2.7 \text{ V}, 500 \text{ mV}$ from rail	_	-	-		-
SID275	I _{OUT_MAX_HI}	Power = Hi	10	-	_	mA	-
SID276	IOUT_MAX_MID	Power = Med	10	-	_	mA	-
SID277	IOUT_MAX_LO	Power = Lo	-	5	-	mA	-
	I _{OUT}	V_{DDA} = 1.71 V, 500 mV from rail	_	-	_		-
SID278	IOUT_MAX_HI	Power = Hi	4	-	-	mA	-
SID279	IOUT_MAX_MID	Power = Med	4	-	-	mA	-
SID280	IOUT_MAX_LO	Power = Lo	_	2	_	mA	-
SID281	V _{IN}	Input voltage range	0	-	V _{DDA} - 0.2	V	Charge pump ON
SID282	V _{CM}	Input common mode voltage	0	-	V _{DDA} - 1.5	V	Charge pump OFF, V _{DDA} ≥ 2.7 V
	V _{OUT}	V _{DDA} ≥ 2.7 V	_	-	_		-
SID283	V _{OUT_1}	Power = Hi, Iload = 10 mA	0.5	-	V _{DDA} - 0.5	V	-
SID284	V _{OUT_2}	Power = Hi, Iload = 1 mA	0.2	-	V _{DDA} - 0.2	V	-
SID285	V _{OUT_3}	Power = Med, Iload = 1 mA	0.2	-	V _{DDA} - 0.2	V	-
SID286	V _{OUT_4}	Power = Lo, Iload = 0.1 mA	0.2	-	V _{DDA} - 0.2	V	-
SID288	V _{OS_TR}	Offset voltage	-1	±0.5	1	mV	Power = Hi, 0.2 V < V _{OUT} < (V _{DDA} - 0.2 V)
SID288A	V _{OS_TR}	Offset voltage	-	±1	-	mV	Power = Med
SID288B	V _{OS_TR}	Offset voltage	_	±2	-	mV	Power = Lo
SID290	V _{OS_DR_TR}	Offset voltage drift	-10	±3	10	µV/°C	Power = Hi, 0.2 V < V _{OUT} < (V _{DDA} - 0.2 V)
SID290A	V _{OS_DR_TR}	Offset voltage drift	_	±10	-	µV/°C	Power = Med
SID290B	V _{OS_DR_TR}	Offset voltage drift	_	±10	-	µV/°C	Power = Lo
SID291	CMRR	DC common mode rejection ratio	67	80	-	dB	V _{DDA} ≥ 2.7 V
SID292	PSRR	Power supply rejection ratio at 1 kHz, 10-mV ripple	70	85	-	dB	V _{DDA} ≥ 2.7 V
SID65A	I _{IL_CTBM}	Input leakage on CTBm input pins	_	_	4	nA	-



Table 19. Opamp Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
Noise							
SID293	VN1	Input-referred, 1 Hz – 1 GHz, power = Hi	_	100	-	μVrms	_
SID294	VN2	Input-referred, 1 kHz, power = Hi	_	180	-	nV/rtHz	_
SID295	VN3	Input-referred, 10 kHz, power = Hi	-	70	-	nV/rtHz	_
SID296	VN4	Input-referred, 100 kHz, power = Hi	_	38	-	nV/rtHz	_
SID297	CLOAD	Stable up to max. load. Performance specs at 50 pF.	_	-	125	pF	_
SID298	SLEW_RATE	Output slew rate	4	-	-	V/µs	Cload = 50 pF, Power = Hi, V _{DDA} ≥2.7 V Refer to Figure 18 and Figure 19.
SID299	T_OP_WAKE	From disable to enable, no external RC dominating	_	25	_	μs	_
	COMP_MODE	Comparator mode; 50-mV overdrive, Trise = Tfall (approx.)	-		_		_
SID300	T _{PD1}	Response time; power = Hi	-	150	-	ns	-
SID301	T _{PD2}	Response time; power = Med	-	400	_	ns	-
SID302	T _{PD3}	Response time; power = Lo	-	2000	_	ns	-
SID303	V _{HYST_OP}	Hysteresis	-	10	—	mV	-
Deep Sleep I		Mode 2 is lowest current range. Mode 1 has higher GBW.					Deep Sleep mode operation: V _{DDA} ≥ 2.7 V. V _{IN} is 0.2 to V _{DDA} −1.5 V
SID_DS_1	I _{DD_HI_M1}	Mode 1, High current	-	1300	1500	μA	Typ at 25 °C
SID_DS_2	IDD_MED_M1	Mode 1, Medium current	_	460	600	μA	Typ at 25 °C
SID_DS_3	I _{DD_LOW_M1}	Mode 1, Low current	-	230	350	μA	Typ at 25 °C
SID_DS_4	I _{DD_HI_M2}	Mode 2, High current	-	120	-	μA	25 °C
SID_DS_5	IDD_MED_M2	Mode 2, Medium current	_	60	_	μA	25 °C
SID_DS_6	IDD_LOW_M2	Mode 2, Low current	_	15	_	μA	25 °C
SID_DS_7	GBW_HI_M1	Mode 1, High current	-	4	-	MHz	25 °C
SID_DS_8	GBW_MED_M1	Mode 1, Medium current	-	2	-	MHz	25 °C
SID_DS_9	GBW_LOW_M1	Mode 1, Low current	-	0.5	-	MHz	25 °C
SID_DS_10	GBW_HI_M2	Mode 2, High current	_	0.5	_	MHz	20-pF load, no DC load 0.2 V to V _{DDA} – 1.5 V
SID_DS_11	GBW_MED_M2	Mode 2, Medium current	_	0.2	_	MHz	20-pF load, no DC load 0.2 V to V _{DDA} – 1.5 V
SID_DS_12	GBW_LOW_M2	Mode 2, Low current	_	0.1	-	MHz	20-pF load, no DC load 0.2 V to V _{DDA} – 1.5 V
SID_DS_13	V _{OS_HI_M1}	Mode 1, High current	_	5	-	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V
SID_DS_14	V _{OS_MED_M1}	Mode 1, Medium current	-	5	-	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V
SID_DS_15	V _{OS_LOW_M1}	Mode 1, Low current	_	5	-	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID_DS_16	V _{OS_HI_M2}	Mode 2, High current	-	5	_	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V
SID_DS_17	V _{OS_MED_M2}	Mode 2, Medium current	-	5	_	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V
SID_DS_18	V _{OS_LOW_M2}	Mode 2, Low current	-	5	_	mV	25 °C, 0.2 V to V _{DDA} – 1.5 V
SID_DS_19	I _{OUT_HI_M1}	Mode 1, High current	-	10	_	mA	Output is 0.5 V to $V_{DDA} - 0.5 V$
SID_DS_20	IOUT_MED_M1	Mode 1, Medium current	-	10	_	mA	Output is 0.5 V to V _{DDA} – 0.5 V
SID_DS_21	I _{OUT_LOW_M1}	Mode 1, Low current	-	4	_	mA	Output is 0.5 V to $V_{DDA} - 0.5 V$
SID_DS_22	I _{OUT_HI_M2}	Mode 2, High current	-	1	_	mA	Output is 0.5 V to $V_{DDA} - 0.5 V$
SID_DS_23	IOUT_MED_M2	Mode 2, Medium current	-	1	_	mA	Output is 0.5 V to V _{DDA} – 0.5 V
SID_DS_24	I _{OUT_LOW_M2}	Mode 2, Low current	_	0.5	_	mA	Output is 0.5 V to V _{DDA} – 0.5 V

Table 19. Opamp Specifications (continued)

Figure 18. Opamp Step Response, Rising

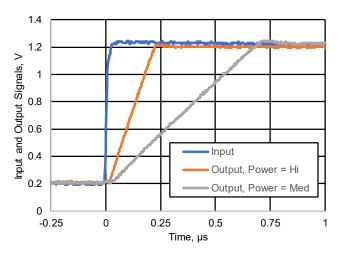
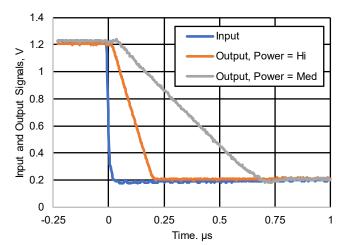


Figure 19. Opamp Step Response, Falling





Low-Power (LP) Comparator

Table 20. LP Comparator DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID84	V _{OFFSET1}	Input offset voltage for COMP1. Normal power mode.	-10	-	10	mV	COMP0 offset is ±25 mV
SID85A	V _{OFFSET2}	Input offset voltage. Low-power mode.	-25	±12	25	mV	-
SID85B	V _{OFFSET3}	Input offset voltage. Ultra low-power mode.	-25	±12	25	mV	-
SID86	V _{HYST1}	Hysteresis when enabled in Normal mode	_	-	60	mV	-
SID86A	V _{HYST2}	Hysteresis when enabled in Low-power mode	-	-	80	mV	-
SID87	V _{ICM1}	Input common mode voltage in Normal mode	0	-	V _{DDIO1} – 0.1	V	-
SID247	V _{ICM2}	Input common mode voltage in Low power mode	0	-	V _{DDIO1} – 0.1	V	-
SID247A	V _{ICM3}	Input common mode voltage in Ultra low power mode	0	-	V _{DDIO1} – 0.1	V	-
SID88	CMRR	Common mode rejection ratio in Normal power mode	50	-	-	dB	-
SID89	I _{CMP1}	Block Current, Normal mode	-	_	150	μA	-
SID248	I _{CMP2}	Block Current, Low power mode	-	_	10	μA	-
SID259	I _{CMP3}	Block Current in Ultra low-power mode	_	0.3	0.85	μA	-
SID90	ZCMP	DC Input impedance of comparator	35	-	-	MΩ	-

Table 21. LP Comparator AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID91	T _{RESP1}	Response time, Normal mode, 100 mV overdrive	_	_	100	ns	—
SID258	T _{RESP2}	Response time, Low power mode, 100 mV overdrive	_	_	1000	ns	-
SID92	T _{RESP3}	Response time, Ultra-low power mode, 100 mV overdrive	_	_	20	μs	-
SID92E	T_CMP_EN1	Time from Enabling to operation	_	_	10	μs	Normal and Low-power modes
SID92F	T_CMP_EN2	Time from Enabling to operation	_	1	50	μs	Ultra low-power mode

Table 22. Temperature Sensor Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID93	T _{SENSACC}	Temperature sensor accuracy	-5	±1	5	°C	–40 to +85 °C

Table 23. Internal Reference Specification

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID93R	V _{REFBG}	_	1.188	1.2	1.212	V	-



SAR ADC

Table 24. 12-bit SAR ADC DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID94	A_RES	SAR ADC Resolution	-	-	12	bits	-
SID95	A_CHNLS_S	Number of channels - single-ended	-	-	16	-	8 full speed.
SID96	A-CHNKS_D	Number of channels - differential	_	-	8	-	Diff inputs use neighboring I/O
SID97	A-MONO	Monotonicity	_	-	-	-	Yes
SID98	A_GAINERR	Gain error	_	-	±0.2	%	With external reference.
SID99	A_OFFSET	Input offset voltage	_	-	2	mV	Measured with 1-V reference
SID100	A_ISAR_1	Current consumption at 1 Msps	_	-	1	mA	At 1 Msps. External Bypass Cap.
SID100A	A_ISAR_2	Current consumption at 1 Msps. Reference = V _{DD}	_	-	1.25	mA	At 1 Msps. External Bypass Cap.
SID101	A_VINS	Input voltage range - single-ended	V _{SS}	-	V _{DDA}	V	-
SID102	A_VIND	Input voltage range - differential	V _{SS}	-	V _{DDA}	V	-
SID103	A_INRES	Input resistance	_	_	2.2	kΩ	-
SID104	A_INCAP	Input capacitance	_	-	10	pF	_

Table 25. 12-bit SAR ADC AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
12-bit SAR	ADC AC Speci	fications					
SID106	A_PSRR	Power supply rejection ratio	70	_	_	dB	-
SID107	A_CMRR	Common mode rejection ratio	66	I	-	dB	Measured at 1 V.
One Megas	ample per sec	ond mode:					
SID108	A_SAMP_1	Sample rate with external reference bypass cap.	_	_	1	Msps	-
SID108A	A_SAMP_2	Sample rate with no bypass cap; Reference = V _{DD}	-	-	250	ksps	-
SID108B	A_SAMP_3	Sample rate with no bypass cap. Internal reference.	-	-	100	ksps	-
SID109	A_SINAD	Signal-to-noise and Distortion ratio (SINAD). V _{DDA} = 2.7 to 3.6 V, 1 Msps.	64	-	_	dB	Fin = 10 kHz
SID111A	A_INL	Integral Non Linearity. V _{DDA} = 2.7 to 3.6 V, 1 Msps	-2	_	2	LSB	Measured with internal V _{REF} = 1.2 V and bypass cap.
SID111B	A_INL	Integral Non Linearity. V _{DDA} = 2.7 to 3.6 V, 1 Msps	-4	-	4	LSB	Measured with external V _{REF} ≥ 1 V and V _{IN} common mode < 2 * Vref.
SID112A	A_DNL	Differential Non Linearity. V _{DDA} = 2.7 to 3.6 V, 1 Msps	–1	-	1.4	LSB	Measured with internal V _{REF} = 1.2 V and bypass cap.
SID112B	A_DNL	Differential Non Linearity. V _{DDA} = 2.7 to 3.6 V, 1 Msps	-1	-	1.7	LSB	Measured with external V _{REF} ≥ 1 V and V _{IN} common mode < 2 * Vref.
SID113	A_THD	Total harmonic distortion. V _{DDA} = 2.7 to 3.6 V, 1 Msps.	_	_	-65	dB	Fin = 10 kHz



DAC

Table 26. 12-bit DAC DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID108D	DAC_RES	DAC resolution	-	-	12	bits	-
SID111D	DAC_INL	Integral non-linearity	-4	Ι	4	LSB	-
SID112D	DAC_DNL	Differential non-linearity	-2	Ι	2	LSB	Monotonic to 11 bits.
SID99D	DAC_OFFSET	Output Voltage zero offset error	-2	-	1	mV	For 000 (hex)
SID103D	DAC_OUT_RES	DAC Output Resistance	-	15	-	kΩ	-
SID100D	DAC_IDD	DAC Current	-	-	125	μA	-
SID101D	DAC_QIDD	DAC Current when DAC stopped	-	-	1	μA	_

Table 27. 12-bit DAC AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID109D	DAC_CONV	DAC Settling time	_	_	2		Driving through CTBm buffer; 25-pF load
SID110D	_ '	Time from Enabling to ready for conversion	_	-	10	μs	_

CSD

Table 28. CapSense Sigma-Delta (CSD) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
CSD V2 Specif	fications	·					
SYS.PER#3	V _{DD_RIPPLE}	Max allowed ripple on power supply, DC to 10 MHz	_	-	±50	mV	$V_{DDA} > 2 V$ (with ripple), 25 °C T _A , Sensitivity = 0.1 pF
SYS.PER#16	V _{DD_RIPPLE_1.8}	Max allowed ripple on power supply, DC to 10 MHz	_	_	±25	mV	V _{DDA} > 1.75 V (with ripple), 25 ° C T _A , Parasitic Capaci- tance (C _P) < 20 pF, Sensitivity ≥ 0.4 pF
SID.CSD.BLK	I _{CSD}	Maximum block current			4500	μA	-
SID.CSD#15	V _{REF}	Voltage reference for CSD and Comparator	0.6	1.2	V _{DDA} – 0.6	V	V _{DDA} – V _{REF} ≥ 0.6 V
SID.CSD#15A	V _{REF_EXT}	External Voltage reference for CSD and Comparator	0.6		V _{DDA} – 0.6	V	V _{DDA} – V _{REF} ≥ 0.6 V
SID.CSD#16	I _{DAC1IDD}	IDAC1 (7-bits) block current	-	-	1900	μA	-
SID.CSD#17	I _{DAC2IDD}	IDAC2 (7-bits) block current	-	-	1900	μA	-
SID308	V _{CSD}	Voltage range of operation	1.7	-	3.6	V	1.71 to 3.6 V
SID308A	V _{COMPIDAC}	Voltage compliance range of IDAC	0.6	-	V _{DDA} – 0.6	V	V _{DDA} – V _{REF} ≥ 0.6 V
SID309	I _{DAC1DNL}	DNL	-1	-	1	LSB	-
SID310	I _{DAC1INL}	INL	-3	-	3	LSB	If V_{DDA} < 2 V then for LSB of 2.4 μ A or less
SID311	I _{DAC2DNL}	DNL	-1	-	1	LSB	_
SID312	I _{DAC2INL}	INL	-3	_	3	LSB	If V_{DDA} < 2 V then for LSB of 2.4 μ A or less



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SNRC of the	following is Ratio	of counts of finger to noise. Guara	anteed	by char	acteriza	tion	
SID313_1A	SNRC_1	SRSS Reference. IMO + FLL Clock Source. 0.1-pF sensitivity	5	-	_	Ratio	9.5-pF max. capacitance
SID313_1B	SNRC_2	SRSS Reference. IMO + FLL Clock Source. 0.3-pF sensitivity	5	-	-	Ratio	31-pF max. capacitance
SID313_1C	SNRC_3	SRSS Reference. IMO + FLL Clock Source. 0.6-pF sensitivity	5	-	-	Ratio	61-pF max. capacitance
SID313_2A	SNRC_4	PASS Reference. IMO + FLL Clock Source. 0.1-pF sensitivity	5	-	-	Ratio	12-pF max. capacitance
SID313_2B	SNRC_5	PASS Reference. IMO + FLL Clock Source. 0.3-pF sensitivity	5	-	-	Ratio	47-pF max. capacitance
SID313_2C	SNRC_6	PASS Reference. IMO + FLL Clock Source. 0.6-pF sensitivity	5	-	-	Ratio	86-pF max. capacitance
SID313_3A	SNRC_7	PASS Reference. IMO + PLL Clock Source. 0.1-pF sensitivity	5	-	-	Ratio	27-pF max. capacitance
SID313_3B	SNRC_8	PASS Reference. IMO + PLL Clock Source. 0.3-pF sensitivity	5	-	-	Ratio	86-pF max. capacitance
SID313_3C	SNRC_9	PASS Reference. IMO + PLL Clock Source. 0.6-pF sensitivity	5	-	-	Ratio	168-pF max. capacitance
SID314	I _{DAC1CRT1}	Output current of IDAC1 (7 bits) in low range	4.2		5.7	μA	LSB = 37.5-nA typ
SID314A	I _{DAC1CRT2}	Output current of IDAC1(7 bits) in medium range	33.7		45.6	μA	LSB = 300-nA typ.
SID314B	I _{DAC1CRT3}	Output current of IDAC1(7 bits) in high range	270		365	μA	LSB = 2.4-µA typ.
SID314C	I _{DAC1CRT12}	Output current of IDAC1 (7 bits) in low range, 2X mode	8		11.4	μA	LSB = 37.5-nA typ. 2X output stage
SID314D	I _{DAC1CRT22}	Output current of IDAC1(7 bits) in medium range, 2X mode	67		91	μA	LSB = 300-nA typ. 2X output stage
SID314E	I _{DAC1CRT32}	Output current of IDAC1(7 bits) in high range, 2X mode. V _{DDA} > 2 V	540		730	μA	LSB = 2.4-µA typ. 2X output stage
SID315	I _{DAC2CRT1}	Output current of IDAC2 (7 bits) in low range	4.2		5.7	μA	LSB = 37.5-nA typ.
SID315A	I _{DAC2CRT2}	Output current of IDAC2 (7 bits) in medium range	33.7		45.6	μA	LSB = 300-nA typ.
SID315B	I _{DAC2CRT3}	Output current of IDAC2 (7 bits) in high range	270		365	μA	LSB = 2.4-µA typ.
SID315C	IDAC2CRT12	Output current of IDAC2 (7 bits) in low range, 2X mode	8		11.4	μA	LSB = 37.5-nA typ. 2X output stage
SID315D	I _{DAC2CRT22}	Output current of IDAC2(7 bits) in medium range, 2X mode	67		91	μA	LSB = 300-nA typ. 2X output stage
SID315E	IDAC2CRT32	Output current of IDAC2(7 bits) in high range, 2X mode. V _{DDA} > 2 V	540		730	μA	LSB = 2.4-µA typ. 2X output stage
SID315F	I _{DAC3CRT13}	Output current of IDAC in 8-bit mode in low range	8		11.4	μA	LSB = 37.5-nA typ.

Table 28. CapSense Sigma-Delta (CSD) Specifications (continued)



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID315G	I _{DAC3CRT23}	Output current of IDAC in 8-bit mode in medium range	67		91	μA	LSB = 300-nA typ.
SID315H	I _{DAC3CRT33}	Output current of IDAC in 8-bit mode in high range. V _{DDA} > 2V	540		730	μA	LSB = 2.4-µA typ.
SID320	IDACOFFSET	All zeroes input	-	-	1	LSB	Polarity set by Source or Sink
SID321	IDACGAIN	Full-scale error less offset	-	-	±15	%	LSB = 2.4-µA typ.
SID322	IDACMISMATCH1	Mismatch between IDAC1 and IDAC2 in Low mode	-	-	9.2	LSB	LSB = 37.5-nA typ.
SID322A	IDACMISMATCH2	Mismatch between IDAC1 and IDAC2 in Medium mode	-	-	6	LSB	LSB = 300-nA typ.
SID322B	IDACMISMATCH3	Mismatch between IDAC1 and IDAC2 in High mode	_	-	5.8	LSB	LSB = 2.4-µA typ.
SID323	I _{DACSET8}	Settling time to 0.5 LSB for 8-bit IDAC	_	-	10	μs	Full-scale transition. No external load.
SID324	I _{DACSET7}	Settling time to 0.5 LSB for 7-bit IDAC	-	-	10	μs	Full-scale transition. No external load.
SID325	CMOD	External modulator capacitor.	-	2.2	-	nF	5-V rating, X7R or NP0 cap.

Table 28. CapSense Sigma-Delta (CSD) Specifications (continued)

Table 29. CSD ADC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
CSDv2 ADC	Specifications						
SIDA94	A_RES	Resolution	_	_	10	bits	Auto-zeroing is required every millisecond
SID95	A_CHNLS_S	Number of channels - single ended	_	_	_	16	-
SIDA97	A-MONO	Monotonicity	-	-	Yes	-	V _{REF} mode
SIDA98	A_GAINERR_VREF	Gain error	_	0.6	_	%	Reference Source: SRSS (V_{REF} = 1.20 V, V_{DDA} < 2.2 V), (V_{REF} = 1.6 V, 2.2 V < V_{DDA} < 2.7 V), (V_{REF} = 2.13 V, V_{DDA} > 2.7 V)
SIDA98A	A_GAINERR_VDDA	Gain error	_	0.2	_	%	$\begin{array}{l} \mbox{Reference Source: SRSS} \\ (V_{REF} = 1.20 \ V, \ V_{DDA} < 2.2 \ V), \\ (V_{REF} = 1.6 \ V, \\ 2.2 \ V < V_{DDA} < 2.7 \ V), \\ (V_{REF} = 2.13 \ V, \ V_{DDA} > 2.7 \ V) \end{array}$
SIDA99	A_OFFSET_VREF	Input offset voltage	_	0.5	-	LSB	After ADC calibration, Ref. Src = SRSS, (V_{REF} = 1.20 V, V_{DDA} < 2.2 V), (V_{REF} = 1.6 V, 2.2 V < V_{DDA} < 2.7 V), (V_{REF} = 2.13 V, V_{DDA} > 2.7 V)
SIDA99A	A_OFFSET_VDDA	Input offset voltage	_	0.5	-	LSB	After ADC calibration, Ref. Src = SRSS, (V_{REF} = 1.20 V, V_{DDA} < 2.2 V), (V_{REF} = 1.6 V, 2.2 V < V_{DDA} < 2.7 V), (V_{REF} = 2.13 V, V_{DDA} > 2.7 V)
SIDA100	A_ISAR_VREF	Current consumption	-	0.3	-	mA	CSD ADC Block current



Table 29.	CSD ADC	Specifications	(continued)
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Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SIDA100A	A_ISAR_VDDA	Current consumption	-	0.3	-	mA	CSD ADC Block current
SIDA101	A_VINS_VREF	Input voltage range - single ended	V _{SSA}	-	V _{REF}	V	(V _{REF} = 1.20 V, V _{DDA} < 2.2 V), (V _{REF} = 1.6 V, 2.2 V < V _{DDA} < 2.7 V), (V _{REF} = 2.13 V, V _{DDA} > 2.7 V)
SIDA101A	A_VINS_VDDA	Input voltage range - single ended	V _{SSA}	-	V _{DDA}	V	
SIDA103	A_INRES	Input charging resistance	_	15	١	kΩ	-
SIDA104	A_INCAP	Input capacitance	-	41	-	pF	-
SIDA106	A_PSRR	Power supply rejection ratio (DC)	-	60	-	dB	-
SIDA107	A_TACQ	Sample acquisition time	_	10	-	μs	Measured with $50-\Omega$ source impedance. 10 µs is default software driver acquisition time setting. Settling to within 0.05%.
SIDA108	A_CONV8	Conversion time for 8-bit resolution at conversion rate = Fhclk/(2"(N+2)). Clock frequency = 50 MHz.	_	25	_	μs	Does not include acquisition time.
SIDA108A	A_CONV10	Conversion time for 10-bit resolution at conversion rate = Fhclk/(2"(N+2)). Clock frequency = 50 MHz.	_	60	-	μs	Does not include acquisition time.
SIDA109	A_SND_VRE	Signal-to-noise and Distortion ratio (SINAD)	-	57	-	dB	Measured with 50-Ω source impedance
SIDA109A	A_SND_VDDA	Signal-to-noise and Distortion ratio (SINAD)	-	52	_	dB	Measured with 50-Ω source impedance
SIDA111	A_INL_VREF	Integral non-linearity. 11.6 ksps	-	-	2	LSB	Measured with 50-Ω source impedance
SIDA111A	A_INL_VDDA	Integral non-linearity. 11.6 ksps	-	_	2	LSB	Measured with 50-Ω source impedance
SIDA112	A_DNL_VREF	Differential non-linearity. 11.6 ksps	-	-	1	LSB	Measured with 50-Ω source impedance
SIDA112A	A_DNL_VDDA	Differential non- linearity. 11.6 ksps	_	-	1	LSB	Measured with 50-Ω source impedance



Digital Peripherals

Table 30. Timer/Counter/PWM (TCPWM) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID.TCPWM.1	I _{TCPWM1}	Block current consumption at 8 MHz	-	-	70	μA	All modes (TCPWM)
SID.TCPWM.2	I _{TCPWM2}	Block current consumption at 24 MHz	-	_	180	μA	All modes (TCPWM)
SID.TCPWM.2A	I _{TCPWM3}	Block current consumption at 50 MHz	-	_	270	μA	All modes (TCPWM)
SID.TCPWM.2B	I _{TCPWM4}	Block current consumption at 100 MHz	-	_	540	μA	All modes (TCPWM)
SID.TCPWM.3	TCPWM _{FREQ}	Operating frequency	-	_	100	MHz	Fc max = Fcpu Maximum = 100 MHz
SID.TCPWM.4	TPWM _{ENEXT}	Input Trigger Pulse Width for all Trigger Events	2 / Fc	_	_	ns	Trigger Events can be Stop, Start, Reload, Count, Capture, or Kill depending on which mode of operation is selected. Fc is counter operating frequency.
SID.TCPWM.5	TPWM _{EXT}	Output Trigger Pulse widths	1.5 / Fc	-	-	ns	Minimum possible width of Overflow, Underflow, and CC (Counter equals Compare value) trigger outputs
SID.TCPWM.5A	TC _{RES}	Resolution of Counter	1 / Fc	_	-	ns	Minimum time between successive counts
SID.TCPWM.5B	PWM _{RES}	PWM Resolution	1 / Fc	Ι	_	ns	Minimum pulse width of PWM Output
SID.TCPWM.5C	Q _{RES}	Quadrature inputs resolution	2 / Fc	_	_	ns	Minimum pulse width between Quadrature phase inputs. Delays from pins should be similar.

Table 31. Serial Communication Block (SCB) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
Fixed I ² C DC S	pecifications						
SID149	I _{I2C1}	Block current consumption at 100 kHz	-	-	30	μ A	-
SID150	I _{I2C2}	Block current consumption at 400 kHz	-	-	80	μ A	-
SID151	I _{I2C3}	Block current consumption at 1 Mbps	-	-	180	μ A	-
SID152	I _{I2C4}	I2C enabled in Deep Sleep mode	-	-	1.7	μ A	At 60 °C
Fixed I ² C AC S	pecifications	·					
SID153	F _{I2C1}	Bit Rate	_	_	1	Mbps	_
Fixed UART D	C Specification	s					
SID160	I _{UART1}	Block current consumption at 100 kbps	-	-	30	μ A	_
SID161	I _{UART2}	Block current consumption at 1000 kbps	-	_	180	μ A	-



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
Fixed UART A	C Specification	าร	1	1			
SID162A	F _{UART1}	Bit Rate	-	_	3	Mbps	ULP Mode
SID162B	F _{UART2}	-	-	-	8		LP Mode
Fixed SPI DC	Specifications	·					
SID163	I _{SPI1}	Block current consumption at 1 Mbps	_	_	220	μ A	-
SID164	I _{SPI2}	Block current consumption at 4 Mbps	-	-	340	μ A	_
SID165	I _{SPI3}	Block current consumption at 8 Mbps	-	_	360	μ A	-
SID165A	I _{SP14}	Block current consumption at 25 Mbps	-	-	800	μ A	_
Fixed SPI AC	Specifications	for LP Mode (1.1 V) unless no	ted ot	herwi	se.		
SID166	F _{SPI}	SPI Operating Frequency Master and Externally Clocked Slave	-	-	25	MHz	14-MHz max for ULP (0.9 V) mode
SID166A	F _{SPI_IC}	SPI Slave Internally Clocked	-	-	15	MHz	5-MHz max for ULP (0.9 V) mode
SID166B	F _{SPI_EXT}	SPI Operating Frequency Master (F _{SCB} is SPI Clock)	-	-	F _{SCB} /4	MHz	F _{SCB} max is 100 MHz in LP mode, 25 MHz max in ULP mode
Fixed SPI Mas	ster mode AC S	pecifications for LP Mode (1.	l V) ur	nless r	noted othe	rwise.	
SID167	T _{DMO}	MOSI Valid after SClock driving edge	-	-	12	ns	20-ns max for ULP (0.9 V) mode
SID168	T _{DSI}	MISO Valid before SClock capturing edge	5	-	-	ns	Full clock, late MISO sampling
SID169	Т _{НМО}	MOSI data hold time	0	-	-	ns	Referred to Slave capturing edge
SID169A	T _{SSELMSCK1}	SSEL Valid to first SCK Valid edge	18	_	-	ns	Referred to Master clock edge
SID169B	T _{SSELMSCK2}	SSEL Hold after last SCK Valid edge	18	_	-	ns	Referred to Master clock edge
Fixed SPI Slav	ve mode AC Sp	ecifications for LP Mode (1.1	V) unl	ess no	oted other	wise.	
SID170	T _{DMI}	MOSI Valid before Sclock Capturing edge	5	_	-	ns	-
SID171A	T _{DSO_EXT}	MISO Valid after Sclock driving edge in Ext. Clk. mode	-	_	20	ns	35-ns max. for ULP (0.9 V) mode
SID171	T _{DSO}	MISO Valid after Sclock driving edge in Internally Clk. Mode	_	_	T _{DSO_EXT} + 3 × Tscb	ns	Tscb is Serial Comm. Block clock period.
SID171B	T _{DSO}	MISO Valid after Sclock driving edge in Internally Clk. Mode with Median filter enabled.	_	_	T _{DSO_EXT} + 4 × Tscb	ns	Tscb is Serial Comm. Block clock period.
SID172	T _{HSO}	Previous MISO data hold time	5	-	-	ns	_
SID172A	TSSEL _{SCK1}	SSEL Valid to first SCK Valid edge	65	-	-	ns	_
SID172B	TSSEL _{SCK2}	SSEL Hold after Last SCK Valid edge	65	_	_	ns	

Table 31. Serial Communication Block (SCB) Specifications (continued)



LCD Specifications

Table 32. LCD Direct Drive DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID154	ILCDLOW	Operating current in low-power mode	-	5	-	μA	16 × 4 small segment display at 50 Hz
SID155	C _{LCDCAP}	LCD capacitance per segment/common driver	Ι	500	5000	pF	-
SID156	LCD _{OFFSET}	Long-term segment offset	-	20	-	mV	-
SID157	I _{LCDOP1}	PWM Mode current. 3.3-V bias. 8-MHz IMO. 25 °C.	-	0.6	-		32 × 4 segments 50 Hz
SID158	I _{LCDOP2}	PWM Mode current. 3.3-V bias. 8-MHz IMO. 25 °C.	-	0.5	-		32 × 4 segments 50 Hz

Table 33. LCD Direct Drive AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID159	F _{LCD}	LCD frame rate	10	50	150	Hz	-

Memory

Flash

Table 34. Flash DC Specifications^[4]

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID173A	I _{PE}	Erase and program current	-	-	6	mA	-

Table 35. Flash AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID174	T _{ROWWRITE}	Row write time (erase & program)	-	-	16	ms	Row = 512 bytes
SID175	T _{ROWERASE}	Row erase time	-	-	11	ms	-
SID176	T _{ROWPROGRAM}	Row program time after erase	-	-	5	ms	-
SID178	T _{BULKERASE}	Bulk erase time (1024 KB)	_	-	11	ms	_
SID179	T _{SECTORERASE}	Sector erase time (256 KB)	-	-	11	ms	512 rows per sector
SID178S	T _{SSERIAE}	Subsector erase time	_	-	11	ms	8 rows per subsector
SID179S	T _{SSWRITE}	Subsector write time; 1 erase plus 8 program times	-	-	51	ms	_
SID180S	T _{SWRITE}	Sector write time; 1 erase plus 512 program times	-	_	2.6	seconds	-
SID180	T _{DEVPROG}	Total device write time	-	-	15	seconds	_
SID181	F _{END}	Flash Endurance	100 k	-	-	cycles	-
SID182	F _{RET1}	Flash Retention. $T_A \le 25 \degree$ C, 100 k P/E cycles	10	_	_	years	-
SID182A	F _{RET2}	Flash Retention. $T_A \le 85 \text{ °C}$, 10 k P/E cycles	10	_	-	years	-
SID182B	F _{RET3}	Flash Retention. $T_A \le 55 \text{ °C}$, 20 k P/E cycles	20	-	_	years	-
SID256	T _{WS100}	Number of Wait states at 100 MHz	3	-	-		-
SID257	T _{WS50}	Number of Wait states at 50 MHz	2	_	_		_

Note

4. It can take as much as 16 milliseconds to write to flash. During this time, the device should not be reset, or flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.



System Resources

Power-on-Reset

Table 36. Power-On-Reset (POR) with Brown-out Detect (BOD) DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID190	V _{FALLPPOR}	BOD trip voltage in system LP and ULP modes.	1.54	_	_	V	Reset guaranteed for V _{DDD} levels below 1.54 V
SID192	V _{FALLDPSLP}	BOD trip voltage in system Deep Sleep mode.	1.54	_	-	V	

Table 37. POR with BOD AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID192A	V _{DDRAMP}	Maximum power supply ramp rate (any supply)	Ι	-	100	mV/µs	System LP mode
SID194A		Maximum power supply ramp rate (any supply) in system Deep Sleep mode	_	_	10	mV/µs	BOD operation guaranteed

Voltage Monitors

Table 38. Voltage Monitors DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID195R	V _{HVD0}		1.18	1.23	1.27	V	-
	V _{HVDI1}		1.38	1.43	1.47	V	-
	V _{HVDI2}		1.57	1.63	1.68	V	-
SID197	V _{HVDI3}		1.76	1.83	1.89	V	-
SID198	V _{HVDI4}		1.95	2.03	2.1	V	-
SID199	V _{HVDI5}		2.05	2.13	2.2	V	-
SID200	V _{HVDI6}		2.15	2.23	2.3	V	-
	V _{HVDI7}		2.24	2.33	2.41	V	-
SID202	V _{HVDI8}		2.34	2.43	2.51	V	-
SID203	V _{HVDI9}		2.44	2.53	2.61	V	-
SID204	V _{HVDI10}		2.53	2.63	2.72	V	-
SID205	V _{HVDI11}		2.63	2.73	2.82	V	-
SID206	V _{HVDI12}		2.73	2.83	2.92	V	-
SID207	V _{HVDI13}		2.82	2.93	3.03	V	-
SID208	V _{HVDI14}		2.92	3.03	3.13	V	-
SID209	V _{HVDI15}		3.02	3.13	3.23	V	-
SID211	LVI_IDD	Block current	1	5	15	μA	-

Table 39. Voltage Monitors AC Specification

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID212	T _{MONTRIP}	Voltage monitor trip time	-	-	170	ns	-



SWD and Trace Interface

Table 40. SWD and Trace Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID214	F_SWDCLK2	$1.7~V \leq V_{DDD} \leq 3.6~V$	_	-	25	MHz	LP mode. V _{CCD} = 1.1 V
SID214L	F_SWDCLK2L	$1.7~V \leq V_{DDD} \leq 3.6~V$	_	Ι	12	MHz	ULP mode. V _{CCD} = 0.9 V
SID215	T_SWDI_SETUP	T = 1/f SWDCLK	0.25 * T	-	-	ns	_
SID216	T_SWDI_HOLD	T = 1/f SWDCLK	0.25 * T	-	-	ns	-
SID217	T_SWDO_VALID	T = 1/f SWDCLK	-	_	0.5 * T	ns	-
SID217A	T_SWDO_HOLD	T = 1/f SWDCLK	1	-	-	ns	-
SID214T	F_TRCLK_LP1	With Trace Data setup/hold times of 2/1 ns respectively	-	-	75	MHz	LP Mode. V _{DD} = 1.1 V
SID215T	F_TRCLK_LP2	With Trace Data setup/hold times of 3/2 ns respectively	-	-	70	MHz	LP Mode. V _{DD} = 1.1 V
SID216T	F_TRCLK_ULP	With Trace Data setup/hold times of 3/2 ns respectively	_	_	25	MHz	ULP Mode. V _{DD} = 0.9 V

Internal Main Oscillator

Table 41. IMO DC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SID218	I _{IMO1}	IMO operating current at 8 MHz	-	9	15	μA	_

Table 42. IMO AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID223	F _{IMOTOL1}	Frequency variation centered on 8 MHz	-	-	±2	%	-
SID227	T _{JITR}	Cycle-to-Cycle and Period jitter	-	±250	-	ps	-

Internal Low-Speed Oscillator

Table 43. ILO DC Specification

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SID231	I _{ILO2}	ILO operating current at 32 kHz	-	0.3	0.7	μA	_

Table 44. ILO AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID234	T _{STARTILO1}	ILO startup time	-	-	7	116	Startup time to 95% of final frequency
SID236	T _{LIODUTY}	ILO Duty cycle	45	50	55	%	-
SID237	F _{ILOTRIM1}	ILO frequency	28.8	32	36.1	kHz	Factory trimmed



Crystal Oscillator

Table 45. ECO Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions				
MHz ECO	MHz ECO DC Specifications										
SID316	I _{DD_MHz}	Block operating current with Cload up to 18 pF	_	800	1600	μA	Max = 35 MHz, Typ = 16 MHz				
MHz ECO	MHz ECO AC Specifications										
SID317	F_MHz	Crystal frequency range	16	-	35	MHz	-				
kHz ECO	DC Specification										
SID318	I _{DD_kHz}	Block operating current with 32-kHz crystal	-	0.38	1	μA	-				
SID321E	ESR32K	Equivalent Series Resistance	_	80	_	kΩ	-				
SID322E	PD32K	Drive level	_	-	1	μW	-				
kHz ECO	AC Specification										
SID319	F_kHz	32-kHz frequency	_	32.768	_	kHz	-				
SID320	Ton_kHz	Startup time	-	-	500	ms	-				
SID320E	F _{TOL32K}	Frequency tolerance	_	50	250	ppm	-				

External Clock

Table 46. External Clock Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID305	EXTCLK _{FREQ}	External Clock input Frequency	0	-	100	MHz	-
SID306	EXTCLK _{DUTY}	Duty cycle; Measured at V _{DD/2}	45	-	55	%	-

PLL

Table 47. PLL Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID304P	PLL_IN	Input frequency to PLL block	4	-	64	MHz	
SID305P	PLL_LOCK	Time to achieve PLL Lock	-	16	35	μs	-
SID306P	PLL_OUT	Output frequency from PLL Block	10.625	-	150	MHz	-
SID307P	PLL_IDD	PLL Current	-	0.55	1.1	mA	Typ at 100 MHz out.
SID308P	PLL_JTR	Period Jitter	-	_	150	ps	100-MHz output frequency

Clock Source Switching Time

Table 48. Clock Source Switching Time Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID262	TCLK _{SWITCH}	Clock switching from clk1 to clk2 in clock periods ^[5]	Ι	Ι	4 clk1 + 3 clk2	periods	_

Note

5. As an example, if the clk_path[1] source is changed from the IMO to the FLL (see Figure 3) then clk1 is the IMO and clk2 is the FLL.



FLL

Table 49. Frequency Locked Loop (FLL) Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID450	FLL_RANGE	Input frequency range.	0.001	_	100	MHz	Lower limit allows lock to USB SOF signal (1 kHz). Upper limit is for External input.
SID451	FLL_OUT_DIV2	Output frequency range. V _{CCD} = 1.1 V	24.00	_	100.00	MHz	Output range of FLL divided-by-2 output
SID451A	FLL_OUT_DIV2	Output frequency range. V _{CCD} = 0.9 V	24.00	_	50.00	MHz	Output range of FLL divided-by-2 output
SID452	FLL_DUTY_DIV2	Divided-by-2 output; High or Low	47.00	-	53.00	%	_
SID454	FLL_WAKEUP	Time from stable input clock to 1% of final value on deep sleep wakeup	_	_	7.50	μs	With IMO input, less than 10 °C change in temperature while in Deep Sleep, and Fout ≥ 50 MHz.
SID455	FLL_JITTER	Period jitter (1 sigma at 100 MHz)	-	-	35.00	ps	50 ps at 48 MHz, 35 ps at 100 MHz
SID456	FLL_CURRENT	CCO + Logic current	_	_	5.50	µA/MHz	_

UDB

Table 50. UDB AC Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
Data Path	Performance	· · · ·					
SID249	F _{MAX-TIMER}	Max frequency of 16-bit timer in a UDB pair	_	_	100	MHz	-
SID250	F _{MAX-ADDER}	Max frequency of 16-bit adder in a UDB pair	_	-	100	MHz	-
SID251	F _{MAX_CRC}	Max frequency of 16-bit CRC/PRS in a UDB pair	_	-	100	MHz	-
PLD Perfor	rmance in UDB						
SID252	F _{MAX_PLD}	Max frequency of 2-pass PLD function in a UDB pair	_	-	100	MHz	-
Clock to O	utput Performanc	e					
SID253	T _{CLK_OUT_UDB1}	Prop. delay for clock in to data out	_	5	-	ns	-
UDB Port A Conditions:	Adapter Specificat 10-pF load, 3-V V	i ons _{DDIO} and V _{DDD}					
SID263	T _{LCLKDO}	LCLK to Output delay	-	I	11	ns	LCLK is a selected clock; for more information see the TRM
SID264	T _{DINLCLK}	Input setup time to LCLK rising edge	_	-	7	ns	-
SID265	T _{DINLCLKHLD}	Input hold time from LCLK rising edge	5	-	-	ns	-
SID266	T _{LCLKHIZ}	LCLK to Output tristated	_	-	28	ns	-
SID267	T _{FLCLK}	LCLK frequency	_	-	33	MHz	-
SID268	T _{LCLKDUTY}	LCLK duty cycle (percentage high)	40%	—	60%	%	-



USB

Table 51. USB Specifications (USB requires LP Mode 1.1-V Internal Supply)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions				
USB Block	USB Block Specifications										
SID322U	Vusb_3.3	Device supply for USB operation	3.15	-	3.6	V	USB Configured				
SID323U	Vusb_3	Device supply for USB operation (functional operation only)	2.85	-	3.6	V	USB Configured				
SID325U	lusb_config	Block supply current in Active mode	-	8	-	mA	V _{DDD} = 3.3 V				
SID328	lusb_suspend	Block supply current in suspend mode	_	0.5	-	mA	V _{DDD} = 3.3 V, Device connected				
SID329	lusb_suspend	Block supply current in suspend mode	_	0.3	-	mA	V _{DDD} = 3.3 V, Device disconnected				
SID330U	USB_Drive_Res	USB driver impedance	28	-	44	Ω	Series resistors are on chip				
SID331U	USB_Pulldown	USB pull-down resistors in Host mode	14.25	-	24.8	kΩ	-				
SID332U	USB_Pullup_Idle	Idle mode range	900	-	1575	Ω	Bus idle				
SID333U	USB_Pullup	Active mode	1425	-	3090	Ω	Upstream device transmitting				

QSPI

Table 52. QSPI Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
SMIF QSPI Sp	ecifications. All	specs with 15-pF load.					
SID390Q	Fsmifclock	SMIF QSPI output clock frequency	_	_	80	MHz	LP mode (1.1 V)
SID390QU	Fsmifclocku	SMIF QSPI output clock frequency	-	_	50	MHz	ULP mode (0.9 V). Guaranteed by Char.
SID397Q	ldd_qspi	Block current in LP mode (1.1 V)	-	-	1900	μA	LP mode (1.1 V)
SID398Q	ldd_qspi_u	Block current in ULP mode (0.9 V)	_	-	590	μA	ULP mode (0.9 V)
SID391Q	Tsetup	Input data set-up time with respect to clock capturing edge	4.5	-	-	ns	-
SID392Q	Tdatahold	Input data hold time with respect to clock capturing edge	0	_	-	ns	-
SID393Q	Tdataoutvalid	Output data valid time with respect to clock falling edge	-	-	3.7	ns	7.5-ns max for ULP mode (0.9 V)
SID394Q	Tholdtime	Output data hold time with respect to clock rising edge	3	_	-	ns	-
SID395Q	Tseloutvalid	Output Select valid time with respect to clock rising edge	-	-	7.5	ns	15-ns max for ULP mode (0.9 V)
SID396Q	Tselouthold	Output Select hold time with respect to clock rising edge	0.5* Tsclk	-	-	ns	Tsclk = Fsmifclk cycle time



Audio Subsystem

Table 53. Audio Subsystem Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
PDM Speci	fications						
SID400P	PDM_IDD1	PDM Active current, Stereo operation, 1-MHz clock	_	175	_	μA	16-bit audio at 16 ksps
SID401	PDM_IDD2	PDM Active current, Stereo operation, 3-MHz clock	-	600	-	μΑ	24-bit audio at 48 ksps
SID402 ^[6]	PDM_JITTER	RMS Jitter in PDM clock	-200	-	200	ps	-
SID403 ^[6]	PDM_CLK	PDM Clock speed	0.384	-	3.072	MHz	-
SID403A ^[6]	PDM_BLK_CLK	PDM Block input clock	1.024	-	49.152	MHz	-
SID403B ^[6]	PDM_SETUP	Data input set-up time to PDM_CLK edge	10	-	_	ns	-
	PDM_HOLD	Data input hold time to PDM_CLK edge	10	-	_	ns	-
SID404 ^[6]	PDM_OUT	Audio sample rate	8	-	48	ksps	_
SID405 ^[6]	PDM_WL	Word Length	16	-	24	bits	-
SID406 ^[6]	PDM_SNR	Signal-to-Noise Ratio (A-weighted)	_	100	_	dB	PDM input, 20 Hz to 20 kHz BW
SID407 ^[6]	PDM_DR	Dynamic Range (A-weighted)	-	100	_	dB	20 Hz to 20 kHz BW, –60 dB FS
SID408 ^[6]	PDM_FR	Frequency Response	-0.2	-	0.2	dB	DC to 0.45f. DC Blocking filter off.
SID409 ^[6]	PDM_SB	Stop Band	-	0.566	_	f	-
SID410 ^[6]	PDM_SBA	Stop Band Attenuation	-	60	_	dB	-
SID411 ^[6]	PDM_GAIN	Adjustable Gain	-12	-	10.5	dB	PDM to PCM, 1.5 dB/step
SID412 ^[6]	PDM_ST	Startup time	-	48	-	WS	(Word Select) cycles
I2S Specific	cations. The same	for LP and ULP modes unless s	tated otherwise.				
SID415	I2S_IDD	Block current	-	400	-	μA	
SID413	I2S_WORD	Length of I2S Word	8	-	32	bits	-
SID414	I2S_WS	Word Clock frequency in LP mode	-	-	192	kHz	12.288-MHz bit clock with 32-bit word
SID414M	12S_WS_U	Word Clock frequency in ULP mode	-	-	48	kHz	3.072-MHz bit clock with 32-bit word
SID414A	I2S_WS_TDM	Word Clock frequency in TDM mode for LP	-	-	48	kHz	Eight 32-bit channels
SID414X	I2S_WS_TDM_U	Word Clock frequency in TDM mode for ULP	-	-	12	kHz	Eight 32-bit channels
I2S Slave N	lode						
SID430	TS_WS	WS Setup Time to the Following Rising Edge of SCK for LP Mode	5	-	_	ns	-
SID430U	TS_WS	WS Setup Time to the Following Rising Edge of SCK for ULP Mode	11	-	_	ns	-
SID430A	TH_WS	WS Hold Time to the Following Edge of SCK	TMCLK_SOC ^[7] + 5	-	_	ns	-

Notes

Guaranteed by design, not production tested.
 TMCLK_SOC is the internal I2S master clock period.



Table 53. Audio Subsystem Specifications (continued)

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID432	TD_SDO	Delay Time of TX_SDO Transition from Edge of TX_SCK for LP mode	 (TMCLK_SOC + 5)	_	TMCLK_SOC +	ns	Associated clock edge depends on selected polarity
SID432U	TD_SDO	Delay Time of TX_SDO Transition from Edge of TX_SCK for ULP mode	(TMCLK_SOC + 70)	_	TMCLK_SOC +	ns	Associated clock edge depends on selected polarity
SID433	TS_SDI	RX_SDI Setup Time to the Following Edge of RX_SCK in Lp Mode	5	-	-	ns	-
SID433U	TS_SDI	RX_SDI Setup Time to the Following Edge of RX_SCK in ULP mode	11	-	-	ns	-
SID434	TH_SDI	RX_SDI Hold Time to the Rising Edge of RX_SCK	TMCLK_SOC +	-	-	ns	-
SID435	TSCKCY	TX/RX_SCK Bit Clock Duty Cycle	45	-	55	%	-
I2S Master	Mode						
SID437	TD_WS	WS Transition Delay from Falling Edge of SCK in LP mode	-10	-	20	ns	-
SID437U	TD_WS_U	WS Transition Delay from Falling Edge of SCK in ULP mode	-10	-	40	ns	-
SID438	TD_SDO	SDO Transition Delay from Falling Edge of SCK in LP mode	-10	-	20	ns	-
SID438U	TD_SDO	SDO Transition Delay from Falling Edge of SCK in ULP mode	-10	-	40	ns	-
SID439	TS_SDI	SDI Setup Time to the Associated Edge of SCK	5	-	-	ns	Associated clock edge depends on selected polarity
SID440	TH_SDI	SDI Hold Time to the Associated Edge of SCK	TMCLK_SOC +	-	_	ns	T is TX/RX_SCK Bit Clock period. Associated clock edge depends on selected polarity.
SID443	TSCKCY	SCK Bit Clock Duty Cycle	45	_	55	%	-
SID445	FMCLK_SOC	MCLK_SOC Frequency in LP mode	1.024	_	98.304	MHz	FMCLK_SOC = 8 * Bit-clock
SID445U	FMCLK_SOC_U	MCLK_SOC Frequency in ULP mode	1.024	_	24.576	MHz	FMCLK_SOC_U = 8 * Bit-clock
SID446	TMCLKCY	MCLK_SOC Duty Cycle	45	-	55	%	-
SID447	TJITTER	MCLK_SOC Input Jitter	-100	-	100	ps	-



Smart I/O

Table 54. Smart I/O Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID420	SMIO_BYP	Smart I/O Bypass delay	-	-	2	ns	-
SID421	SMIO_LUT	Smart I/O LUT prop delay	-	8	-	ns	-

Precision ILO (PILO)

Table 55. PILO Specifications

Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID 430R	I _{PILO}	Operating current	-	1.2	4	μA	-
SID431	F_PILO	PILO nominal frequency	-	32768	-	Hz	T = 25 °C
SID432R	ACC_PILO	PILO accuracy with periodic calibration	-500	-	500	ppm	-

JTAG Boundary Scan

Table 56. JTAG Boundary Scan

Sp	ec ID#	Parameter	Description	Min	Тур	Max	Units				
JTAG Boun	dary Scan Para	meters									
JTAG Boundary Scan Parameters for 1.1 V (LP) Mode Operation:											
SID468	TCKLOW	TCK LOW	52	Ι	-	ns	-				
SID469	TCKHIGH	TCK HIGH	10	-	-	ns	-				
SID470	TCK_TDO	TCK falling edge to output valid		_	40	ns	-				
SID471	TSU_TCK	Input valid to TCK rising edge	12	_	-	ns	-				
SID472	TCk_THD	Input hold time to TCK rising edge	10	-	-	ns	-				
SID473	TCK_TDOV	TCK falling edge to output valid (High-Z to Active).	40	_	I	ns	-				
SID474	TCK_TDOZ	TCK falling edge to output valid (Active to High-Z).	40	_	Ι	ns	-				
JTAG Bound	dary Scan Para	meters for 0.9 V (ULP) Mode Operation	on:								
SID468A	TCKLOW	TCK low	102	-	-	ns	-				
SID469A	TCKHIGH	TCK high	20	_	-	ns	-				
SID470A	TCK_TDO	TCK falling edge to output valid		_	80	ns	-				
SID471A	TSU_TCK	Input valid to TCK rising edge	22	_	-	ns	-				
SID472A	TCk_THD	Input hold time to TCK rising edge	20	_	-	ns	-				
SID473A	TCK_TDOV	TCK falling edge to output valid (high-Z to active).	80	-	-	ns	-				
SID474A	TCK_TDOZ	TCK falling edge to output valid (active to high-Z).	80	-	-	ns	-				



Bluetooth LE

Table 57. Bluetooth LE Subsystem Specifications

Spec ID#	Parameter	Description	Min	Тур	Мах	Unit	Details / Conditions
RF Receiv	er Specifications	s (1 Mbps)					
SID317R	RXS,IDLE	RX Sensitivity with Ideal Trans- mitter	_	-95	-	dBm	Across RF Operating Frequency Range
SID317RR	RXS,IDLE	RX Sensitivity with Ideal Trans- mitter	-	-93	_	dBm	255-byte packet length, across Frequency Range
SID318R	RXS,DIRTY	RX Sensitivity with Dirty Transmitter	-	-92	-	dBm	RF-PHY Specification (RCV-LE/CA/01/C)
SID319R	PRXMAX	Maximum received signal strength at < 0.1% PER	_	0	_	dBm	RF-PHY Specification (RCV-LE/CA/06/C)
SID320R	CI1	Co-channel interference, Wanted Signal at –67 dBm and Interferer at FRX	-	9	21	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID321R	CI2	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at FRX ± 1 MHz	-	3	15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID322R	CI3	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at FRX ± 2 MHz	-	-26	-17	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID323R	Cl4	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at ≥ FRX ± 3 MHz	_	-33	-27	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID324R	CI5	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (FIMAGE)	_	-20	-9	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID325R	C16	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (FIMAGE ± 1 MHz)	_	-28	-15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
RF Receiv	er Specifications	s (2 Mbps)					
SID326	RXS,IDLE	RX Sensitivity with Ideal Trans- mitter	_	-92	_	dBm	Across RF Operating Frequency Range
SID326R	RXS,IDLE	RX Sensitivity with Ideal Trans- mitter	-	-90	_	dBm	255-byte packet length, across Frequency Range
SID327	RXS,DIRTY	RX Sensitivity with Dirty Transmitter	_	-89	_	dBm	RF-PHY Specification (RCV-LE/CA/01/C)
SID328R	PRXMAX	Maximum received signal strength at < 0.1% PER	_	0	_	dBm	RF-PHY Specification (RCV-LE/CA/06/C)
SID329R	CI1	Co-channel interference, Wanted Signal at –67 dBm and Interferer at FRX	-	9	21	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID330	CI2	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at FRX ± 2 MHz	-	3	15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID331	CI3	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at FRX ± 4 MHz	_	-26	-17	dB	RF-PHY Specification (RCV-LE/CA/03/C)



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID332	Cl4	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at ≥ FRX ± 6 MHz	_	-33	-27	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID333	CI5	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (FIMAGE)	_	-20	-9	dB	RF-PHY Specification (RCV-LE/CA/03/C)
SID334	CI6	Adjacent channel interference Wanted Signal at –67 dBm and Interferer at Image frequency (FIMAGE ± 2MHz)	_	-28	-15	dB	RF-PHY Specification (RCV-LE/CA/03/C)
RF Receiv	er Specification (1 & 2 Mbps)					
SID338	OBB1	Out of Band Blocking Wanted Signal at –67 dBm and Interferer at F = 30–2000 MHz	-30	-27	-	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID339	OBB2	Out of Band Blocking Wanted Signal at –67 dBm and Interferer at F = 2003–2399 MHz	-35	-27	Ι	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID340	OBB3	Out of Band Blocking, Wanted Signal at –67 dBm and Interferer at F= 2484–2997MHz	-35	-27	-	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID341	OBB4	Out of Band Blocking Wanted Signal at –67 dBm and Interferer at F= 3000–12750 MHz	-30	-27	-	dBm	RF-PHY Specification (RCV-LE/CA/04/C)
SID342	IMD	Intermodulation Performance Wanted Signal at –64 dBm and 1 Mbps Bluetooth LE, 3rd, 4th, and 5th offset channel	-50	-	_	dBm	RF-PHY Specification (RCV-LE/CA/05/C)
SID343	RXSE1	Receiver Spurious emission 30 MHz to 1.0 GHz	-	-	-57	dBm	100-kHz measurement bandwidth ETSI EN300 328 V2.1.1
SID344	RXSE2	Receiver Spurious emission 1.0 GHz to 12.75 GHz	_	-	-53	dBm	1-MHz measurement bandwidth ETSI EN300 328 V2.1.1
RF Transm	itter Specificatio	ons	I	_	1	-	
SID345	TXP,ACC	RF Power Accuracy	–1	-	1	dB	-
SID346	TXP,RANGE	Frequency Accuracy	-	24	_	dB	–20 dBm to +4 dBm
SID347	TXP,0dBm	Output Power, 0 dB Gain setting	_	0	-	dBm	-
SID348	TXP,MAX	Output Power, Maximum Power Setting	Ι	4	Ι	dBm	-
SID349	TXP,MIN	Output Power, Minimum Power Setting	-	-20	_	dBm	-
SID350	F2AVG	Average Frequency deviation for 10101010 pattern	185	-	_	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID350R	F2AVG_2M	Average Frequency deviation for 10101010 pattern for 2 Mbps	370	-	-	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID351	F1AVG	Average Frequency deviation for 11110000 pattern	225	250	275	kHz	RF-PHY Specification (TRM-LE/CA/05/C)

Table 57. Bluetooth LE Subsystem Specifications (continued)



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions
SID351R	F1AVG_2M	Average Frequency deviation for 11110000 pattern for 2 Mbps	450	500	550	kHz	RF-PHY Specification (TRM-LE/CA/05/C)
SID352	EO	Eye opening = Δ F2AVG/ Δ F1AVG	0.8	_	-	-	RF-PHY Specification (TRM-LE/CA/05/C)
SID353	FTX,ACC	Frequency Accuracy	-150	_	150	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID354	FTX,MAXDR	Maximum Frequency Drift	-50	_	50	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID355	FTX,INITDR	Initial Frequency drift	-20	_	20	kHz	RF-PHY Specification (TRM-LE/CA/06/C)
SID356	FTX,DR	Maximum Drift Rate	-20	_	20	kHz/ 50 μs	RF-PHY Specification (TRM-LE/CA/06/C)
SID357	IBSE1	In Band Spurious Emission at 2 MHz offset (1 Mbps) In Band Spurious Emission at 4 MHz offset (2 Mbps)	_	_	-20	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID358	IBSE2	In Band Spurious Emission at ≥ 3 MHz offset (1 Mbps) In Band Spurious Emission at ≥ 6 MHz offset (2 Mbps)	_	_	-30	dBm	RF-PHY Specification (TRM-LE/CA/03/C)
SID359	TXSE1	Transmitter Spurious Emissions (Averaging), < 1.0 GHz	_	_	-55.5	dBm	FCC-15.247
SID360	TXSE2	Transmitter Spurious Emissions (Averaging), > 1.0 GHz			-41.5	dBm	FCC-15.247
RF Curren	t Specification						·
SID361	IRX1_wb	Receive Current (1 Mbps)	-	6.7	-	mA	VDD_NS = V _{DDD} = 3.3 V current with buck
SID362	ITX1_wb_0dBm	TX Current at 0 dBm setting (1 Mbps)	-	5.7	-	mA	VDD_NS = V _{DDD} = 3.3 V current with buck
SID363	IRX1_nb	Receive Current (1 Mbps)	-	11	-	mA	V _{DDD} current without buck
SID364	ITX1_nb_0dBm	TX Current at 0-dBm setting (1 Mbps)	-	10	-	mA	V _{DDD} current without buck
SID365	ITX1_nb_4dBm	TX Current at 4-dBm setting (1 Mbps)	-	13	-	mA	V _{DDD} current without buck
SID365R	ITX1_wb_4dBm	TX Current at 4-dBm setting (1 Mbps)	-	8.5	-	mA	VDD_NS = V _{DDD} = 3.3 V current with buck
SID366	ITX1_nb_20dBm	TX Current at –20-dBm setting (1 Mbps)	_	7	-	mA	V _{DDD} current without buck
SID367	IRX2_wb	Receive Current (2 Mbps)	_	7	-	mA	VDD_NS = V _{DDD} = 3.3 V current with buck
SID368	ITX2_wb_0dBm	TX Current at 0-dBm setting (2 Mbps)	_	5.7	_	mA	VDD_NS = V _{DDD} = 3.3 V current with buck
SID369	IRX2_nb	Receive Current (2 Mbps)	-	11.3	_	mA	V _{DDD} current without buck
SID370	ITX2_nb_0dBm	TX Current at 0-dBm setting (2 Mbps)	_	10	_	mA	V _{DDD} current without buck
SID371	ITX2_nb_4dBm	TX Current at 4-dBm setting (2 Mbps)	_	13	-	mA	V _{DDD} current without buck

Table 57. Bluetooth LE Subsystem Specifications (continued)



Spec ID#	Parameter	Description	Min	Тур	Max	Unit	Details / Conditions		
SID371R	ITX2_wb_4dBm	TX Current at 4-dBm setting (2 Mbps)	Ι	8.5	-	mA	VDD_NS = V _{DDD} = 3.3 V current with buck		
SID372	ITX2_nb_20dBm	TX Current at –20-dBm setting (2 Mbps)	Ι	7	-	mA	V _{DDD} current without buck		
General RI	General RF Specification								
SID373	FREQ	RF operating frequency	2400	-	2482	MHz	-		
SID374	CHBW	Channel spacing	-	2	-	MHz	_		
SID375	DR1	On-air Data Rate (1 Mbps)	-	1000	-	kbps	_		
SID376	DR2	On-air Data Rate (2 Mbps)	-	2000	-	kbps	_		
SID377	TXSUP	Transmitter Startup time	-	80	82	μs	_		
SID378	RXSUP	Receiver Startup time	-	80	82	μs	_		
RSSI Spec	RSSI Specification								
SID379	RSSI,ACC	RSSI Accuracy	-4	-	4	dB	–95 dBm to –20 dBm measurement range		
SID380	RSSI,RES	RSSI Resolution	-	1	-	dB	_		
SID381	RSSI,PER	RSSI Sample Period	-	6	-	μs	_		
System-Le	System-Level Bluetooth LE Specifications								
SID433R	Adv_Pwr	1.28s, 32 bytes, 0 dBm	-	42	-	μW	3.3 V, Buck, w/o Deep Sleep current		
SID434R	Conn_Pwr_300	300 ms, 0 byte, 0 dBm	_	70	-	μW	3.3 V, Buck, w/o Deep Sleep current		
SID435R	Conn_Pwr_1S	1000 ms, 0 byte, 0 dBm	-	30	_	μW	3.3 V, Buck, w/o Deep Sleep current		
SID436R	Conn_Pwr_4S	4000 ms, 0 byte, 0 dBm	_	4	_	μW	3.3 V, Buck, w/o Deep Sleep current		

Table 57. Bluetooth LE Subsystem Specifications (continued)



Spec ID#	Parameter	Description Min Typ Max Unit Det		Details / Conditions				
16-MHz C	rystal Oscillator							
SID382	FXO1	Crystal frequency	-	16	_	MHz	-	
SID383	ESR1	Equivalent series resistance	-	100	250	Ω	-	
SID384	Txostart1	Startup time	-	400	-	μs	Frequency Stable (16 MHz ±50 ppm)	
SID385	IXO1	Operating current	-	300	-	μA	Includes crystal current, LDO and BG	
32-MHz Crystal Oscillator								
SID386	FXO2	Crystal frequency	-	32	_	MHz	-	
SID387	ESR2	Equivalent series resistance	-	50	100	Ω	-	
SID388	Txostart2	Startup time	-	400	-	μs	Frequency Stable (32 MHz ±50 ppm)	
SID389	IXO2	Operating current	-	350	-	μA	Includes crystal current, LDO and BG	
16-MHz ar	nd 32-MHz Crystal	Oscillator						
SID390	FTOL	Frequency tolerance	-20	-	20	ppm	After trimming, including aging and temp drift	
SID391	PD	Drive level	-	-	100	μW	-	

Table 58. Bluetooth LE ECO Specifications





Ordering Information

Table 59 lists the CYB06447BZI-BLD5x part numbers and features. All devices include a Bluetooth LE radio, DC-DC converter, QSPI SMIF, ADC, DAC, 9 SCBs, 32 TCPWMs, 2 PDM, and I2S. See also the product selector guide.

Table 59. Ordering Information

Family	NdW	CPU Speed (CM4)	CPU Speed (CM0+)	Single CPU/Dual CPU	0LP/LP	Flash (KB)	SRAM (KB)	No. of CTBMs	No. of UDBs	CapSense	GPIOS	СКҮРТО	ASU	Package
64	CYB06447BZI-BLD54	150/50	100/25	Dual	FLEX	1024	288	1	12	Yes	84	Yes	Yes	124-BGA
04	CYB06447BZI-BLD53	150/50	100/25	Dual	FLEX	1024	288	1	12	Yes	78	Yes	No	116-BGA





PSoC 6 MPN Decoder

CY XX 6 A B C DD E - FF G H I JJ K L

Field	Description	Values	Meaning
CY	Cypress	CY	Cypress
		8C	Standard
xx	Firmware	B0	"Secure Boot" v1
,,,,		S0	"Standard Secure" - AWS
6	Architecture	6	PSoC 6
		0	Value
		1	Programmable
А	Line	2	Performance
		3	Connectivity
		4	Secured
		2	100 MHz
В	Speed	3	150 MHz
		4	150/50 MHz
		0-3	Reserved
		4	256K/128K
		5	512K/256K
С	Memory Size (Flash/SRAM)	6	512K/128K
		7	1024K/288K
		8	1024K/512K
		9	Reserved
		Α	2048K/1024K
		AZ, AX	TQFP
		LQ	QFN
DD	Package	BZ	BGA
		FM	M-CSP
		FN, FD, FT	WLCSP

Field	Description	Values Meaning	
		С	Consumer
Е	Temperature Range	I	Industrial
		Q	Extended Industrial
FF	Feature Code		Cypress internal
ГГ	realure Code	S2-S6	
		BL	Integrated Bluetooth LE
G	CPU Core	F	Single Core
9		D	Dual Core
Н	Attributes Code	0–9	Feature set
		1	31–50
I.	GPIO count	2	51–70
I		3	71–90
		4	91–110
JJ	Engineering sample (optional)	ES	Engineering samples or not
к	Die Revision		Base
IX.	r (optional) A1–A		Die revision
L	Tape/Reel Shipment (optional)		



Packaging

This product line is offered in two packages: 124-BGA and 116-BGA.

Table 60. Package Dimensions

Spec ID#	Package	Description	Package Drawing Number
PKG_1	124-BGA	124-BGA, 9 mm \times 9 mm \times 1 mm height with 0.65-mm pitch	001-97718
PKG_2	116-BGA	116-BGA, 5.2 "e 6.4 "e 0.70 mm height with 0.5-mm pitch	002-16574

Table 61. Package Characteristics

Parameter	Description	Conditions	Min	Тур	Max	Units
T _A	Operating ambient temperature	-	-40	25	85	°C
TJ	Operating junction temperature	-	-40	-	100	°C
T _{JA}	Package θ_{JA} (124-BGA)	_	-	64.3	-	°C/watt
T _{JC}	Package θ_{JC} (124-BGA)	-	-	37	-	°C/watt
T _{JA}	Package θ_{JA} (116-BGA)	_	-	36.5	-	°C/watt
T _{JC}	Package θ_{JC} (116-BGA)	_	-	12	-	°C/watt

Table 62. Solder Reflow Peak Temperature

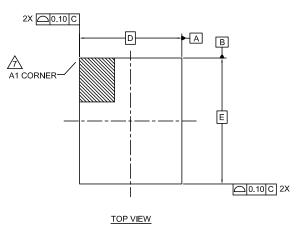
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All packages	260 °C	30 seconds

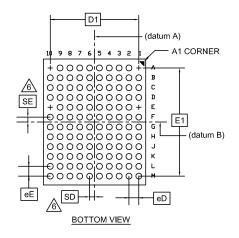
Table 63. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-2

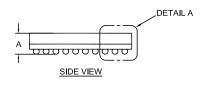
Package	MSL
All packages	MSL 3



Figure 20. 116-BGA 5.2 × 6.4 × 0.70 mm







116XØb → 0.20C 116XØb → 0.1500CAB ↓ 0.20C
<u>DETAIL A</u>

0.44501		DIMENSIONS				
SYMBOL	MIN.	NOM.	MAX.			
A	-	-	0.70			
A1	0.16	0.21	0.26			
D		5.20 BSC				
E	6.40 BSC					
D1	4.50 BSC					
E1	5.50 BSC					
MD	10					
ME		12				
N		116				
Øb	0.25 0.30 0.35					
eD	0.50 BSC					
eE	0.50 BSC					
SD	0.25 BSC					
SE		0.25 BSC				

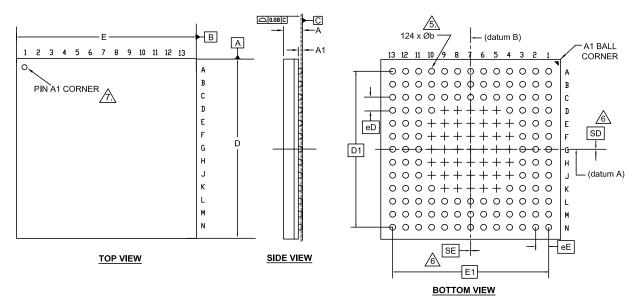
NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
- 3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
- 4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION. SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION. N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- 5 DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- *SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" OR "SE" = 0.
 - WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
- A1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
- 8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.
- 9. JEDEC SPECIFICATION NO. REF: N/A

002-16574 *B







	DIMENSIONS			
SYMBOL	MIN.	NOM.	MAX.	
A	-	-	1.00	
A1	0.16	0.21	0.26	
D	8.90	9.00	9.10	
E	8.90	9.00	9.10	
D1	7.80 BSC			
E1	7.80 BSC			
MD	13			
ME		13		
N		124		
Øb	0.25	0.30	0.35	
eD	0.65 BSC			
еE	0.65 BSC			
SD	0			
SE		0		

NOTES:

- 1. ALL DIMENSIONS ARE IN MILLIMETERS.
- 2. SOLDER BALL POSITION DESIGNATION PER JEP95, SECTION 3, SPP-020.
- 3. "e" REPRESENTS THE SOLDER BALL GRID PITCH.
- 4. SYMBOL "MD" IS THE BALL MATRIX SIZE IN THE "D" DIRECTION. SYMBOL "ME" IS THE BALL MATRIX SIZE IN THE "E" DIRECTION. N IS THE NUMBER OF POPULATED SOLDER BALL POSITIONS FOR MATRIX SIZE MD X ME.
- ▲ DIMENSION "b" IS MEASURED AT THE MAXIMUM BALL DIAMETER IN A PLANE PARALLEL TO DATUM C.
- "SD" AND "SE" ARE MEASURED WITH RESPECT TO DATUMS A AND B AND DEFINE THE POSITION OF THE CENTER SOLDER BALL IN THE OUTER ROW. WHEN THERE IS AN ODD NUMBER OF SOLDER BALLS IN THE OUTER ROW "SD" OR "SE" = 0.
- WHEN THERE IS AN EVEN NUMBER OF SOLDER BALLS IN THE OUTER ROW, "SD" = eD/2 AND "SE" = eE/2.
- A 1 CORNER TO BE IDENTIFIED BY CHAMFER, LASER OR INK MARK METALIZED MARK, INDENTATION OR OTHER MEANS.
- 8. "+" INDICATES THE THEORETICAL CENTER OF DEPOPULATED SOLDER BALLS.
- 9. JEDEC SPECIFICATION NO. REF. : MO-280.

001-97718 *B



Acronyms

Acronym	Description		
3DES	triple DES (data encryption standard)		
ADC	analog-to-digital converter		
AES	advanced encryption standard		
АНВ	AMBA (advanced microcontroller bus architecture) high-performance bus, an Arm data transfer bus		
AMUX	analog multiplexer		
AMUXBUS	analog multiplexer bus		
API	application programming interface		
Arm [®]	advanced RISC machine, a CPU architecture		
BGA	ball grid array		
BOD	brown-out detect		
CAD	computer aided design		
ссо	current controlled oscillator		
CM0+	Cortex-M0+, an Arm CPU		
CM4	Cortex-M4, an Arm CPU		
CMAC	cipher-based message authentication code		
CMOS	complementary metal-oxide-semiconductor, a process technology for IC fabrication		
CMRR	common-mode rejection ratio		
CPU	central processing unit		
CRC	cyclic redundancy check, an error-checking protocol		
CSD	CapSense Sigma-Delta		
CSX	Cypress mutual capacitance sensing method. See also CSD		
DAC	digital-to-analog converter, see also IDAC, VDAC		
DAP	debug access port		
DES	data encryption standard		
DMA	direct memory access, see also TD		
DNL	differential nonlinearity, see also INL		
DSI	digital system interconnect		
DU	data unit		
ECC	elliptic curve cryptography		
ECO	external crystal oscillator		
EEPROM	electrically erasable programmable read-only memory		
EMI	electromagnetic interference		
ESD	electrostatic discharge		
ETM	embedded trace macrocell		
FIFO	first-in, first-out		
FLL	frequency locked loop		
FPU	floating-point unit		

Acronym	Description		
FS	full-speed		
GND	Ground		
GPIO	general-purpose input/output, applies to a PSoC pin		
HMAC	Hash-based message authentication code		
HSIOM	high-speed I/O matrix		
I/O	input/output, see also GPIO, DIO, SIO, USBIO		
l ² C, or IIC	Inter-Integrated Circuit, a communications protocol		
l ² S	inter-IC sound		
IC	integrated circuit		
IDAC	current DAC, see also DAC, VDAC		
IDE	integrated development environment		
ILO	internal low-speed oscillator, see also IMO		
IMO	internal main oscillator, see also ILO		
INL	integral nonlinearity, see also DNL		
loT	internet of things		
IPC	inter-processor communication		
IRQ	interrupt request		
ISR	interrupt service routine		
JTAG	Joint Test Action Group		
LCD	liquid crystal display		
LIN	Local Interconnect Network, a communications protocol		
LP	low power		
LS	low-speed		
LUT	lookup table		
LVD	low-voltage detect, see also LVI		
LVTTL	low-voltage transistor-transistor logic		
MAC	multiply-accumulate		
M-CSP	molded chip scale package		
MCU	microcontroller unit		
MCWDT	multi-counter watchdog timer		
MISO	master-in slave-out		
MMIO	memory-mapped input output		
MOSI	master-out slave-in		
MPU	memory protection unit		
MSL	moisture sensitivity level		
Msps	million samples per second		
MTB	micro trace buffer		
MUL	multiplier		
NC	no connect		
NMI	nonmaskable interrupt		



Acronym	Description		
NVIC	nested vectored interrupt controller		
OTP	one-time programmable		
OVT	overvoltage tolerant		
PASS	programmable analog subsystem		
РСВ	printed circuit board		
PCM	pulse code modulation		
PDM	pulse density modulation		
PHY	physical layer		
PICU	port interrupt control unit		
PLL	phase-locked loop		
PMIC	power management integrated circuit		
POR	power-on reset		
PPU	peripheral protection unit		
PRNG	pseudo random number generator		
PSoC [®]	Programmable System-on-Chip™		
PSRR	power supply rejection ratio		
PWM	pulse-width modulator		
QD	quadrature decoder		
QSPI	quad serial peripheral interface		
RAM	random-access memory		
RISC	reduced-instruction-set computing		
RMS	root-mean-square		
ROM	read-only memory		
RSA Rivest–Shamir–Adleman, a public-key crypto raphy algorithm			
RTC	real-time clock		
RX	receive		
S/H	sample and hold		
SAR	successive approximation register		
SARMUX	SAR ADC multiplexer bus		
SCB	serial communication block		
SFlash	supervisory flash		
SHA	secure hash algorithm		
SINAD	signal to noise and distortion ratio		
SNR signal-to-noise ration			
SOF	start of frame		
SPI	Serial Peripheral Interface, a communications protocol		
SRAM	static random access memory		
SROM	supervisory read-only memory		
SRSS	system resources subsystem		
SWD	serial wire debug, a test protocol		
SWJ	serial wire JTAG		

Acronym	Description	
SWO	single wire output	
SWV	serial-wire viewer	
TCPWM	timer, counter, pulse-width modulator	
TDM	time division multiplexed	
TQFP	thin quad flat package	
TRM	technical reference manual	
TRNG	true random number generator	
ТХ	transmit	
UART	Universal Asynchronous Transmitter Receiver, a communications protocol	
UDB	universal digital block	
ULP	ultra-low power	
USB	Universal Serial Bus	
WCO	watch crystal oscillator	
WDT watchdog timer		
WIC	wakeup interrupt controller	
WLCSP	wafer level chip scale package	
XIP	execute-in-place	
XRES	external reset input pin	



Document Conventions

Unit of Measure

Table 64. Unit of Measure

Symbol	Unit of Measure	
°C	degrees Celsius	
dB	decibel	
fF	femto farad	
Hz	hertz	
KB	1024 bytes	
kbps	kilobits per second	
khr	kilohour	
kHz	kilohertz	
kΩ	kilo ohm	
ksps	kilosamples per second	
LSB	least significant bit	
Mbps	megabits per second	
MHz	megahertz	
MΩ	mega-ohm	
Msps	megasamples per second	
μA	microampere	
μF	microfarad	

Table 64. Unit of Measure (continued)

Symbol	Unit of Measure	
μH	microhenry	
μs	microsecond	
μV	microvolt	
μW	microwatt	
mA	milliampere	
ms	millisecond	
mV	millivolt	
nA	nanoampere	
ns	nanosecond	
nV	nanovolt	
Ω	ohm	
pF	picofarad	
ppm	parts per million	
ps	picosecond	
s	second	
sps	samples per second	
sqrtHz	square root of hertz	
V	volt	



Revision History

Revision	ECN	Submission Date	Description of Change
**	6694857	10/10/2019	New datasheet
*A	6756608	12/19/2019	Updated Features. Updated Blocks and Functionality and Functional Description. Updated Pinouts and Power Supply Considerations.
*B	6848239	04/07/2020	Updated Features. Updated Functional Description. Updated Pinouts. Updated PSoC 6 MPN Decoder
*C	6898008	06/25/2020	Updated Development Ecosystem, GPIO, and LCD sections. Added External Crystal Oscillators. Updated Errata
*D	7004924	11/10/2020	Updated amount of available SRAM in Features, Blocks and Functionality, Memory, Table 4, and Ordering Information. Updated PSoC 6 MCU Resources subsection. Updated CPUs subsection. Updated PSoC 64 Security. Updated Flexible Clocking Options, Block Diagram, CPUs, Clock System, and SID431. Updated Universal Digital Blocks (UDBs), UDB Port Adapter Specifications Conditions. Added InterProcessor Communication (IPC). Updated Analog Subsystem diagram. Updated the XRES bullet in Reset, updated SID15 Description and Conditions, and Power-on-Reset specifications table. Updated ModusToolbox Software. Updated Reset events are asynchronous and guarantee reversion to a known state. Some of the reset sources are recorded in a register, which is retained through reset and allows software to determine the cause of the reset. Updated Power Supply Considerations. Added footnote to TMCLK_SOC specs. Updated SID7A conditions, SID7D description, and SID8 conditions. Added spec SID468 - SID474, and SID468A - SID474A. Updated Ordering Information. Integrated ECO erratum into External Crystal Oscillators. Added ECO Usage Guidelines table. Added three errata items.
*E	7094508	03/01/2021	Added Table 12 and Figure 17. Updated conditions for SID316 and updated description of SID319. Changed BLE references to Bluetooth LE. Updated Security terminology to Infineon standards. Incorporated GPIO-related errata into the GPIO, ADC, and CapSense sections.
*F	7173987	06/30/2021	Added opamp graphs (Figure 18 and Figure 19). Updated Security terminology.
*G	7231613	08/19/2021	Updated SIDDS2 - Corrected Deep Sleep current values Removed "System Deep Sleep power higher than specification" errata item.
*H	7508678	12/13/2021	Removed Errata and Preliminary tag. Added note regarding unused USB pins in USB Full-Speed Device Interface, Power Supply Considerations, and Pinouts. Updated SIDC1 description. Updated Figure 17 and added related footnote. Updated details/conditions for SID7A. Updated SID325U, SID328, and SID329 description.



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	*	7785319	10/26/2022	Added device identification and revision information in Features. Added spec SID415 and SID304P. Added footnote "Guaranteed by design, not production tested" for specs SID402 - SID412. Updated Clock System and PLL specifications. Updated Protection Units.



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